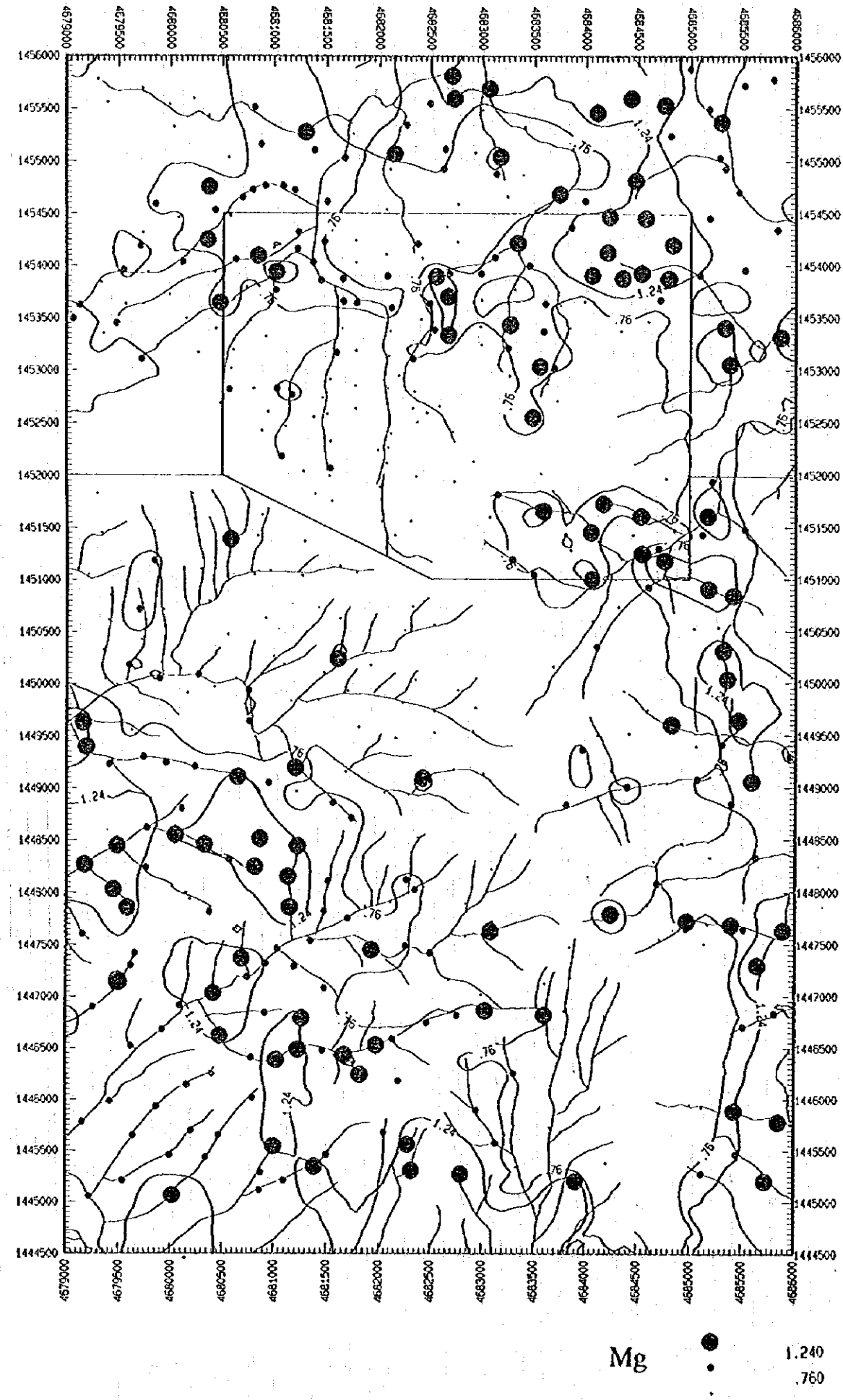
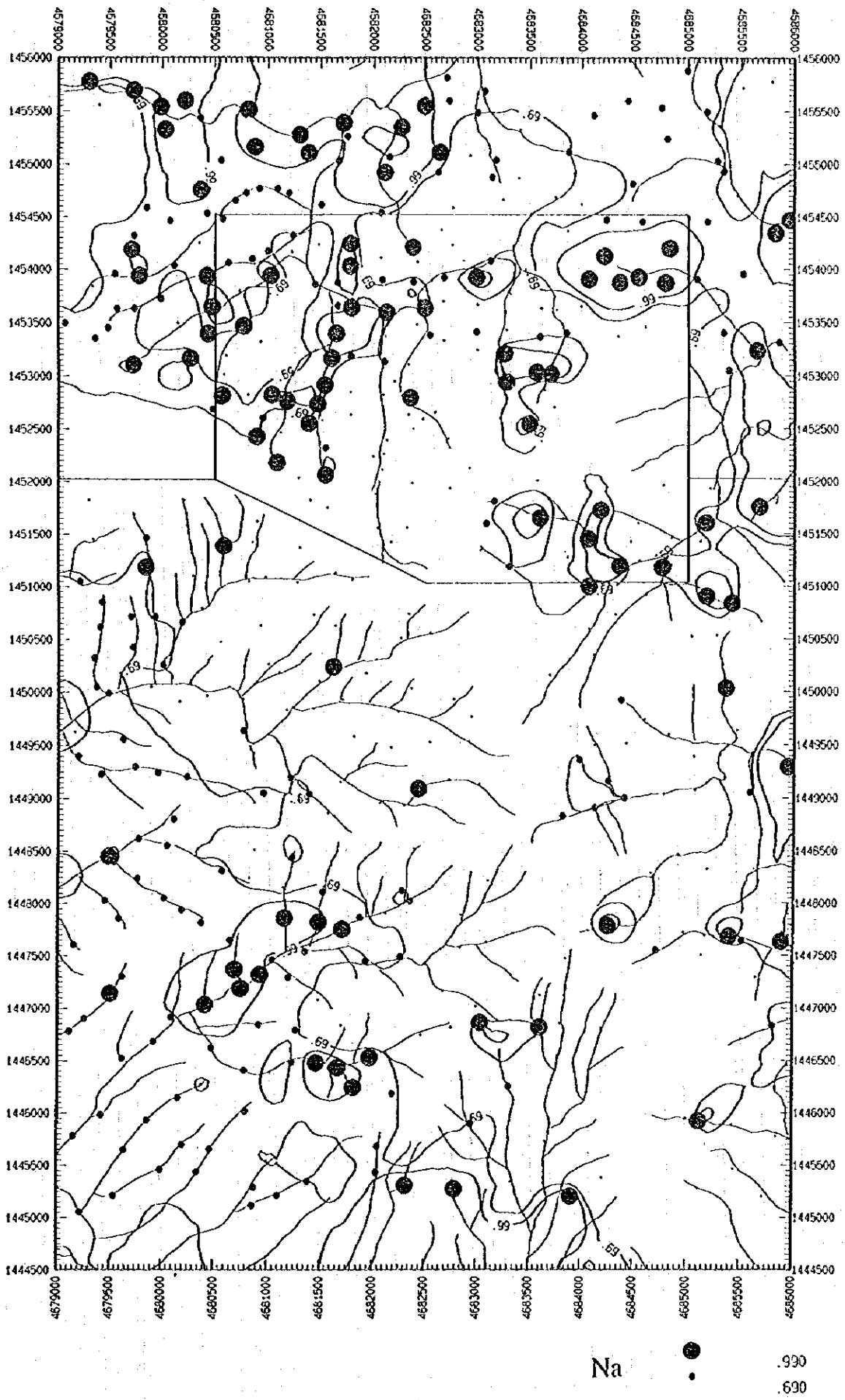
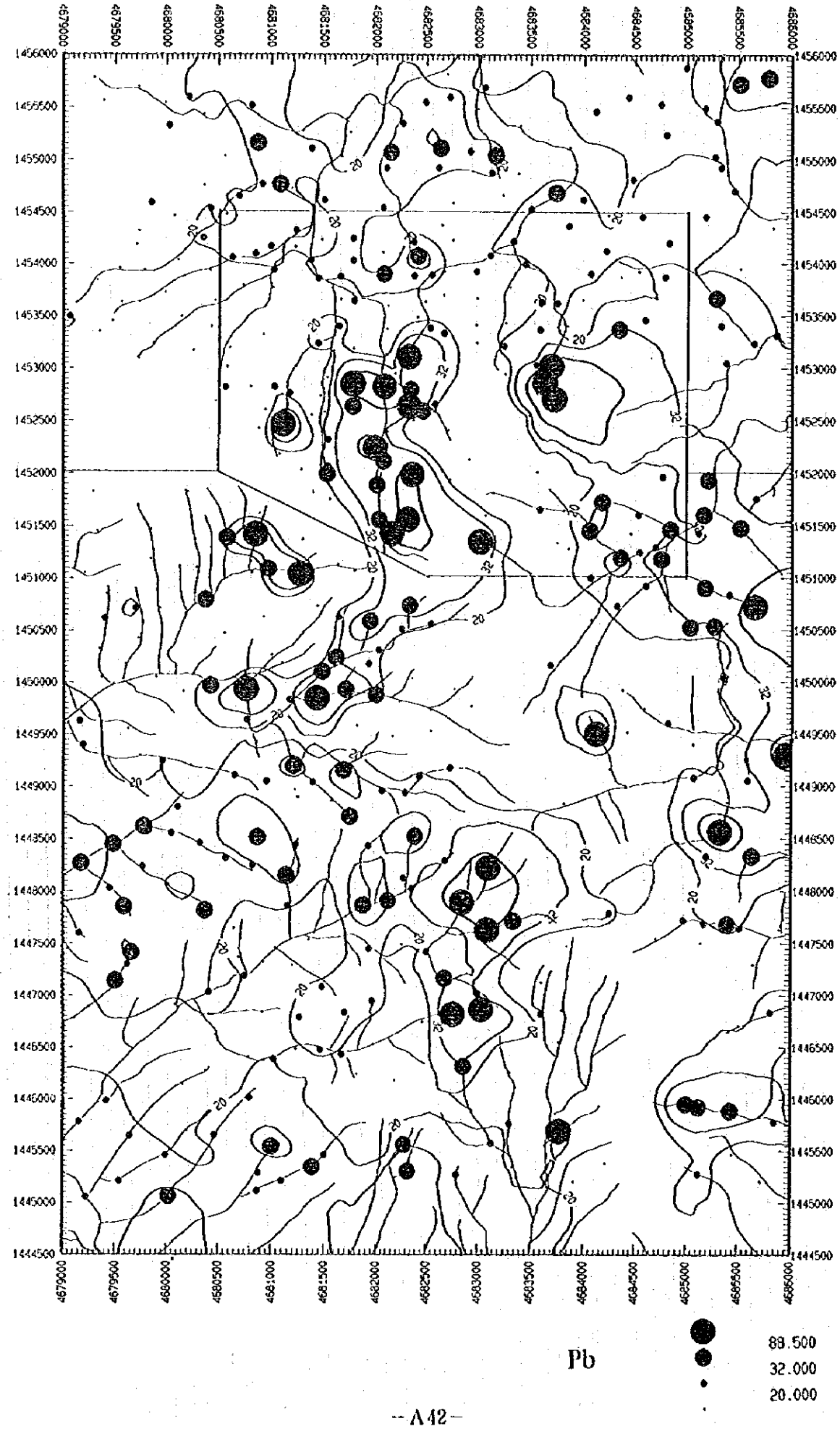
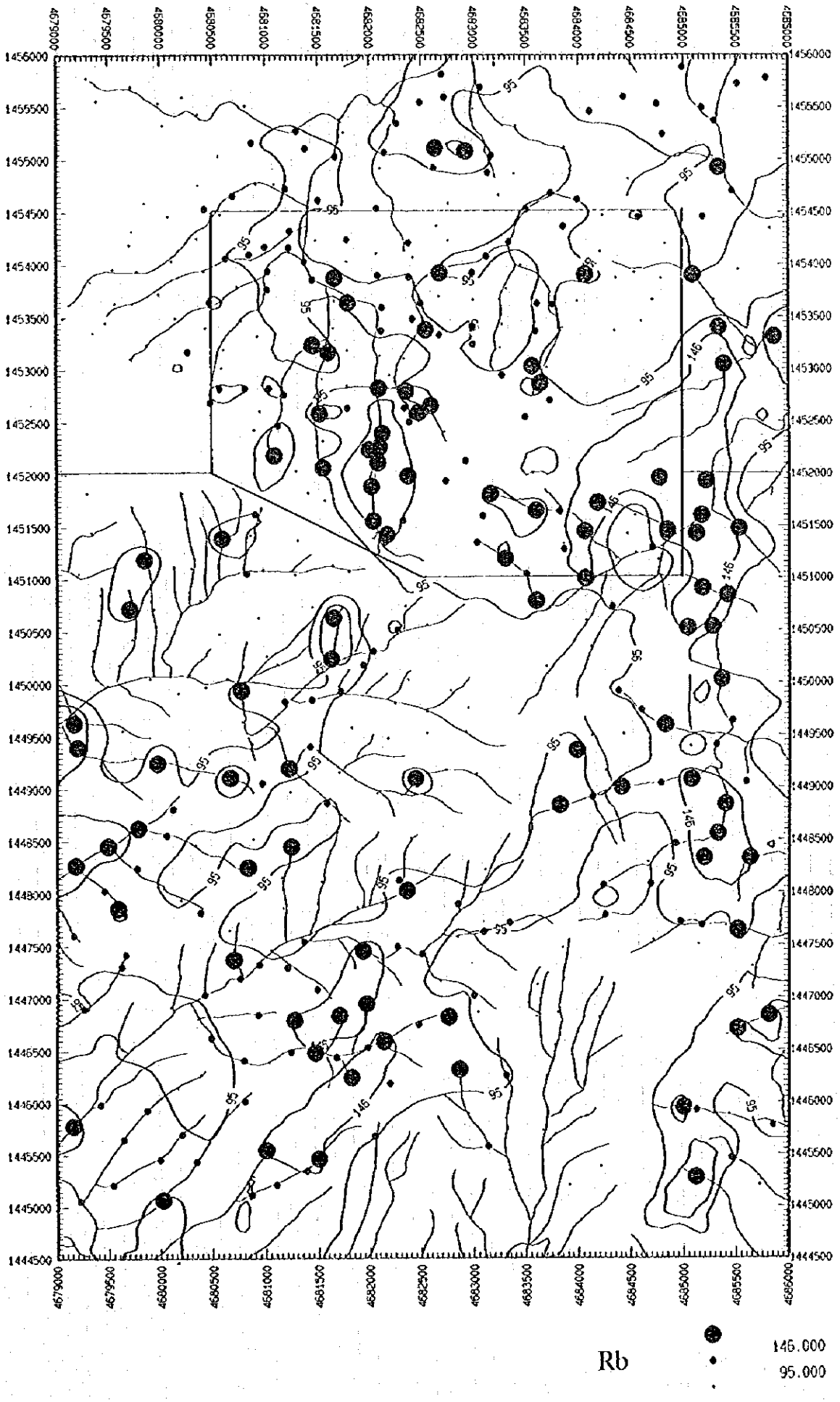
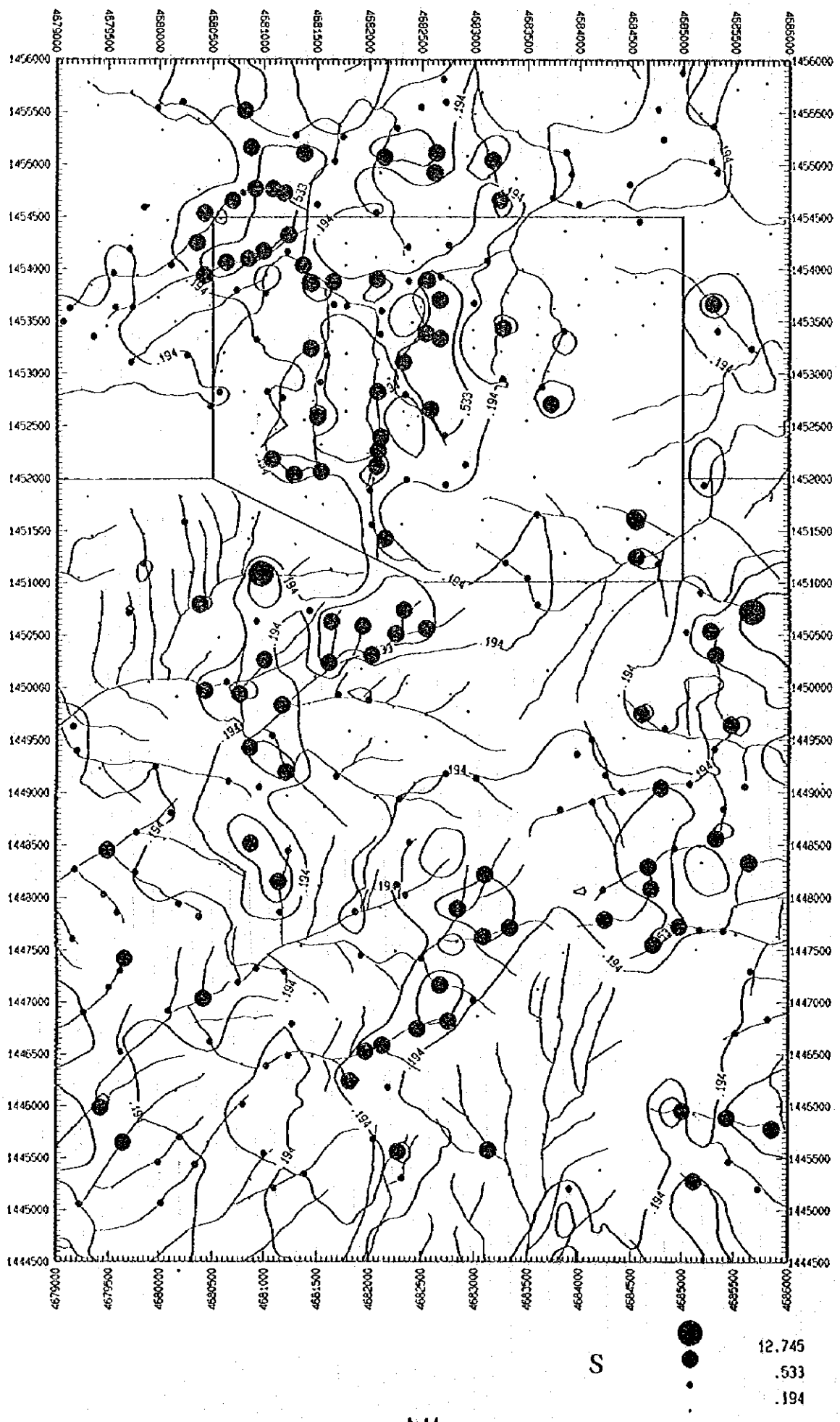
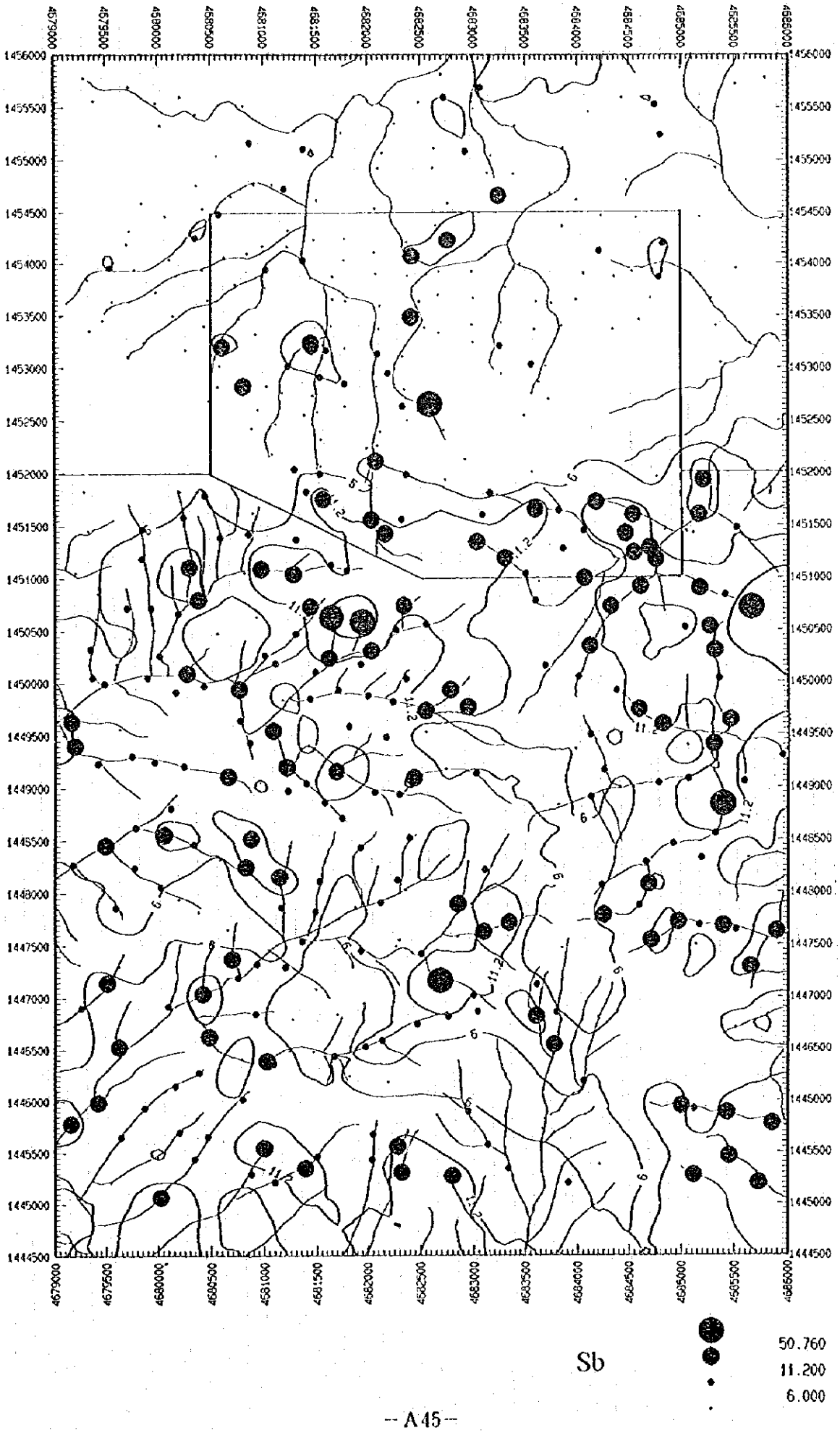

Mg
1.240
.760

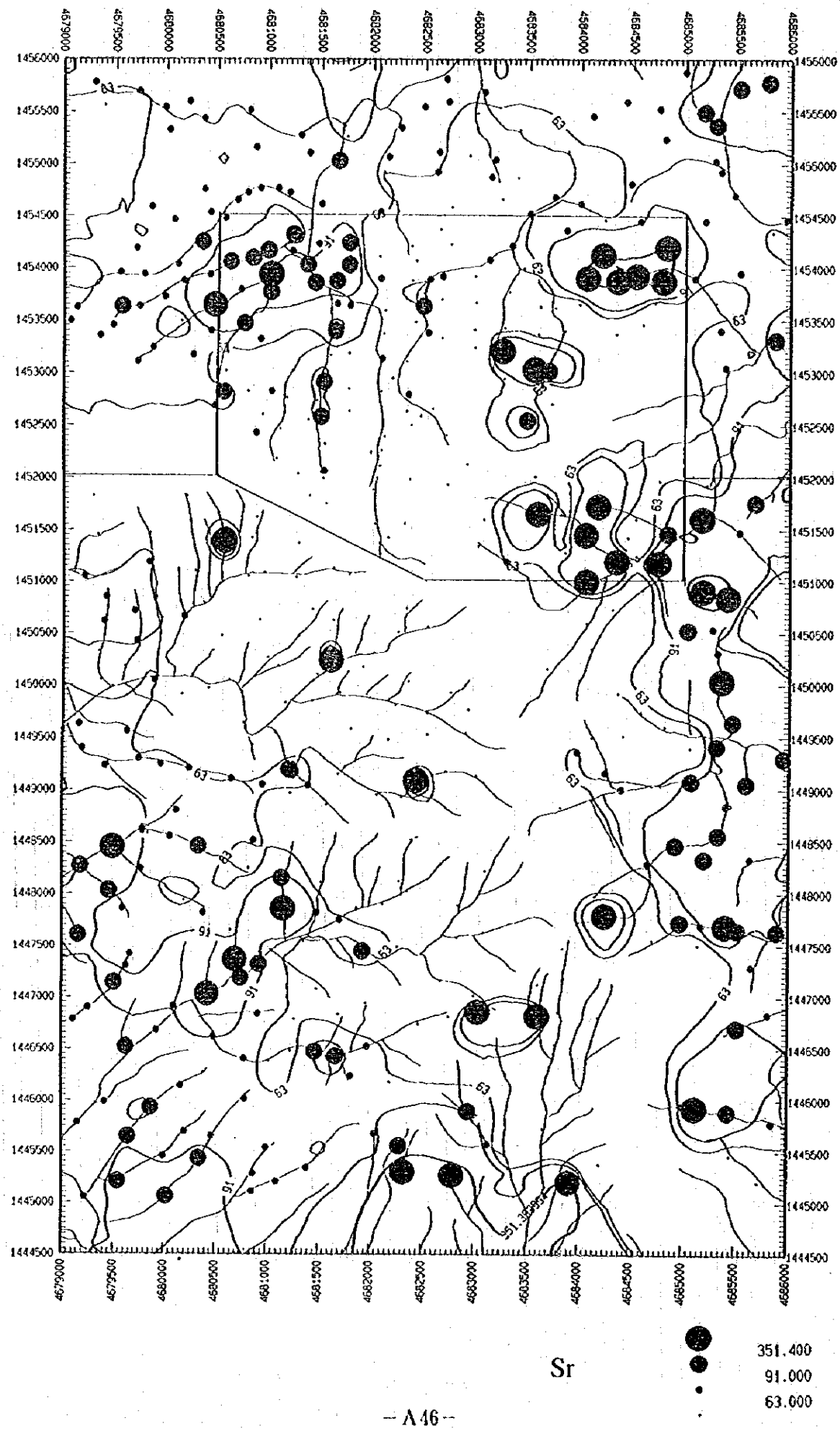

Na
.990
.690

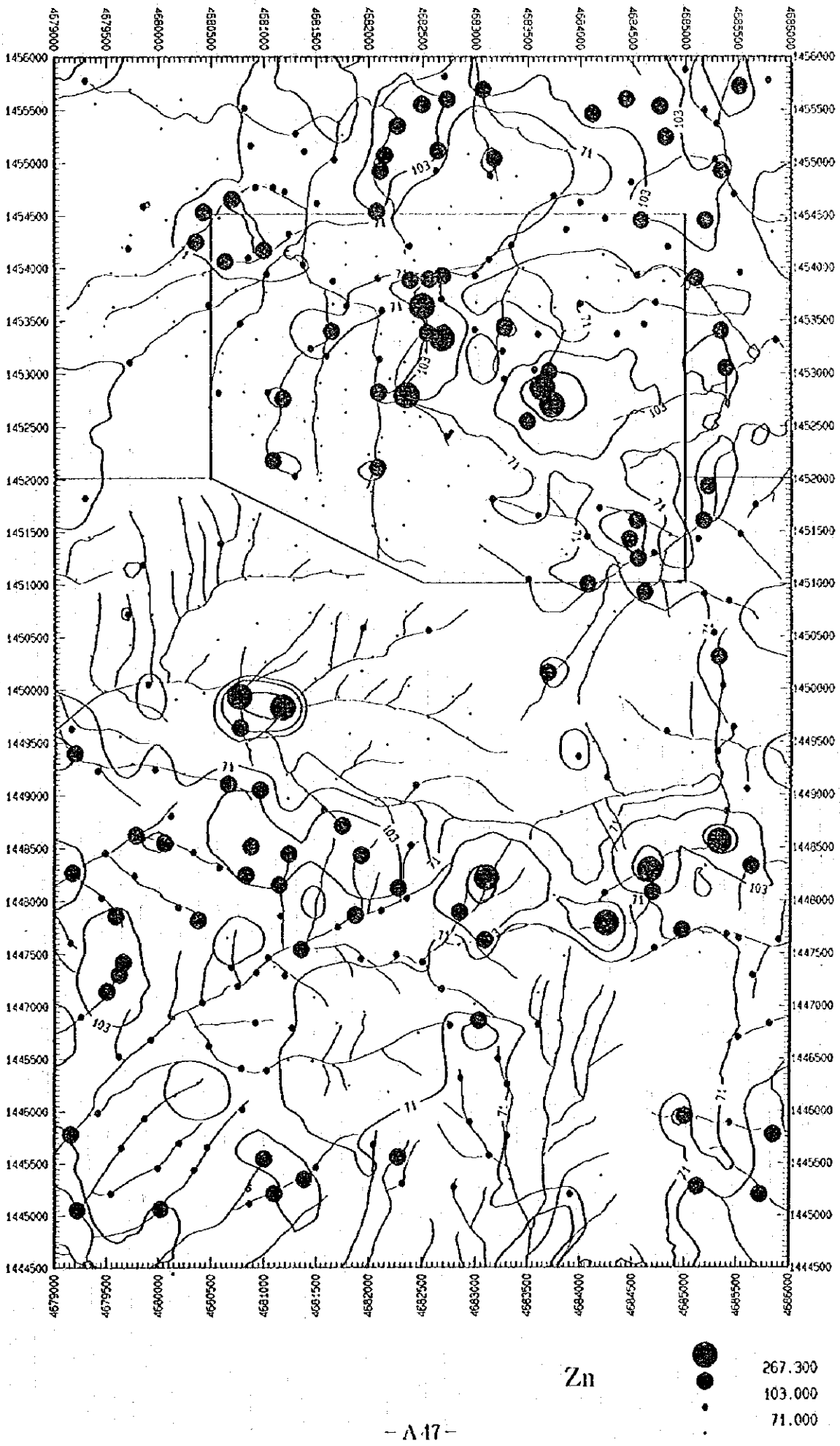

Pb
88.500
32.000
20.000


Rb
146.000
95.000


S
12.745
.533
.194


Sb
50.760
11.200
6.000


Sr
351.400
91.000
63.000

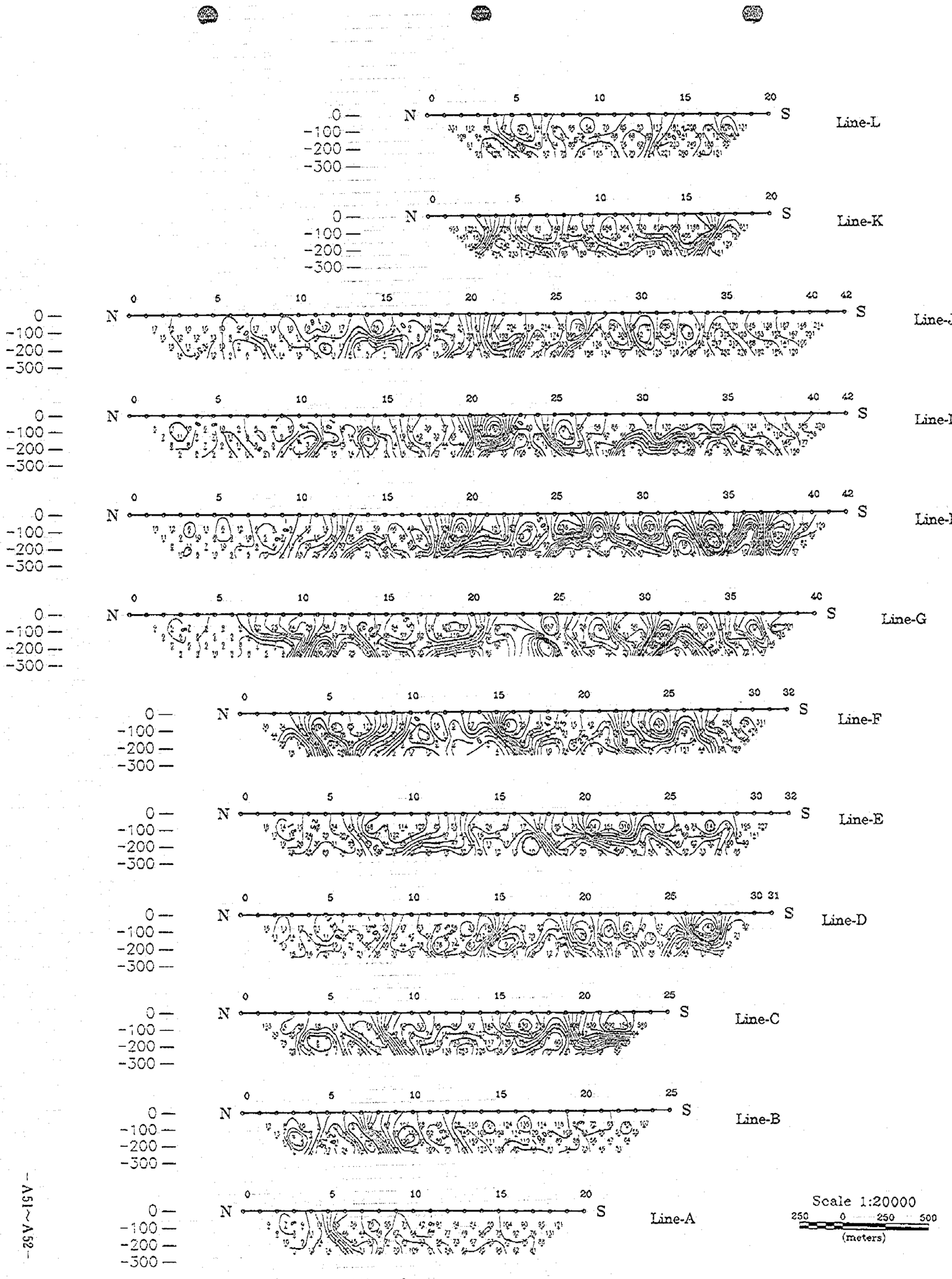


Zn

267.300
103.000
71.000

Appendix 5

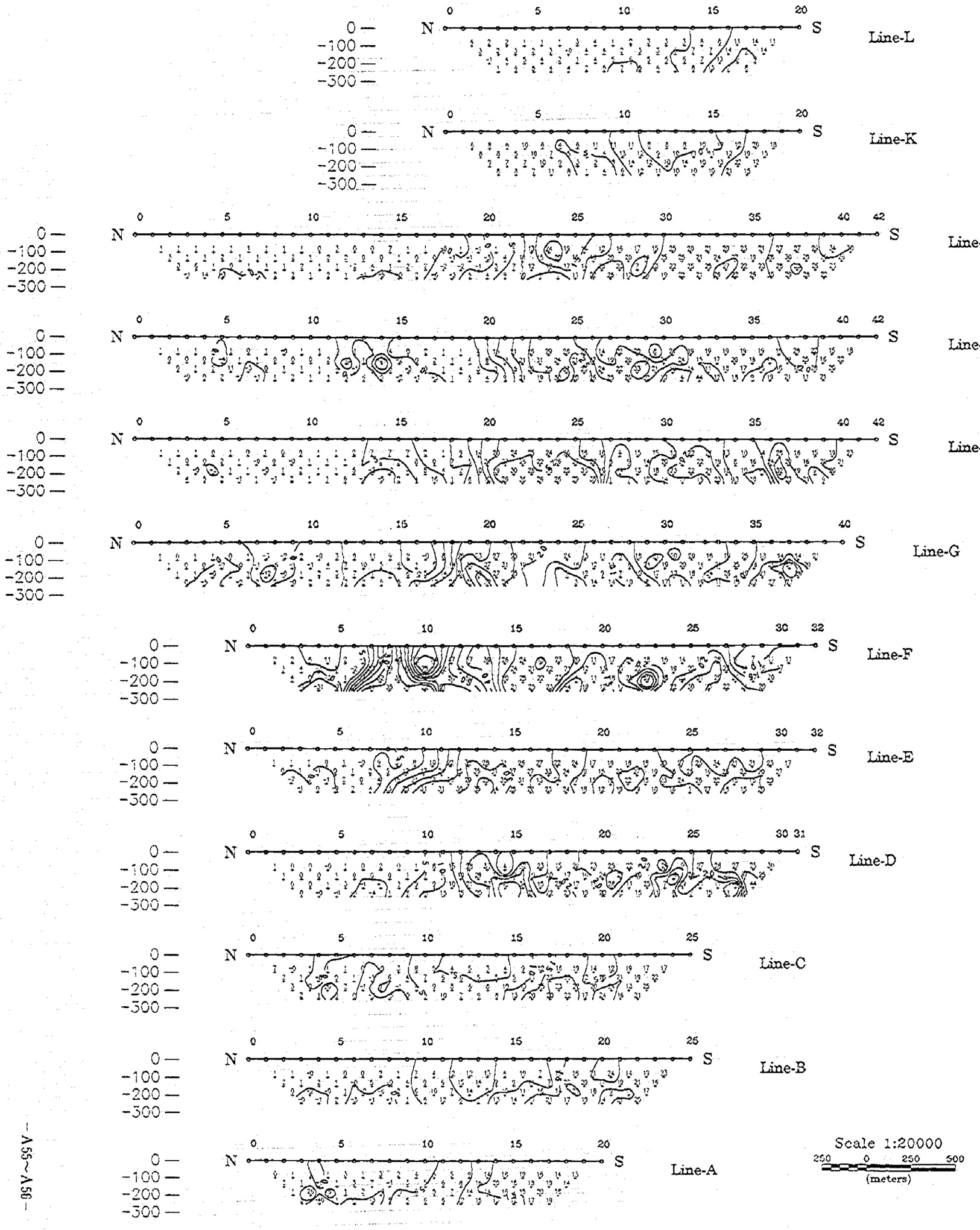
Pseudo-section of apparent resistivity in S. Imbak Sub-area North



Appendix5 Pseudo-section of apparent resistivity in S.Imbak Sub-area North

Appendix 6

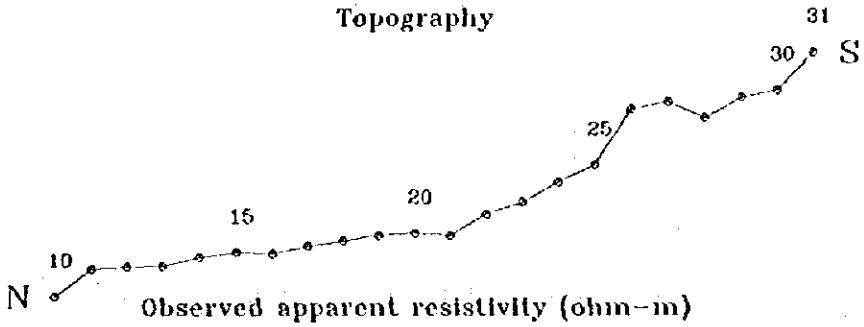
Pseudo-section of chargeability in S. Imbak Sub-area North

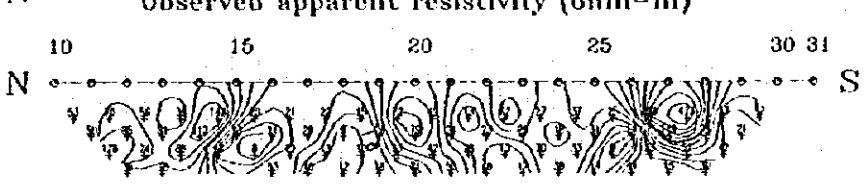


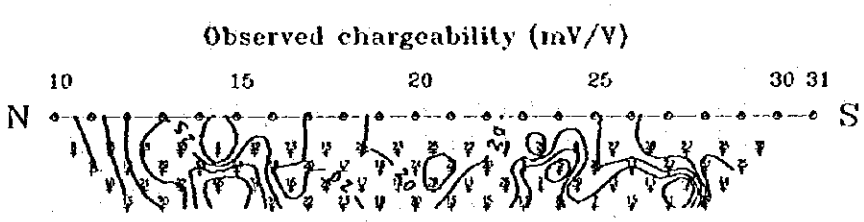
Appendix6 Pseudo-section of chargeability in S.Imbak Sub-area North

Appendix 7

IP model simulation in S. Imbak Sub-area North

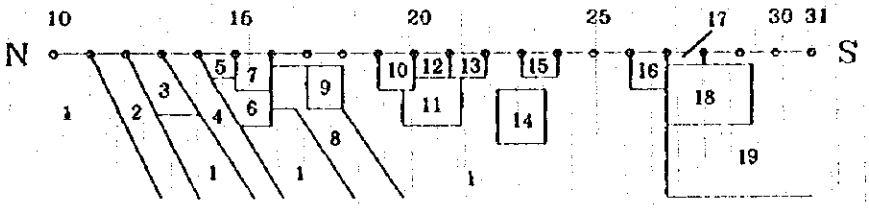


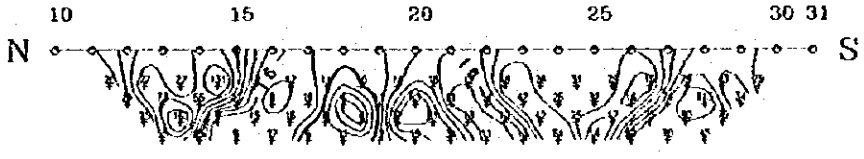


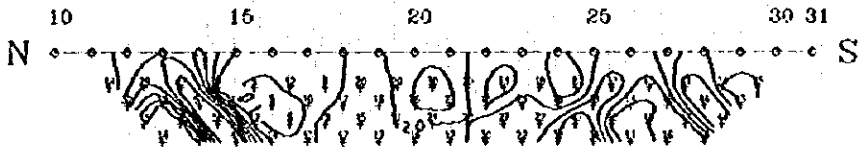


CODE NUMBER	:	1	2	3	4	5	6	7	8	9	10
RESIS (ohm-m)	:	30.0	100.0	30.0	100.0	50.0	100.0	100.0	3.0	10.0	8.0
CHARGE (mV/V)	:	15.0	10.0	60.0	10.0	5.0	5.0	10.0	15.0	5.0	25.0

CODE NUMBER	:	11	12	13	14	15	16	17	18	19	
RESIS (ohm-m)	:	40.0	10.0	60.0	20.0	35.0	30.0	10.0	500.0	50.0	
CHARGE (mV/V)	:	50.0	20.0	7.0	40.0	2.0	60.0	25.0	35.0	25.0	

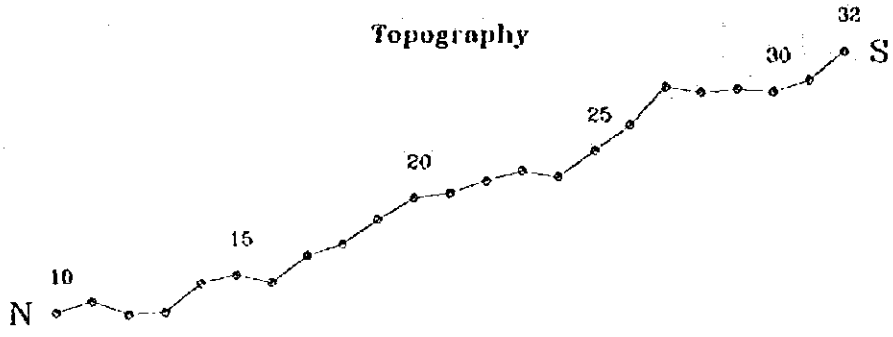




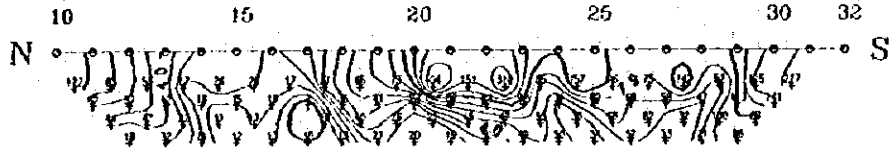


Results of IP model simulation of Line-D in S.Imbak Sub-area

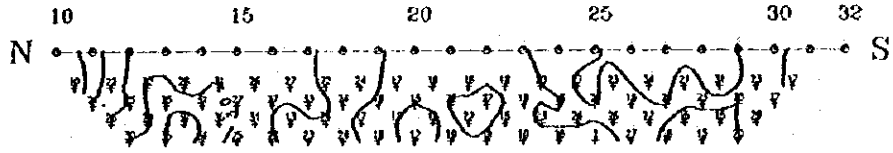
Topography



Observed apparent resistivity (ohm-m)



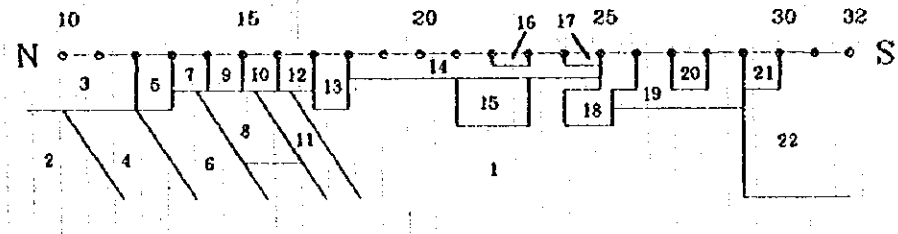
Observed chargeability (mV/V)



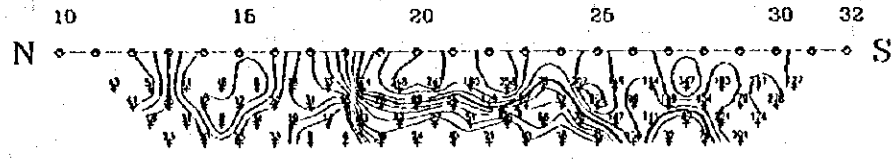
CODE NUMBER	:	1	2	3	4	5	6	7	8	9	10	11
RESIS (ohm·m)	:	20.0	20.0	600.0	20.0	25.0	25.0	25.0	14.0	10.0	10.0	100.0
CHARGE (mV/V)	:	15.0	2.0	2.0	15.0	26.0	30.0	20.0	28.0	25.0	30.0	20.0

CODE NUMBER	:	12	13	14	15	16	17	18	19	20	21	22
RESIS (ohm·m)	:	100.0	200.0	400.0	20.0	180.0	100.0	100.0	300.0	200.0	100.0	250.0
CHARGE (mV/V)	:	20.0	15.0	20.0	50.0	15.0	20.0	25.0	25.0	30.0	30.0	20.0

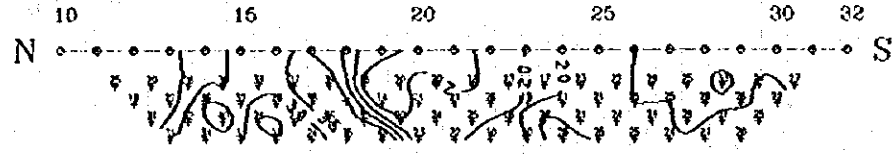
IP model



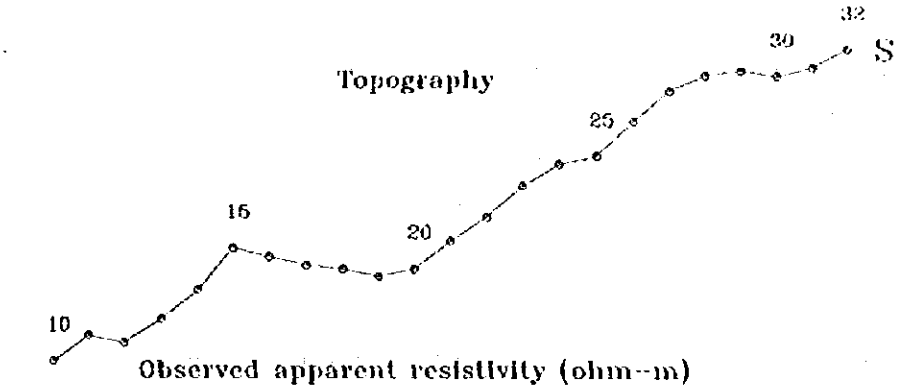
Calculated apparent resistivity (ohm-m)



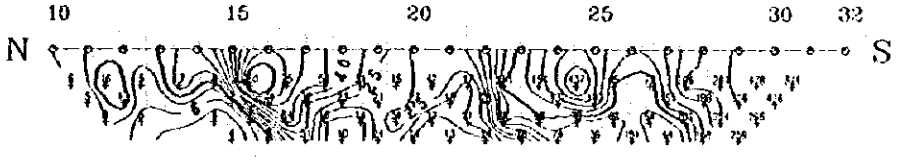
Calculated chargeability (mV/V)



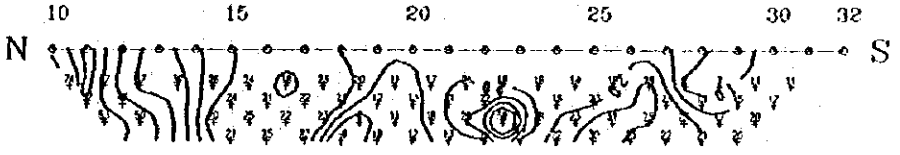
Results of IP model simulation of Line-E in S.Imbak Sub-area



Observed apparent resistivity (ohm-m)



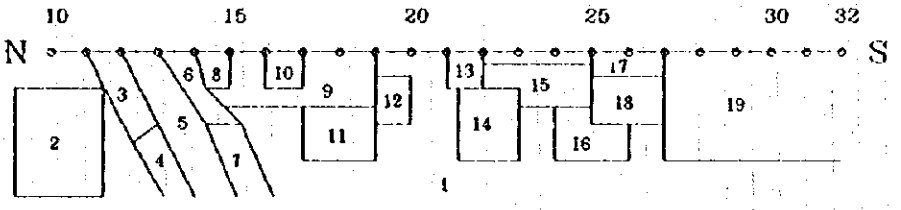
Observed chargeability (mV/V)



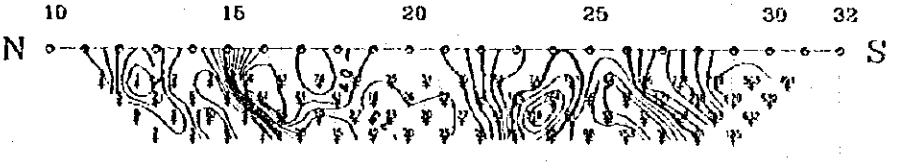
CODE NUMBER	:	1	2	3	4	5	6	7	8	9	10
RESIS (ohm-m)	:	30.0	3.0	2.0	5.0	5.0	2.0	5.0	100.0	50.0	100.0
CHARGE (mV/V)	:	15.0	50.0	40.0	30.0	20.0	20.0	25.0	20.0	14.0	15.0

CODE NUMBER	:	11	12	13	14	15	16	17	18	19
RESIS (ohm-m)	:	10.0	5.0	50.0	20.0	500.0	20.0	200.0	20.0	500.0
CHARGE (mV/V)	:	10.0	3.0	20.0	80.0	10.0	50.0	8.0	40.0	12.0

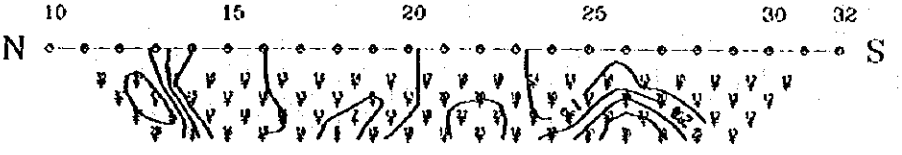
IP model



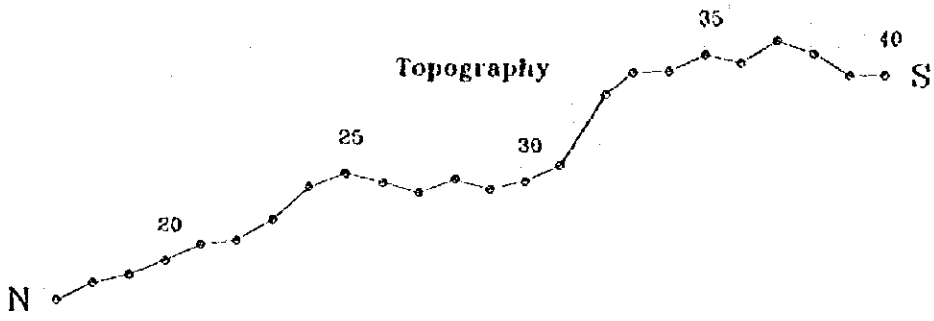
Calculated apparent resistivity (ohm-m)



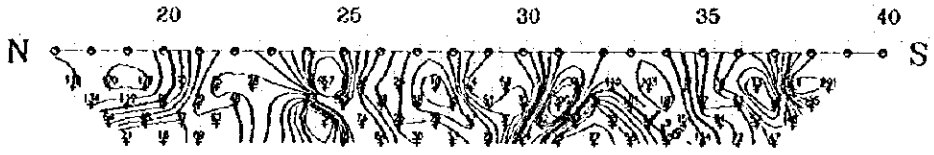
Calculated chargeability (mV/V)



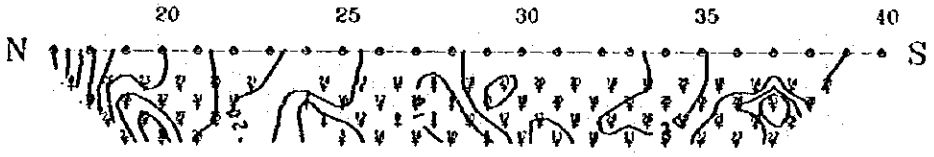
Results of IP model simulation of Line-F in S.Imbak Sub-area



Observed apparent resistivity (ohm-m)



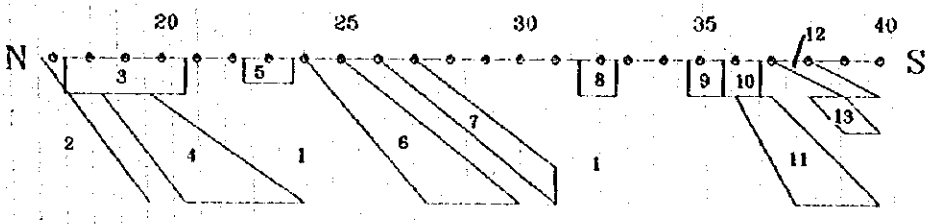
Observed chargeability (mV/V)



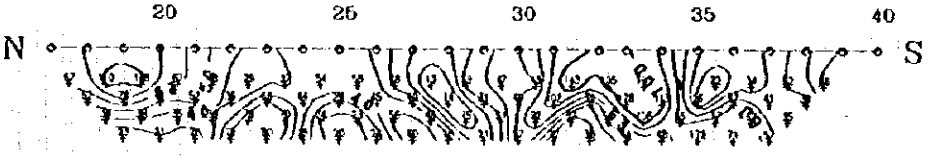
CODE NUMBER	:	1	2	3	4	5	6	7	8	9	10
RESIS (ohm-m)	:	50.0	50.0	120.0	10.0	20.0	100.0	10.0	500.0	50.0	15.0
CHARGE (mV/V)	:	15.0	5.0	15.0	40.0	15.0	25.0	8.0	25.0	25.0	15.0

CODE NUMBER	:	11	12	13
RESIS (ohm-m)	:	50.0	150.0	15.0
CHARGE (mV/V)	:	40.0	15.0	25.0

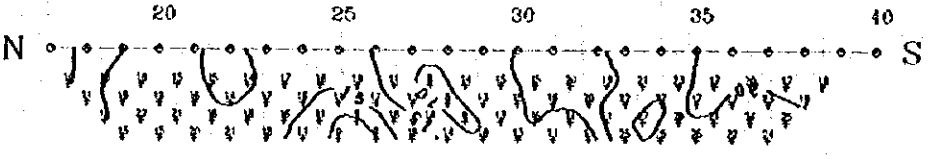
IP model



Calculated apparent resistivity (ohm-m)

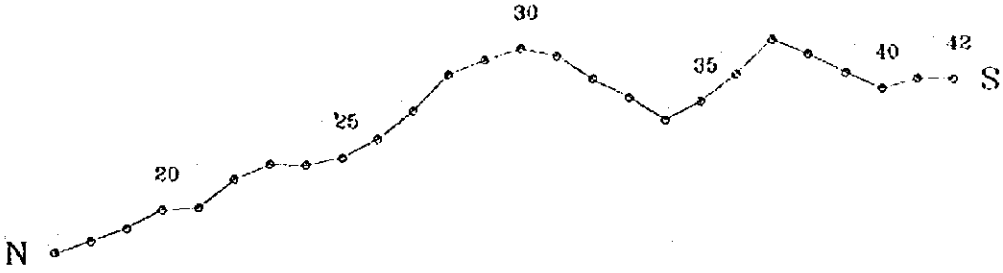


Calculated chargeability (mV/V)

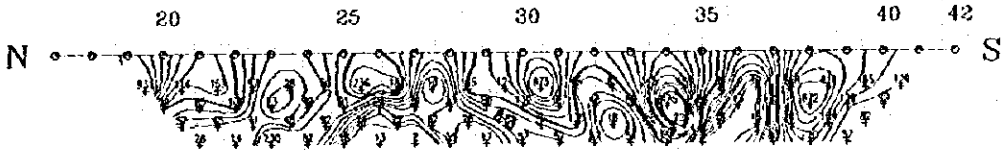


Results of IP model simulation of Line-G in S.Imbak Sub-area

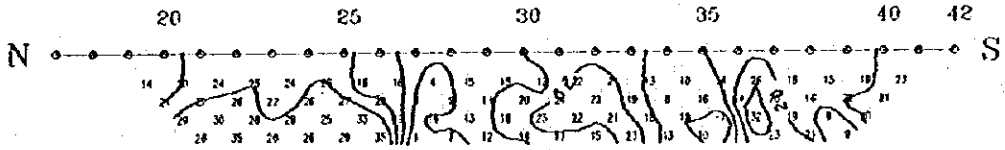
Topography



Observed apparent resistivity (ohm-m)



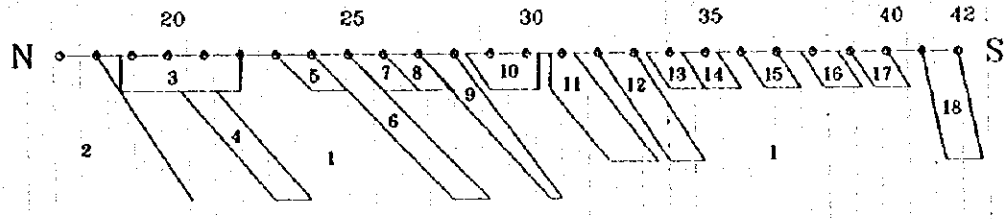
Observed chargeability (mV/V)



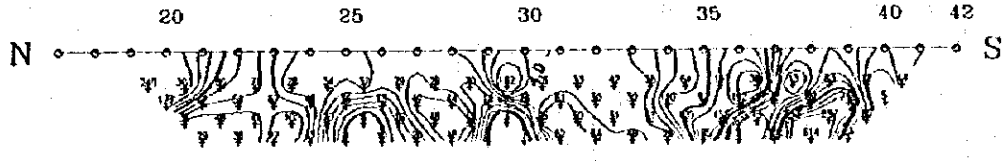
CODE NUMBER	:	1	2	3	4	5	6	7	8	9	10
RESIS (ohm-m)	:	50.0	50.0	300.0	20.0	20.0	15.0	120.0	10.0	10.0	150.0
CHARGE (mV/V)	:	15.0	5.0	20.0	35.0	25.0	30.0	15.0	8.0	20.0	20.0

CODE NUMBER	:	11	12	13	14	15	16	17	18
RESIS (ohm-m)	:	15.0	80.0	25.0	150.0	120.0	12.0	120.0	50.0
CHARGE (mV/V)	:	35.0	20.0	8.0	35.0	10.0	25.0	25.0	10.0

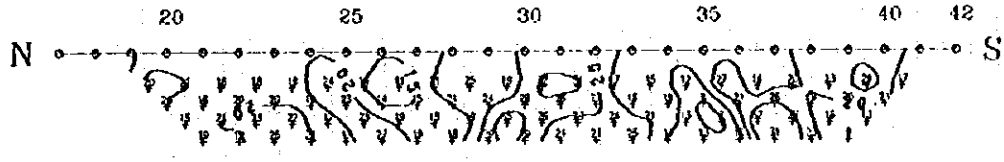
IP model



Calculated apparent resistivity (ohm-m)

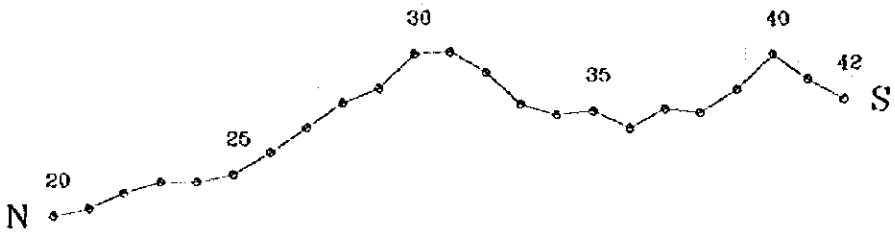


Calculated chargeability (mV/V)

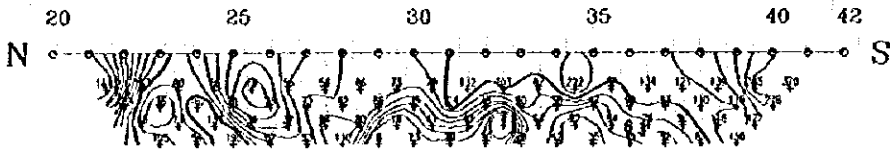


Results of IP model simulation of Line-H in S.Imbak Sub-area

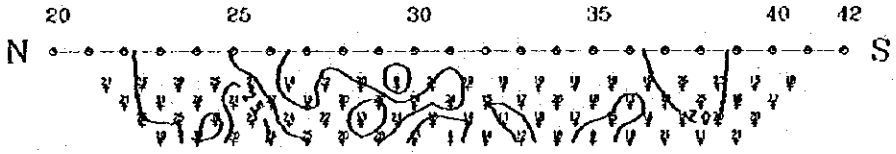
Topography



Observed apparent resistivity (ohm-m)



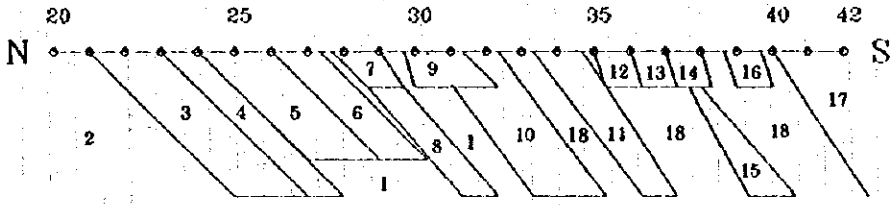
Observed chargeability (mV/V)



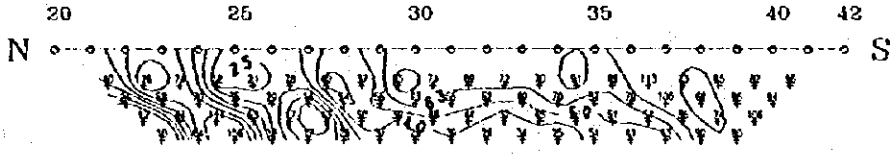
CODE NUMBER	:	1	2	3	4	5	6	7	8	9	10
RESIS (ohm-m)	:	30.0	25.0	200.0	30.0	20.0	120.0	120.0	10.0	80.0	10.0
CHARGE (mV/V)	:	15.0	5.0	20.0	30.0	20.0	25.0	10.0	25.0	25.0	15.0

CODE NUMBER	:	11	12	13	14	15	16	17	18
RESIS (ohm-m)	:	10.0	150.0	80.0	100.0	15.0	80.0	150.0	80.0
CHARGE (mV/V)	:	10.0	20.0	25.0	25.0	15.0	25.0	20.0	15.0

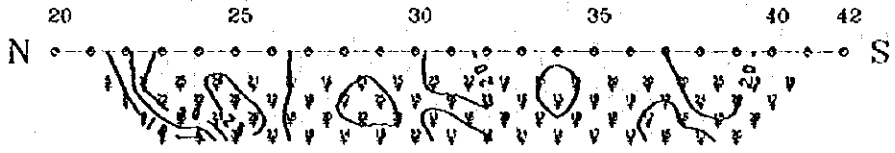
IP model



Calculated apparent resistivity (ohm-m)

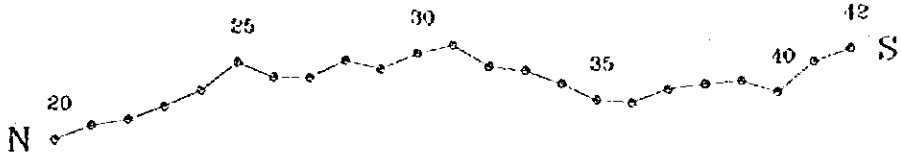


Calculated chargeability (mV/V)

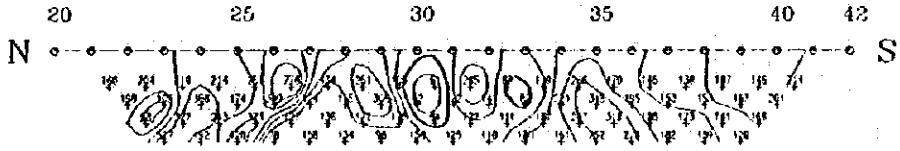


Results of IP model simulation of Line-I in S.Imbak Sub-area

Topography



Observed apparent resistivity (ohm-m)

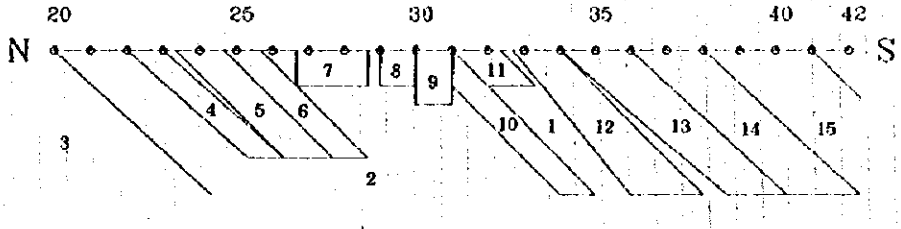


Observed chargeability (mV/V)

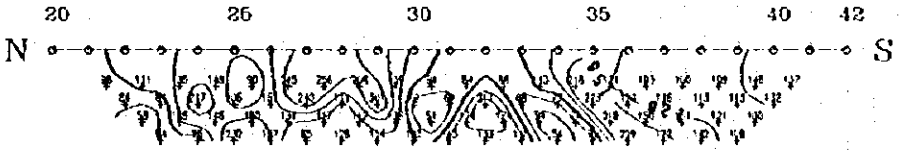
CODE NUMBER	:	1	2	3	4	5	6	7	8	9	10
RESIS (ohm-m)	:	100.0	100.0	20.0	200.0	100.0	250.0	300.0	150.0	200.0	150.0
CHARGE (mV/V)	:	20.0	15.0	8.0	20.0	25.0	10.0	25.0	25.0	20.0	20.0

CODE NUMBER	:	11	12	13	14	15
RESIS (ohm-m)	:	50.0	300.0	120.0	100.0	150.0
CHARGE (mV/V)	:	30.0	30.0	20.0	25.0	35.0

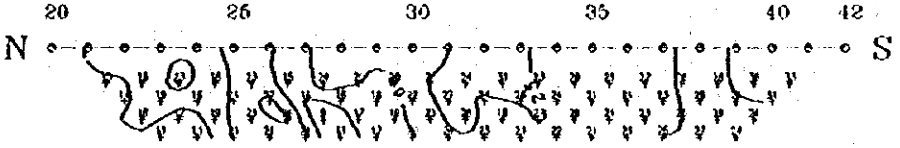
IP model



Calculated apparent resistivity (ohm-m)



Calculated chargeability (mV/V)



Results of IP model simulation of Line-J in S.Imbak Sub-area

Appendix 8

List of IP data measured in S. Imbak Sub-areas North

IP DATA LIST IN S. IMBAK SUB-AREA

IP data of Line-A in S. Imbak Sub-area (1)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resis1 (ohm-m)	Tcf	Resis2 (ohm-m)	Charge. (mV/V)
1	0	2	1	2200	12.14	10	1.006	9	0.42
2	0	3	2	3600	6.34	13	1.337	9	1.46
3	0	4	3	3200	2.09	12	1.174	10	0.80
4	0	5	4	1750	0.31	7	0.620	11	1.73
5	1	3	1	3200	17.02	10	1.298	7	0.77
6	1	4	2	2800	3.36	9	1.030	8	0.52
				.					
				.					
				.					

Legend for the List

No. : Serial No. of IP data at each point
P1 : Name of a station of potential electrode
C1 : Name of a station of current electrode
N : N spread
Curr : Current value (mili ampere)
Voltage : Received voltage difference in mV between potential dipoles
Resis1 : Apparent resistivity value in ohm-m before terrain correction
Tcf : Terrain correction factor
Resis2 : Apparent resistivity value in ohm-m after terrain correction
Charge. : Chargeability value in mV/V between 820 and 1050 msec

IP data of Line-A in S. Imbak Sub-area (1)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resis1 (ohm-m)	Tcf	Resis2 (ohm-m)	Charge. (mV/V)
1	0	2	1	2200	12.14	10	1.006	9	0.42
2	0	3	2	3600	6.34	13	1.337	9	1.46
3	0	4	3	3200	2.09	12	1.174	10	0.80
4	0	5	4	1750	0.31	7	0.620	11	1.73
5	1	3	1	3200	17.02	10	1.298	7	0.77
6	1	4	2	2800	3.36	9	1.030	8	0.52
7	1	5	3	1750	0.45	5	0.546	9	25.92
8	1	6	4	1700	0.37	8	0.580	13	-39.63
9	2	4	1	3200	11.83	7	0.776	9	0.69
10	2	5	2	2000	1.27	5	0.448	11	-5.49
11	2	6	3	2000	0.77	7	0.496	14	15.66
12	2	7	4	2500	0.86	13	0.900	14	0.63
13	3	5	1	1800	6.37	7	0.619	11	1.19
14	3	6	2	1700	2.78	12	0.765	15	0.53
15	3	7	3	2500	2.66	20	1.410	14	0.47
16	3	8	4	2400	0.77	12	0.748	16	-1.42
17	4	6	1	1800	66.77	70	1.259	55	3.26
18	4	7	2	3200	38.27	90	1.916	46	2.60
19	4	8	3	3200	6.95	41	0.905	45	1.90
20	4	9	4	3200	4.08	48	1.507	31	-2.65
21	5	7	1	1750	41.34	45	1.221	36	1.22
22	5	8	2	1750	5.26	23	0.516	44	6.79
23	5	9	3	2000	3.17	30	0.884	33	-2.48
24	5	10	4	2000	3.75	71	1.145	62	5.32
25	6	8	1	1700	31.78	35	0.455	76	3.39
26	6	9	2	2000	14.28	54	0.913	59	-1.32
27	6	10	3	2000	8.88	84	1.169	71	10.19
28	6	11	4	1800	2.58	54	0.766	70	5.56
29	7	9	1	2500	117.08	88	1.584	55	2.17
30	7	10	2	2500	50.03	151	1.726	87	2.83
31	7	11	3	2500	11.66	88	1.082	81	5.39
32	7	12	4	2500	5.32	80	0.728	109	5.81
33	8	10	1	2400	89.76	70	0.980	71	3.89
34	8	11	2	2400	12.14	38	0.593	64	5.09
35	8	12	3	1700	3.39	38	0.408	93	5.15
36	8	13	4	1600	3.13	74	0.813	91	6.15
37	9	11	1	2600	36.77	27	0.629	42	5.33
38	9	12	2	1700	7.18	32	0.504	63	5.61
39	9	13	3	1600	5.00	59	1.053	56	6.61
40	9	14	4	1300	2.22	64	1.173	54	11.54
41	10	12	1	1800	73.34	77	0.840	91	5.12
42	10	13	2	1600	28.33	134	1.733	77	8.45
43	10	14	3	1300	9.02	131	1.781	73	14.33
44	10	15	4	1400	2.28	61	0.718	84	15.04
45	11	13	1	1600	107.57	127	1.963	64	8.96
46	11	14	2	1300	16.71	97	1.398	69	15.46
47	11	15	3	1400	2.57	35	0.517	67	14.39
48	11	16	4	1650	4.02	92	0.966	95	12.61
49	12	14	1	1300	41.70	60	0.711	84	13.57
50	12	15	2	1400	3.02	16	0.272	58	19.66

IP data of Line-A in S. Imbak Sub-area (2)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resis1 (ohm-m)	Tcf	Resis2 (ohm-m)	Charge. (mV/V)
51	12	16	3	1700	4.70	52	0.556	93	16.05
52	12	17	4	1700	2.06	46	0.478	96	11.67
53	13	15	1	1400	18.48	25	0.411	60	18.08
54	13	16	2	1600	16.77	79	1.043	75	18.05
55	13	17	3	1600	5.59	66	0.899	73	14.75
56	13	18	4	1600	2.52	59	0.943	62	17.35
57	14	16	1	1300	117.60	171	1.639	104	19.40
58	14	17	2	1300	19.44	113	1.218	92	18.44
59	14	18	3	1300	6.65	96	1.250	76	19.69
60	14	19	4	1300	3.70	107	1.308	81	19.29
61	15	17	1	1400	47.64	64	0.707	90	15.46
62	15	18	2	1400	10.66	57	0.745	76	18.88
63	15	19	3	1400	4.99	67	0.755	88	17.90
64	16	18	1	1650	88.43	101	1.063	95	13.90
65	16	19	2	1650	31.24	143	1.085	131	14.24
66	17	19	1	1800	123.83	130	1.071	121	12.91

IP data of Line-B in S. Imbak Sub-area (1)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resis1 (ohm-m)	Tcf	Resis2 (ohm-m)	Charge. (mV/V)
1	0	2	1	2800	14.61	10	0.815	12	0.77
2	0	3	2	2600	3.74	11	0.817	13	1.86
3	0	4	3	1650	1.06	12	0.896	13	0.08
4	0	5	4	1850	0.49	10	1.423	7	-0.21
5	1	3	1	2600	12.95	9	1.038	8	1.38
6	1	4	2	1750	2.59	3	1.132	2	1.15
7	1	5	3	1850	1.02	10	1.693	5	-1.79
8	1	6	4	2600	1.13	16	1.414	11	-0.99
9	2	4	1	1700	10.09	11	1.053	10	-0.16
10	2	5	2	1850	2.66	11	1.435	7	1.67
11	2	6	3	2600	2.29	17	1.131	15	-0.08
12	2	7	4	1900	0.57	11	0.619	17	1.71
13	3	5	1	1850	11.91	12	1.233	9	0.59
14	3	6	2	2600	6.31	18	0.928	19	0.92
15	3	7	3	1900	1.13	11	0.512	21	1.16
16	3	8	4	1900	0.59	12	0.483	24	-2.91
17	4	6	1	2600	16.01	12	0.563	21	0.26
18	4	7	2	1650	1.54	7	0.367	19	-0.15
19	4	8	3	1650	0.75	9	0.374	24	-0.28
20	4	9	4	1650	0.45	10	0.668	14	-0.55
21	5	7	1	1850	4.72	5	0.735	6	0.03
22	5	8	2	1850	1.54	6	0.790	7	5.08
23	5	9	3	1850	0.80	8	1.405	5	-5.48
24	5	10	4	1850	0.66	13	1.569	8	-1.00
25	6	8	1	2600	62.85	46	1.077	42	2.07
26	6	9	2	2600	19.34	56	1.736	32	-0.40
27	6	10	3	2600	10.17	74	1.730	42	1.66
28	6	11	4	2600	4.08	59	1.102	53	1.04
29	7	9	1	1900	92.65	92	1.358	67	1.40
30	7	10	2	1900	27.88	111	1.136	97	3.65
31	7	11	3	1900	8.77	87	0.667	130	6.03
32	7	12	4	1900	1.92	38	0.548	69	5.79
33	8	10	1	1900	94.75	94	0.883	106	6.68
34	8	11	2	1900	20.52	81	0.522	155	9.28
35	8	12	3	1800	4.12	43	0.464	92	9.76
36	8	13	4	1700	4.26	94	0.860	109	11.53
37	9	11	1	2700	60.80	42	0.617	68	4.08
38	9	12	2	1800	8.24	35	0.668	52	5.92
39	9	13	3	1700	6.77	75	1.271	59	7.17
40	9	14	4	2000	5.62	106	1.498	70	7.49
41	10	12	1	1800	40.35	42	0.697	60	11.74
42	10	13	2	1700	21.98	98	1.450	67	14.51
43	10	14	3	2100	13.67	123	1.605	76	14.26
44	10	15	4	1700	3.93	87	1.003	86	7.36
45	11	13	1	1700	209.55	232	1.810	128	12.29
46	11	14	2	2100	60.28	216	1.480	145	14.41
47	11	15	3	1700	12.60	140	0.825	169	8.96
48	11	16	4	1450	4.99	130	0.750	173	13.14
49	12	14	1	2100	93.32	84	0.761	110	12.98
50	12	15	2	1700	10.67	47	0.447	105	8.89

IP data of Line-B in S. Imbak Sub-area (2)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resis1 (ohm-m)	Tef	Resis2 (ohm-m)	Charge. (mV/V)
51	12	16	3	1800	4.56	48	0.432	111	10.40
52	12	17	4	1800	4.11	86	0.789	108	13.57
53	13	15	1	1700	52.23	58	0.637	91	6.27
54	13	16	2	1700	17.27	77	0.708	108	8.80
55	13	17	3	1700	11.47	127	1.315	96	11.45
56	13	18	4	1600	2.52	59	0.943	62	17.35
57	14	16	1	2000	135.73	128	1.025	124	9.67
58	14	17	2	2000	54.88	207	1.811	114	11.16
59	14	18	3	2100	8.20	74	0.669	110	15.60
60	14	19	4	2100	4.18	75	1.091	68	20.79
61	15	17	1	1700	196.58	218	1.608	135	6.85
62	15	18	2	1700	13.35	59	0.491	120	6.98
63	15	19	3	1700	6.60	73	0.824	88	14.44
64	15	20	4	900	1.86	77	0.944	81	16.47
65	16	18	1	1450	26.90	35	0.307	114	15.14
66	16	19	2	1450	10.51	55	0.633	86	21.71
67	16	20	3	900	3.27	68	0.761	89	20.70
68	16	21	4	700	1.52	82	1.097	74	18.66
69	17	19	1	1400	141.81	191	1.618	118	16.03
70	17	20	2	950	22.53	178	1.647	108	19.54
71	17	21	3	700	7.08	191	2.154	88	18.09
72	17	22	4	730	2.33	120	1.633	73	13.52
73	18	20	1	950	37.55	74	0.879	84	20.82
74	18	21	2	700	6.31	68	1.068	63	17.32
75	18	22	3	730	1.62	42	0.738	56	9.03
76	18	23	4	700	0.32	15	0.323	46	20.98
77	19	21	1	800	34.35	81	1.122	72	24.18
78	19	22	2	800	4.70	44	0.779	56	18.70
79	19	23	3	800	0.77	16	0.339	47	10.71
80	19	24	4	800	0.46	26	0.504	51	19.56
81	20	22	1	950	22.61	45	0.660	68	14.44
82	20	23	2	950	2.26	16	0.310	51	20.77
83	20	24	3	950	1.31	32	0.498	64	16.65
84	21	23	1	700	7.28	18	0.440	40	18.56
85	21	24	2	700	3.28	46	0.825	55	15.78
86	22	24	1	730	35.06	137	1.275	107	23.09

IP data of Line-C in S. Imbak Sub-area (1)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resis1 (ohm-m)	Tcf	Resis2 (ohm-m)	Chargo. (mV/V)
1	0	2	1	1300	220.95	320	1.655	193	7.15
2	0	3	2	1600	6.71	32	1.054	30	2.28
3	0	4	3	1700	7.08	79	1.010	78	3.38
4	0	5	4	1700	1.75	39	1.330	29	1.78
5	1	3	1	1600	7.24	9	0.627	14	-0.10
6	1	4	2	1700	5.20	23	0.651	35	0.96
7	1	5	3	1700	1.08	12	0.885	13	0.10
8	1	6	4	2100	0.73	13	0.855	15	1.02
9	2	4	1	700	26.03	29	1.011	28	1.06
10	2	5	2	1700	2.56	11	1.409	7	-8.10
11	2	6	3	2100	1.21	11	1.305	8	19.84
12	2	7	4	2800	1.19	16	1.367	11	0.44
13	3	5	1	1700	16.76	19	1.023	18	1.33
14	3	6	2	2100	2.33	8	0.923	8	0.00
15	3	7	3	2700	1.64	11	0.963	11	1.53
16	3	8	4	2800	0.71	10	0.623	16	0.29
17	4	6	1	1800	16.97	18	0.901	19	0.62
18	4	7	2	1700	5.36	24	0.961	24	0.99
19	4	8	3	1700	1.97	22	0.609	36	-1.11
20	4	9	4	1700	1.06	24	0.677	35	-2.61
21	5	7	1	1700	11.75	13	1.064	12	0.08
22	5	8	2	1700	2.23	10	0.680	14	-1.34
23	5	9	3	1700	1.01	11	0.777	14	9.44
24	5	10	4	1700	0.51	11	0.635	17	-5.12
25	6	8	1	2100	8.34	7	0.699	10	-0.14
26	6	9	2	2100	2.37	9	0.854	10	5.46
27	6	10	3	2100	0.96	9	0.708	12	-0.84
28	6	11	4	2100	0.93	17	1.050	16	0.11
29	7	9	1	2800	73.23	49	1.045	46	2.73
30	7	10	2	2800	15.42	42	0.881	47	4.30
31	7	11	3	2800	11.19	75	1.287	58	3.76
32	7	12	4	2800	3.62	49	0.881	55	5.26
33	8	10	1	2800	70.76	48	0.710	67	7.52
34	8	11	2	2800	38.41	103	1.080	95	7.31
35	8	12	3	2100	8.28	74	0.712	103	8.57
36	8	13	4	1600	4.62	109	0.762	143	9.48
37	9	11	1	2400	106.72	84	1.579	53	4.87
38	9	12	2	2100	18.19	65	0.867	74	6.16
39	9	13	3	1600	8.86	104	0.890	116	7.91
40	9	14	4	1300	4.36	127	0.914	138	6.83
41	10	12	1	2100	61.58	55	0.571	96	4.35
42	10	13	2	1600	20.59	97	0.639	151	5.84
43	10	14	3	1300	9.03	131	0.676	193	5.64
44	10	15	4	1200	5.78	182	0.718	253	8.80
45	11	13	1	1600	97.42	115	1.217	94	4.63
46	11	14	2	1300	31.28	181	1.149	157	4.71
47	11	15	3	1200	17.00	267	1.158	230	7.53
48	11	16	4	1300	5.52	160	1.273	125	8.10
49	12	14	1	1300	50.61	73	0.750	97	3.14
50	12	15	2	1200	16.04	101	0.792	127	5.07

IP data of Line-C in S. Imbak Sub-area (2)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resis1 (ohm-m)	Tcf	Resis2 (ohm-m)	Charge. (mV/V)
51	12	16	3	2100	11.34	102	0.869	117	10.12
52	12	17	4	2100	7.10	127	0.915	138	12.84
53	13	15	1	1200	99.45	156	1.088	143	3.98
54	13	16	2	1600	25.40	120	1.120	107	5.03
55	13	17	3	1600	13.39	158	1.130	139	12.94
56	13	18	4	1600	5.41	128	1.347	95	20.24
57	14	16	1	1300	184.48	267	0.910	293	8.71
58	14	17	2	1300	39.96	115	0.940	122	10.51
59	14	18	3	1300	11.60	168	1.106	151	15.32
60	14	19	4	1300	2.04	59	1.001	58	20.00
61	15	17	1	1200	292.03	458	1.041	439	11.50
62	15	18	2	1200	38.95	245	1.171	209	22.64
63	15	19	3	1200	5.37	84	1.024	82	23.09
64	15	20	4	500	0.65	49	0.511	95	22.04
65	16	18	1	1300	210.91	306	1.099	278	16.31
66	16	19	2	1300	9.09	53	0.928	57	22.47
67	16	20	3	500	0.72	28	0.466	60	21.49
68	16	21	4	730	1.81	93	0.658	141	17.44
69	17	19	1	1300	50.00	73	0.847	86	18.71
70	17	20	2	500	2.66	41	0.445	92	12.34
71	17	21	3	730	5.22	134	0.665	201	19.78
72	17	22	4	680	1.49	76	0.795	95	23.80
73	18	20	1	500	58.17	221	0.541	408	13.87
74	18	21	2	730	61.78	628	0.913	687	15.67
75	18	22	3	680	13.67	349	1.087	321	23.55
76	18	23	4	600	1.28	85	0.945	89	15.74
77	19	21	1	500	304.77	1110	1.322	839	11.71
78	19	22	2	500	41.78	582	1.395	417	20.85
79	19	23	3	500	3.80	151	1.144	131	12.97
80	19	24	4	500	0.82	59	1.180	50	20.62
81	20	22	1	500	471.19	1708	0.953	1792	19.06
82	20	23	2	500	24.56	412	0.767	537	19.42
83	20	24	3	500	4.23	159	0.775	205	24.77
84	21	23	1	730	417.66	1301	0.842	1545	17.00
85	21	24	2	730	58.99	632	0.897	704	22.10
86	22	24	1	680	249.80	617	1.046	589	16.81

IP data of Line-D in S. Imbak Sub-area (1)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resis1 (ohm-m)	Tcf	Resis2 (ohm-m)	Charge. (mV/V)
1	0	2	1	3000	23.84	15	0.912	16	0.66
2	0	3	2	3000	4.14	10	0.903	11	1.06
3	0	4	3	3500	3.22	17	1.127	15	0.21
4	0	5	4	3900	1.95	19	1.156	16	0.24
5	1	3	1	3000	17.74	11	1.002	10	0.29
6	1	4	2	3500	8.33	18	1.232	14	0.06
7	1	5	3	3900	3.84	19	1.229	15	0.22
8	1	6	4	2900	1.84	24	1.412	16	-0.05
9	2	4	1	3500	37.84	20	1.172	17	0.45
10	2	5	2	3900	9.66	19	1.089	17	0.19
11	2	6	3	2900	3.38	22	1.209	18	1.38
12	2	7	4	2600	1.97	29	0.992	29	-0.21
13	3	5	1	3900	23.23	11	0.962	11	-0.09
14	3	6	2	2900	4.60	12	1.050	11	0.81
15	3	7	3	2600	2.36	17	0.856	19	3.24
16	3	8	4	3500	1.63	18	0.909	19	-0.82
17	4	6	1	2900	21.73	14	1.094	12	0.59
18	4	7	2	3500	9.51	20	0.890	22	0.19
19	4	8	3	3500	3.85	21	0.957	21	-0.64
20	4	9	4	3500	1.78	19	0.900	21	-4.11
21	5	7	1	3900	34.31	17	0.782	21	0.39
22	5	8	2	3900	9.53	18	0.893	20	0.12
23	5	9	3	3900	3.60	17	0.848	20	-1.28
24	5	10	4	3900	3.24	31	0.800	38	1.40
25	6	8	1	2900	35.81	23	1.151	19	1.81
26	6	9	2	2900	8.38	22	1.063	20	0.34
27	6	10	3	2900	6.17	40	1.005	39	1.61
28	6	11	4	2900	1.39	18	0.571	31	7.86
29	7	9	1	2600	27.90	20	0.862	23	0.41
30	7	10	2	2600	15.87	46	0.856	53	1.13
31	7	11	3	2600	3.06	22	0.492	44	9.26
32	7	12	4	2600	2.36	34	0.917	37	11.03
33	8	10	1	3500	87.17	47	0.994	47	1.01
34	8	11	2	3500	11.46	25	0.587	42	7.34
35	8	12	3	1600	3.62	43	1.120	38	8.62
36	8	13	4	1500	1.47	37	1.090	33	14.69
37	9	11	1	3400	65.68	36	0.668	53	7.70
38	9	12	2	1600	14.02	66	1.318	50	8.98
39	9	13	3	1450	16.72	217	1.216	178	10.45
40	9	14	4	1200	1.17	37	0.947	39	15.16
41	10	12	1	1600	93.01	110	1.550	70	14.64
42	10	13	2	1500	20.85	105	1.221	85	18.91
43	10	14	3	1200	4.37	69	0.930	74	21.36
44	10	15	4	1150	1.61	53	1.359	38	20.23
45	11	13	1	1500	31.03	39	0.693	56	27.59
46	11	14	2	1350	5.23	29	0.567	51	29.23
47	11	15	3	1350	5.18	72	0.832	86	21.93
48	11	16	4	1400	0.50	14	0.645	21	89.52
49	12	14	1	1350	22.35	31	0.853	36	30.42
50	12	15	2	1350	26.35	147	1.309	112	32.63

IP data of Line-D in S. Imbak Sub-area (2)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resis1 (ohm-m)	Tcf	Resis2 (ohm-m)	Charge. (mV/V)
51	12	16	3	1600	1.26	15	1.012	14	44.97
52	12	17	4	1600	0.77	18	1.385	12	11.25
53	13	15	1	1200	99.45	156	1.088	143	3.98
54	13	16	2	1500	2.68	14	1.013	13	34.07
55	13	17	3	1500	1.08	13	1.359	9	34.39
56	13	18	4	1450	1.99	52	0.968	53	27.98
57	14	16	1	1200	8.86	14	0.673	20	31.65
58	14	17	2	1200	1.80	11	0.961	11	19.06
59	14	18	3	1200	0.95	15	0.679	22	14.61
60	14	19	4	1200	0.26	8	0.768	10	22.01
61	15	17	1	1150	20.67	34	1.562	21	22.66
62	15	18	2	1300	4.74	28	0.965	29	20.15
63	15	19	3	1300	1.01	15	1.105	13	27.54
64	15	20	4	600	0.26	16	1.275	12	23.01
65	16	18	1	1200	8.80	14	0.613	22	15.43
66	16	19	2	1200	1.01	7	0.776	9	16.59
67	16	20	3	600	0.37	12	0.943	12	17.42
68	16	21	4	880	0.32	14	0.858	16	18.53
69	17	19	1	1200	11.57	18	1.173	15	20.06
70	17	20	2	600	2.59	32	1.375	23	16.01
71	17	21	3	880	1.94	41	1.213	33	15.58
72	17	22	4	400	0.23	21	0.999	21	19.63
73	18	20	1	600	25.05	79	1.092	72	23.36
74	18	21	2	880	8.65	74	0.927	79	23.97
75	18	22	3	400	0.68	32	0.757	42	28.00
76	18	23	4	400	0.50	46	0.919	50	15.34
77	19	21	1	880	19.01	41	0.824	49	24.74
78	19	22	2	400	0.97	18	0.727	24	27.09
79	19	23	3	400	0.54	25	0.886	28	0.86
80	19	24	4	850	0.26	12	0.657	18	-89.38
81	20	22	1	475	3.53	14	1.011	13	21.88
82	20	23	2	400	1.55	28	1.176	23	19.50
83	20	24	3	950	0.52	11	0.837	13	24.81
84	20	25	4	1164	0.52	16	0.936	17	-27.83
85	21	23	1	880	34.68	73	1.166	62	18.78
86	21	24	2	1150	3.48	23	0.784	29	6.78
87	21	25	3	1330	1.89	26	0.863	30	7.37
88	21	26	4	1500	0.43	11	0.285	38	7.93
89	22	24	1	550	4.79	18	0.664	27	26.26
90	22	25	2	1050	1.67	14	0.749	18	-9.04
91	22	26	3	400	0.18	9	0.270	33	28.64
92	22	27	4	900	0.48	11	0.766	14	7.06
93	23	25	1	910	9.68	32	0.860	37	8.93
94	23	26	2	400	0.85	16	0.505	31	20.29
95	23	27	3	900	0.27	12	1.214	9	11.32
96	23	28	4	400	0.76	71	1.585	44	14.78
97	24	26	1	850	7.13	19	0.750	25	26.98
98	24	27	2	850	1.77	16	1.403	11	11.24
99	24	28	3	580	1.62	54	1.541	35	11.06
100	24	29	4	580	-0.37	24	1.507	15	10.76

IP data of Line-D in S. Imbak Sub-area (3)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resis1 (ohm-m)	Tcf	Resis2 (ohm-m)	Charge. (mV/V)
101	25	27	1	1450	291.22	375	1.794	209	27.86
102	25	28	2	1450	44.77	229	1.531	149	22.04
103	25	29	3	1450	6.17	79	1.385	57	-8.42
104	25	30	4	1450	1.46	36	1.166	30	29.42
105	26	28	1	1500	254.44	319	0.674	473	26.68
106	26	29	2	1500	8.80	44	0.582	75	37.22
107	26	30	3	1500	1.63	20	0.467	42	44.19
108	27	29	1	1800	30.99	32	0.959	33	25.38
109	27	30	2	1800	4.31	18	0.826	21	25.25
110	28	30	1	2100	42.32	38	0.725	52	29.70

IP data of Line-E in S. Imbak Sub-area (1)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resis1 (ohm-m)	Tcf	Resis2 (ohm-m)	Charge. (mV/V)
1	0	2	1	1500	13.19	17	0.912	18	0.65
2	0	3	2	2100	4.81	17	0.974	17	0.25
3	0	4	3	2700	2.85	20	1.031	19	-7.37
4	0	5	4	2800	1.84	25	0.872	28	-1.24
5	1	3	1	2100	16.98	15	1.001	14	0.85
6	1	4	2	2700	5.45	15	1.056	14	0.53
7	1	5	3	2800	2.65	18	0.888	20	0.18
8	1	6	4	2600	2.06	30	1.059	28	0.22
9	2	4	1	2700	26.69	19	0.988	19	0.81
10	2	5	2	2800	7.67	21	0.842	24	-1.06
11	2	6	3	2600	4.33	31	1.016	30	-0.60
12	2	7	4	3000	8.59	108	1.209	89	-0.37
13	3	5	1	2800	35.61	24	0.856	28	0.20
14	3	6	2	2600	11.10	32	1.072	29	0.02
15	3	7	3	2600	5.39	39	1.243	31	1.48
16	3	8	4	2700	2.77	39	1.130	34	2.20
17	4	6	1	2600	58.31	42	1.233	34	1.18
18	4	7	2	2700	13.52	38	1.301	29	0.57
19	4	8	3	2700	4.79	33	1.144	28	0.24
20	4	9	4	2700	2.60	36	1.059	33	3.66
21	5	7	1	2800	71.00	48	1.055	45	-0.27
22	5	8	2	2800	15.10	41	0.907	45	2.04
23	5	9	3	2800	6.69	45	0.835	53	3.99
24	5	10	4	2800	2.59	35	0.602	58	13.27
25	6	8	1	2600	171.69	124	0.835	148	8.87
26	6	9	2	2600	21.74	63	0.818	77	4.85
27	6	10	3	2600	7.16	52	0.616	84	14.96
28	6	11	4	2600	3.00	43	0.741	58	23.15
29	7	9	1	2600	132.03	96	1.028	93	2.59
30	7	10	2	2600	33.78	98	0.798	122	11.98
31	7	11	3	2600	11.50	83	0.969	85	20.93
32	7	12	4	2600	3.67	53	1.818	29	31.30
33	8	10	1	2700	123.78	86	0.750	114	7.97
34	8	11	2	2700	33.98	95	0.975	97	16.94
35	8	12	3	1700	5.79	64	1.755	36	27.67
36	8	13	4	2000	1.50	28	0.985	28	30.98
37	9	11	1	2400	203.99	160	1.302	122	10.20
38	9	12	2	1700	27.43	122	1.945	62	21.02
39	9	13	3	2000	4.66	44	0.980	44	26.10
40	9	14	4	2000	1.38	13	0.700	18	30.14
41	10	12	1	1700	94.06	104	1.211	85	22.37
42	10	13	2	2000	8.48	32	0.557	57	25.24
43	10	14	3	2000	2.10	20	0.422	47	28.99
44	10	15	4	1700	0.69	15	0.465	32	35.40
45	11	13	1	2000	28.40	27	0.488	55	31.89
46	11	14	2	2000	4.64	18	0.423	42	35.14
47	11	15	3	1700	1.41	16	0.488	32	38.88
48	11	16	4	1400	0.84	23	1.047	21	34.03
49	12	14	1	2000	17.76	17	0.988	17	27.45
50	12	15	2	1700	3.98	18	1.119	16	30.94

IP data of Line-E in S. Imbak Sub-area (2)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resis1 (ohm-m)	Tcf	Resis2 (ohm-m)	Charge. (mV/V)
51	12	16	3	1700	2.35	26	2.265	11	34.45
52	12	17	4	1700	0.51	11	0.884	12	25.42
53	13	15	1	1700	21.64	24	0.900	26	30.87
54	13	16	2	2000	7.21	27	1.705	15	27.39
55	13	17	3	2000	1.03	10	0.583	17	31.14
56	13	18	4	2000	0.59	12	0.923	13	26.74
57	14	16	1	2000	31.79	30	1.478	20	25.88
58	14	17	2	2000	1.87	7	0.427	16	26.54
59	14	18	3	2000	0.70	7	0.718	9	13.29
60	14	19	4	2000	0.31	6	0.546	10	23.00
61	15	17	1	1700	4.76	5	0.291	17	27.03
62	15	18	2	1700	1.11	5	0.629	7	32.60
63	15	19	3	1700	0.45	5	0.490	10	24.20
64	15	20	4	830	0.15	7	0.521	13	23.72
65	16	18	1	1400	38.50	53	1.431	37	21.96
66	16	19	2	1400	7.23	38	1.049	36	23.61
67	16	20	3	830	1.92	43	1.066	40	16.66
68	16	21	4	900	0.99	41	1.516	27	18.43
69	17	19	1	1600	41.70	46	0.702	65	23.82
70	17	20	2	830	3.19	29	0.702	41	19.21
71	17	21	3	680	0.95	26	0.964	26	14.83
72	17	22	4	710	0.27	14	0.694	20	12.19
73	18	20	1	830	31.15	71	0.966	73	16.85
74	18	21	2	680	3.39	38	1.313	28	14.90
75	18	22	3	710	0.75	20	0.922	21	11.76
76	18	23	4	680	0.47	26	1.356	19	18.73
77	19	21	1	680	157.90	437	1.081	404	18.47
78	19	22	2	710	4.72	50	0.748	66	21.48
79	19	23	3	680	1.80	49	1.082	45	21.92
80	19	24	4	830	0.94	42	1.358	30	19.20
81	20	22	1	830	45.75	103	0.682	151	16.40
82	20	23	2	830	9.87	89	1.049	84	27.03
83	20	24	3	830	2.67	60	1.275	47	15.10
84	20	25	4	830	0.85	39	0.794	49	10.36
85	21	23	1	830	211.89	482	1.551	310	17.68
86	21	24	2	866	16.57	144	1.552	92	19.14
87	21	25	3	866	2.36	51	0.916	55	23.42
88	21	26	4	680	0.69	38	0.755	50	16.23
89	22	24	1	710	19.34	51	0.924	55	19.89
90	22	25	2	710	1.79	19	0.547	34	18.07
91	22	26	3	710	0.55	14	0.463	30	24.26
92	22	27	4	1170	0.22	7	0.205	34	0.69
93	23	25	1	680	37.70	104	0.659	157	26.67
94	23	26	2	680	3.94	43	0.617	69	25.88
95	23	27	3	1207	1.21	18	0.272	66	-49.85
96	23	28	4	1500	1.98	49	0.926	52	26.99
97	24	26	1	1000	48.14	91	0.940	96	23.23
98	24	27	2	1350	4.47	25	0.415	60	15.85
99	24	28	3	1100	5.43	93	1.491	62	22.11
100	24	29	4	1100	1.49	51	1.503	33	17.66

IP data of Line-E in S. Imbak Sub-area (3)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resis1 (ohm-m)	Tcf	Resis2 (ohm-m)	Charge. (mV/V)
101	25	27	1	1350	22.20	31	0.424	73	34.26
102	25	28	2	1100	14.26	98	1.682	58	25.29
103	25	29	3	1100	2.70	46	1.431	32	15.36
104	25	30	4	1100	3.32	113	1.586	71	15.28
105	26	28	1	1000	144.14	271	1.901	142	20.58
106	26	29	2	1000	7.71	58	1.219	47	22.73
107	26	30	3	1000	6.85	129	1.285	100	15.28
108	26	31	4	1000	2.40	102	1.182	86	19.48
109	27	29	1	1350	19.85	28	0.538	52	30.99
110	27	30	2	1350	12.62	71	0.627	113	19.93
111	27	31	3	1350	3.28	51	0.568	89	28.67
112	28	30	1	1230	132.88	203	1.039	195	22.98
113	28	31	2	1230	21.36	143	1.010	141	27.05
114	29	31	1	1250	137.04	220	0.967	227	16.77

IP data of Line-F in S. Imbak Sub-area (1)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resis1 (ohm-m)	Tcf	Resis2 (ohm-m)	Charge. (mV/V)
1	0	2	1	1800	32.93	34	1.128	30	1.77
2	0	3	2	1500	8.26	42	0.951	44	2.96
3	0	4	3	1300	2.48	36	1.733	20	3.96
4	0	5	4	1600	0.99	23	1.260	18	-3.53
5	1	3	1	1500	22.98	29	0.840	34	2.15
6	1	4	2	1300	3.89	23	1.502	15	4.38
7	1	5	3	1600	1.26	15	1.012	14	0.10
8	1	6	4	1900	0.78	15	0.781	19	-30.81
9	2	4	1	1300	47.88	69	1.628	42	5.57
10	2	5	2	1600	8.00	38	0.880	43	-2.62
11	2	6	3	1900	3.13	31	0.695	44	-3.38
12	2	7	4	1800	1.76	37	0.461	80	-7.25
13	3	5	1	1600	103.25	122	0.579	210	11.40
14	3	6	2	1900	25.03	99	0.524	188	4.59
15	3	7	3	1500	9.04	114	0.358	318	1.31
16	3	8	4	1500	5.25	132	0.515	256	26.57
17	4	6	1	1900	39.96	40	0.934	42	1.78
18	4	7	2	1300	9.24	54	0.687	78	-1.69
19	4	8	3	1300	4.83	70	1.027	68	23.69
20	4	9	4	1300	1.31	38	1.384	27	40.77
21	5	7	1	1600	59.42	70	0.822	85	-0.52
22	5	8	2	1600	19.93	94	1.216	77	22.58
23	5	9	3	1600	3.17	37	1.520	24	32.20
24	5	10	4	1600	0.90	21	1.475	14	34.70
25	6	8	1	1900	136.72	136	1.208	112	22.26
26	6	9	2	1900	11.05	44	1.369	32	39.00
27	6	10	3	1900	2.33	23	1.256	18	38.58
28	6	11	4	1900	0.30	6	0.919	6	38.97
29	7	9	1	2100	41.80	38	0.943	40	39.54
30	7	10	2	2100	5.13	18	0.869	20	45.19
31	7	11	3	2100	0.53	5	0.606	8	46.64
32	7	12	4	2100	0.92	17	0.964	17	21.49
33	8	10	1	1800	18.41	19	0.864	21	72.14
34	8	11	2	1800	0.86	4	0.631	6	74.75
35	8	12	3	2000	1.18	11	1.052	10	47.54
36	8	13	4	1600	0.43	10	0.663	15	60.94
37	9	11	1	1800	4.33	5	0.772	6	73.53
38	9	12	2	2000	2.05	8	1.366	5	51.76
39	9	13	3	1600	0.56	7	0.816	8	53.11
40	9	14	4	1150	0.08	3	0.591	5	152.79
41	10	12	1	2300	22.73	19	1.154	16	46.61
42	10	13	2	1900	2.34	9	0.684	13	46.46
43	10	14	3	1350	0.24	3	0.532	5	49.72
44	10	15	4	2700	2.77	39	1.130	34	2.20
45	11	13	1	1900	3.40	3	0.577	5	36.71
46	11	14	2	2700	13.52	38	1.301	29	0.57
47	11	15	3	2700	4.79	33	1.144	28	0.24
48	11	16	4	2700	2.60	36	1.059	33	3.66
49	12	14	1	1350	10.95	15	0.845	17	38.55
50	12	15	2	1400	0.62	3	0.514	5	-7.23

IP data of Line-F in S. Imbak Sub-area (2)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resis1 (ohm-m)	Tcf	Resis2 (ohm-m)	Charge. (mV/V)
51	12	16	3	2300	0.76	6	1.272	4	20.19
52	12	17	4	2300	0.49	8	1.811	4	20.81
53	13	15	1	1400	4.97	7	0.871	8	26.21
54	13	16	2	1900	3.21	13	1.686	7	23.66
55	13	17	3	1900	1.51	15	1.922	7	25.37
56	13	18	4	1900	0.99	20	2.229	8	25.29
57	14	16	1	1350	260.91	364	1.399	260	23.75
58	14	17	2	1350	17.65	99	1.320	74	20.67
59	14	18	3	1350	6.34	89	1.371	64	22.03
60	14	19	4	1350	1.30	36	1.126	31	23.00
61	15	17	1	1400	50.25	68	0.902	75	18.07
62	15	18	2	1400	5.44	29	0.892	32	22.36
63	15	19	3	1400	0.88	12	0.710	16	22.78
64	15	20	4	1000	0.12	5	0.456	10	-3.47
65	16	18	1	2000	58.55	55	1.020	53	22.98
66	16	19	2	2000	5.31	20	0.857	23	20.68
67	16	20	3	1000	0.51	10	0.676	14	4.42
68	16	21	4	1510	0.54	13	0.530	24	18.59
69	17	19	1	2100	25.12	23	0.726	31	19.74
70	17	20	2	1000	1.82	14	0.645	21	11.85
71	17	21	3	1510	1.43	18	0.527	34	11.39
72	17	22	4	2000	0.35	7	0.490	14	11.89
73	18	20	1	1000	6.88	13	0.848	15	10.88
74	18	21	2	1510	4.09	20	0.733	27	12.80
75	18	22	3	2000	0.98	9	0.687	13	17.54
76	18	23	4	1600	0.34	9	0.643	13	16.86
77	19	21	1	1510	32.76	40	0.940	42	16.94
78	19	22	2	2000	4.44	16	0.855	18	21.18
79	19	23	3	1600	1.32	17	0.773	21	25.35
80	19	24	4	1082	0.45	12	0.801	14	17.82
81	20	22	1	1000	-8.38	16	0.913	17	21.21
82	20	23	2	1000	2.72	23	0.806	28	22.17
83	20	24	3	1000	4.84	71	0.801	88	58.79
84	20	25	4	1000	0.74	37	1.288	28	16.97
85	21	23	1	1510	80.56	107	0.945	113	17.54
86	21	24	2	1510	12.07	45	0.853	52	-8.35
87	21	25	3	1510	7.79	129	1.304	98	17.82
88	21	26	4	1510	2.43	55	0.743	74	21.80
89	22	24	1	2000	185.29	123	0.811	151	15.51
90	22	25	2	2000	32.49	164	1.242	132	18.83
91	22	26	3	2000	6.05	51	0.651	78	22.85
92	22	27	4	2000	1.00	17	0.430	39	29.61
93	23	25	1	1600	232.72	518	1.185	437	13.81
94	23	26	2	1600	21.47	112	0.580	193	20.03
95	23	27	3	1600	1.87	25	0.397	62	30.57
96	23	28	4	1600	3.88	101	0.665	151	22.62
97	24	26	1	1200	51.35	45	0.472	95	17.51
98	24	27	2	1600	3.50	11	0.378	29	-3.37
99	24	28	3	1450	4.55	42	0.654	64	25.26
100	24	29	4	1550	2.17	38	0.856	44	21.77

IP data of Line-F in S. Imbak Sub-area (3)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resis1 (ohm-m)	Tcf	Resis2 (ohm-m)	Charge. (mV/V)
101	25	27	1	1600	40.23	54	0.696	77	27.68
102	25	28	2	1450	31.05	189	1.246	151	23.41
103	25	29	3	1550	10.56	154	1.519	101	22.93
104	25	30	4	1000	7.90	365	2.170	168	20.83
105	26	28	1	1200	315.23	488	1.646	296	7.75
106	26	29	2	1200	44.89	277	1.466	188	11.38
107	26	30	3	1200	29.52	458	1.800	254	17.32
108	26	31	4	1200	9.83	362	1.395	259	19.86
109	27	29	1	1600	189.90	224	0.774	289	7.23
110	27	30	2	1600	66.62	316	0.967	326	14.76
111	27	31	3	1600	16.27	215	0.726	296	19.93
112	28	30	1	1450	401.03	522	1.090	478	10.62
113	28	31	2	1450	69.55	400	0.840	476	16.98
114	29	31	1	1550	187.44	240	0.770	311	11.16

IP data of Line-G in S. Imbak Sub-area (1)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resis1 (ohm-m)	Tcf	Resis2 (ohm-m)	Charge. (mV/V)
1	0	2	1	4000	16.37	8	0.828	9	0.51
2	0	3	2	2900	3.33	9	0.964	9	0.56
3	0	4	3	2400	1.03	8	0.983	8	1.19
4	0	5	4	1800	0.33	7	0.865	8	0.03
5	1	3	1	2900	11.41	7	1.167	5	0.29
6	1	4	2	2400	2.20	7	1.135	6	0.18
7	1	5	3	1800	0.58	6	0.989	6	1.03
8	1	6	4	1700	0.34	8	0.984	8	-5.37
9	2	4	1	2600	10.06	7	0.946	7	0.66
10	2	5	2	1800	1.64	7	0.834	8	0.21
11	2	6	3	1700	0.76	8	0.843	9	-0.26
12	2	7	4	2100	0.46	8	0.783	10	0.54
13	3	5	1	1800	7.33	8	0.968	8	0.92
14	3	6	2	1700	2.11	9	0.989	9	-2.25
15	3	7	3	2100	1.02	9	0.916	9	0.89
16	3	8	4	2000	0.52	10	1.189	8	-1.60
17	4	6	1	1700	9.10	10	1.041	9	0.35
18	4	7	2	2080	2.38	9	0.958	9	-0.09
19	4	8	3	1960	0.99	10	1.238	8	0.62
20	4	9	4	2000	0.40	8	0.952	8	1.46
21	5	7	1	1880	8.79	9	0.969	9	1.05
22	5	8	2	1880	2.10	8	1.223	6	-0.66
23	5	9	3	1900	0.71	7	0.920	7	-12.26
24	5	10	4	1900	0.32	6	1.134	5	2.35
25	6	8	1	1750	23.93	26	1.147	22	-3.16
26	6	9	2	1750	2.15	9	0.846	10	-5.86
27	6	10	3	1750	0.76	8	1.049	7	-0.23
28	6	11	4	1750	0.49	11	1.275	8	-0.30
29	7	9	1	1700	16.79	19	0.734	25	-1.48
30	7	10	2	1700	2.19	10	0.964	10	-0.64
31	7	11	3	2100	1.19	11	1.159	9	1.37
32	7	12	4	2100	3.53	63	1.181	53	2.11
33	8	10	1	1600	46.96	55	1.233	44	1.88
34	8	11	2	1950	5.46	21	1.395	15	-0.56
35	8	12	3	1950	9.32	90	1.354	66	1.85
36	8	13	4	2100	9.39	169	0.841	200	1.93
37	9	11	1	2000	27.07	26	0.907	28	-0.09
38	9	12	2	2000	19.67	74	0.875	84	4.12
39	9	13	3	2100	18.20	163	0.545	299	2.48
40	9	14	4	1600	0.90	21	0.617	34	6.58
41	10	12	1	2000	59.19	56	0.950	58	2.50
42	10	13	2	1600	8.23	39	0.612	63	6.47
43	10	14	3	1600	1.90	22	0.726	30	6.73
44	10	15	4	2000	0.85	16	0.637	25	2.15
45	11	13	1	1600	42.70	50	0.635	78	9.18
46	11	14	2	1600	7.75	37	0.858	43	9.59
47	11	15	3	2000	3.33	31	0.769	40	0.87
48	11	16	4	2500	2.93	44	1.058	41	5.49
49	12	14	1	1600	127.97	151	1.177	128	10.56
50	12	15	2	2000	37.25	140	1.027	136	5.45

IP data of Line-G in S. Imbak Sub-area (2)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resis1 (ohm-m)	Tcf	Resis2 (ohm-m)	Charge. (mV/V)
51	12	16	3	2500	31.49	237	1.381	171	3.77
52	12	17	4	2700	16.09	225	1.104	203	4.82
53	13	15	1	2000	61.71	58	0.861	67	8.56
54	13	16	2	2500	25.83	78	1.133	68	6.14
55	13	17	3	2700	11.98	84	0.856	98	8.17
56	13	18	4	1600	5.15	121	0.661	183	14.61
57	14	16	1	1600	55.59	65	1.202	54	1.99
58	14	17	2	1600	10.52	50	0.867	57	1.05
59	14	18	3	1600	5.42	64	0.682	93	5.03
60	14	19	4	1600	3.28	77	1.047	73	17.17
61	15	17	1	2000	43.52	41	0.666	61	-0.13
62	15	18	2	2000	12.63	48	0.580	82	4.58
63	15	19	3	2000	7.68	72	0.912	78	13.82
64	15	20	4	1900	1.06	21	0.668	31	21.11
65	16	18	1	2500	121.75	92	0.776	118	8.39
66	16	19	2	2500	57.39	173	1.283	134	14.14
67	16	20	3	1900	6.03	59	0.909	64	22.65
68	16	21	4	1600	1.12	26	1.191	21	24.91
69	17	19	1	2700	358.82	251	1.473	170	25.67
70	17	20	2	1900	26.61	105	0.881	119	35.98
71	17	21	3	1600	4.60	54	1.117	48	38.87
72	17	22	4	1610	0.96	22	1.314	16	38.58
73	18	20	1	1900	107.16	106	0.596	177	23.39
74	18	21	2	1600	16.20	76	0.818	92	27.18
75	18	22	3	1905	3.65	36	0.950	37	27.15
76	18	23	4	2050	2.65	49	0.706	69	23.64
77	19	21	1	1600	109.54	129	1.425	90	26.59
78	19	22	2	1905	10.68	42	1.428	29	30.51
79	19	23	3	2050	6.87	63	1.010	62	24.80
80	19	24	4	2026	0.06	1	0.413	2	47.08
81	20	22	1	1900	23.50	23	0.897	25	25.17
82	20	23	2	2050	7.09	26	0.640	40	18.58
83	20	24	3	1826	0.05	0	0.269	0	61.16
84	20	25	4	1900	0.10	2	0.502	3	22.59
85	21	23	1	2050	22.13	20	0.714	28	20.99
86	21	24	2	1640	0.06	0	0.337	0	92.89
87	21	25	3	1450	0.12	2	0.635	3	26.02
88	21	26	4	1360	0.00	2	1.151	1	78.26
89	22	24	1	1650	0.97	1	0.462	2	-1.42
90	22	25	2	1432	1.65	9	1.025	8	7.35
91	22	26	3	1467	0.44	6	1.779	3	-82.72
92	22	27	4	1381	1.02	30	1.912	15	3.38
93	23	25	1	1300	939.82	1394	2.120	657	23.76
94	23	26	2	1360	24.04	133	2.129	62	16.19
95	23	27	3	1210	8.86	137	1.851	74	11.80
96	23	28	4	1200	2.63	83	1.294	64	14.28
97	24	26	1	1360	19.92	27	0.829	32	12.99
98	24	27	2	1210	3.69	23	0.690	33	11.85
99	24	28	3	1200	0.75	12	0.467	25	9.23
100	24	29	4	1680	0.87	19	0.624	30	13.79

IP data of Line-G in S. Imbak Sub-area (3)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resis1 (ohm-m)	Tcf	Resis2 (ohm-m)	Charge. (mV/V)
101	25	27	1	1210	15.22	24	0.894	26	11.36
102	25	28	2	1200	1.88	12	0.642	18	10.68
103	25	29	3	1700	2.45	27	0.904	29	7.44
104	25	30	4	1700	1.33	29	0.853	33	9.76
105	26	28	1	1360	5.66	8	0.785	10	7.58
106	26	29	2	1360	3.34	19	1.200	15	6.44
107	26	30	3	1360	1.44	20	1.123	17	9.64
108	26	31	4	1300	1.05	26	1.214	21	8.30
109	27	29	1	1210	59.58	92	1.243	74	18.24
110	27	30	2	1210	9.27	57	1.105	51	21.32
111	27	31	3	1300	3.40	43	1.144	37	16.86
112	27	32	4	1400	0.35	13	0.058	224	17.00
113	28	30	1	1200	32.66	51	0.900	56	20.46
114	28	31	2	1300	5.85	30	0.910	32	18.74
115	28	32	3	1400	0.30	6	0.017	352	12.67
116	28	33	4	1850	0.21	4	0.207	19	11.05
117	29	31	1	1300	51.99	70	0.982	71	20.10
118	29	32	2	1400	1.48	12	0.010	1200	19.57
119	29	33	3	1850	1.01	10	0.268	37	17.86
120	29	34	4	1800	1.19	23	0.848	27	19.22
121	30	32	1	1400	6.71	16	0.046	347	19.56
122	30	33	2	1850	3.82	15	0.390	38	16.16
123	30	34	3	1800	4.22	42	1.182	35	24.32
124	30	35	4	2000	1.25	27	0.709	38	11.37
125	31	33	1	1850	192.81	109	0.988	110	16.40
126	31	34	2	1800	99.74	268	2.631	101	20.89
127	31	35	3	2000	15.50	123	1.303	94	26.02
128	31	36	4	1550	9.98	178	1.799	98	14.77
129	32	34	1	1800	269.96	317	1.561	203	19.39
130	32	35	2	2000	18.66	103	0.548	187	24.91
131	32	36	3	1550	6.41	96	0.635	151	19.05
132	32	37	4	1400	3.65	123	0.915	134	22.14
133	33	35	1	2000	32.37	39	0.332	117	24.78
134	33	36	2	1700	7.69	34	0.588	57	17.85
135	33	37	3	1625	5.08	58	0.635	91	20.78
136	33	38	4	1850	3.28	66	0.915	72	26.59
137	34	36	1	1800	49.75	45	1.132	39	18.06
138	34	37	2	1800	26.29	94	1.397	67	25.92
139	34	38	3	1800	11.90	109	1.890	57	17.89
130	34	39	4	1800	6.17	113	2.382	47	26.68
131	35	37	1	2000	17.05	17	1.216	13	13.78
132	35	38	2	2000	6.60	26	1.341	19	51.23
133	35	39	3	2000	6.98	70	1.494	46	26.04
134	36	38	1	1550	236.88	287	0.913	314	14.09
135	36	39	2	1550	27.85	135	0.996	135	20.09
136	37	39	1	1100	116.34	199	0.986	201	20.93

IP data of Line-H in S. Imbak Sub-area (1)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resis1 (ohm-m)	Tcf	Resis2 (ohm-m)	Charge. (mV/V)
1	0	2	1	2600	17.14	12	1.135	10	1.07
2	0	3	2	2500	3.57	11	0.968	11	1.20
3	0	4	3	4250	1.78	8	0.924	8	1.48
4	0	5	4	2700	0.63	9	0.828	10	4.25
5	1	3	1	2500	14.04	11	0.887	12	0.76
6	1	4	2	4200	4.32	8	0.871	9	0.20
7	1	5	3	2700	1.28	9	0.792	11	-0.05
8	1	6	4	2400	0.58	9	1.084	8	5.45
9	2	4	1	4200	16.49	7	1.003	6	0.83
10	2	5	2	2700	3.42	10	0.933	10	-0.04
11	2	6	3	2400	1.25	10	1.275	7	-1.70
12	2	7	4	1800	0.56	12	1.186	10	1.65
13	3	5	1	2700	16.38	11	1.000	11	0.43
14	3	6	2	2400	3.40	11	1.308	8	1.78
15	3	7	3	3100	1.98	12	1.164	10	0.79
16	3	8	4	2090	0.65	12	1.243	9	-0.46
17	4	6	1	2400	11.01	9	1.327	6	0.57
18	4	7	2	3100	3.70	9	1.059	8	0.78
19	4	8	3	3600	1.59	8	1.113	7	1.20
20	4	9	4	4100	0.68	6	1.021	5	0.50
21	5	7	1	2250	12.25	10	0.808	12	0.24
22	5	8	2	2250	2.68	9	0.882	10	-0.20
23	5	9	3	2650	0.92	7	0.811	8	-0.14
24	5	10	4	2650	0.62	9	0.893	10	-1.01
25	6	8	1	1600	6.89	8	1.188	6	0.69
26	6	9	2	1900	1.55	6	1.046	5	0.16
27	6	10	3	1900	0.81	8	1.149	6	0.67
28	6	11	4	1900	0.49	10	0.903	11	2.31
29	7	9	1	2600	7.98	6	0.919	6	0.20
30	7	10	2	2600	2.88	8	1.025	7	-0.19
31	7	11	3	2500	1.41	11	0.804	13	1.69
32	7	12	4	2500	1.05	16	0.864	18	1.42
33	8	10	1	4800	28.89	11	1.115	9	0.34
34	8	11	2	4800	8.17	13	0.859	15	0.67
35	8	12	3	4800	4.79	19	0.935	20	1.11
36	8	13	4	2700	2.10	29	0.998	29	1.43
37	9	11	1	2800	16.02	11	0.812	13	0.79
38	9	12	2	2200	4.28	15	0.927	16	1.17
39	9	13	3	2700	3.69	26	0.985	26	1.08
40	9	14	4	2500	2.96	45	0.848	53	5.72
41	10	12	1	2200	20.07	17	1.142	14	1.00
42	10	13	2	2700	11.02	31	1.164	26	1.20
43	10	14	3	2500	7.50	57	0.990	57	5.39
44	10	15	4	2000	0.81	15	0.946	15	-0.64
45	11	13	1	2700	46.44	32	1.001	31	1.88
46	11	14	2	2500	20.78	63	0.837	75	5.48
47	11	15	3	2000	1.90	18	0.805	22	-1.60
48	11	16	4	1700	0.72	16	0.758	21	-4.73
49	12	14	1	2500	91.64	69	0.826	83	6.97
50	12	15	2	2000	5.84	22	0.843	26	1.77

IP data of Line-II in S. Imbak Sub-area (2)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resist (ohm-m)	Tcf	Resis2 (ohm-m)	Charge. (mV/V)
51	12	16	3	2100	2.18	20	0.799	25	-2.30
52	12	17	4	2100	1.50	27	0.942	28	2.24
53	13	15	1	2000	62.16	59	0.987	59	6.85
54	13	16	2	2400	17.37	54	0.942	57	3.05
55	13	17	3	2400	9.26	73	1.093	66	3.65
56	13	18	4	2400	2.86	45	1.060	42	4.32
57	14	16	1	2250	81.44	68	1.028	66	6.82
58	14	17	2	2250	32.75	110	1.116	98	8.34
59	14	18	3	2250	8.55	72	1.036	69	8.29
60	14	19	4	2250	6.49	109	1.071	101	15.80
61	15	17	1	1800	49.89	52	1.079	48	1.63
62	15	18	2	1800	7.42	31	0.963	32	0.21
63	15	19	3	1800	3.98	42	0.980	42	3.87
64	15	20	4	2350	5.73	92	0.748	122	0.48
65	16	18	1	1550	50.27	61	0.902	67	1.02
66	16	19	2	1550	17.44	85	0.921	92	6.47
67	16	20	3	2350	25.32	203	0.692	293	2.38
68	16	21	4	1510	1.48	37	1.182	31	8.05
69	17	19	1	2000	139.07	131	1.035	126	8.54
70	17	20	2	2350	102.07	327	0.771	424	4.63
71	17	21	3	1510	5.24	65	1.319	49	10.31
72	17	22	4	1680	0.67	15	0.521	28	12.37
73	18	20	1	1625	613.79	705	0.757	931	14.20
74	18	21	2	1275	23.25	132	1.322	99	21.14
75	18	22	3	1700	2.62	29	0.504	57	29.35
76	18	23	4	1700	1.12	25	0.884	28	25.99
77	19	21	1	1275	124.44	177	1.551	114	20.13
78	19	22	2	1700	10.25	45	0.529	85	26.80
79	19	23	3	1700	4.15	46	0.950	48	29.88
80	19	24	4	1700	0.92	20	1.353	14	35.20
81	20	22	1	2350	69.88	56	0.356	157	23.96
82	20	23	2	2350	24.57	79	0.745	106	25.97
83	20	24	3	2350	5.47	44	1.057	41	27.57
84	20	25	4	2350	12.99	208	0.901	230	25.78
85	21	23	1	1510	87.17	109	1.881	57	25.26
86	21	24	2	1510	9.03	45	1.934	23	22.12
87	21	25	3	1510	5.55	69	1.483	46	27.56
88	21	26	4	1510	4.36	109	1.315	82	26.12
89	22	24	1	1680	20.53	23	0.804	28	23.94
90	22	25	2	1680	6.60	30	0.608	49	25.45
91	22	26	3	1680	4.40	49	0.531	92	24.50
92	22	27	4	1680	0.33	7	0.463	15	28.46
93	23	25	1	1220	23.70	37	0.735	50	26.15
94	23	26	2	1120	9.98	67	0.731	91	27.25
95	23	27	3	1480	0.66	8	0.562	14	32.80
96	23	28	4	1750	0.76	5	0.381	13	34.52
97	24	26	1	1120	135.56	228	0.965	236	16.09
98	24	27	2	1480	3.24	16	0.761	21	22.31
99	24	28	3	1750	3.85	12	0.522	22	18.58
100	24	29	4	1700	0.27	2	1.000	2	0.93

IP data of Line-H in S. Imbak Sub-area (3)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resis1 (ohm-m)	Tcf	Resis2 (ohm-m)	Charge. (mV/V)
101	25	27	1	1480	114.05	145	0.775	187	17.96
102	25	28	2	1310	2.78	16	0.550	29	7.74
103	25	29	3	1220	2.16	33	0.623	52	13.51
104	25	30	4	1220	0.71	22	0.624	35	6.56
105	26	28	1	1310	5.73	8	0.764	10	4.40
106	26	29	2	1120	4.32	29	0.875	33	8.72
107	26	30	3	1120	1.40	23	0.869	26	13.31
108	26	31	4	1120	1.00	33	1.858	17	12.37
109	27	29	1	1480	114.12	145	0.997	145	15.15
110	27	30	2	1480	15.79	80	0.989	80	13.89
111	27	31	3	1480	9.06	115	1.956	58	18.29
112	27	32	4	1480	5.03	128	2.230	57	14.04
113	28	30	1	1310	84.36	121	0.969	124	14.99
114	28	31	2	1310	34.09	196	1.735	112	19.89
115	28	32	3	1310	9.16	132	1.654	79	22.55
116	28	33	4	1680	4.16	93	1.605	57	17.01
117	29	31	1	1650	1208.16	1380	1.580	873	11.77
118	29	32	2	1650	48.03	219	1.171	187	23.58
119	29	33	3	1680	12.32	138	1.060	130	22.19
120	29	34	4	1100	1.30	44	0.764	57	15.13
121	30	32	1	1650	40.66	46	0.703	65	22.01
122	30	33	2	1680	7.17	32	0.658	48	21.61
123	30	34	3	1100	0.52	9	0.487	18	20.98
124	30	35	4	1100	0.44	15	0.277	54	22.99
125	31	33	1	1680	70.38	79	0.943	83	21.23
126	31	34	2	1100	7.67	52	0.758	68	18.65
127	31	35	3	1100	2.44	41	0.450	91	18.27
128	31	36	4	1480	1.55	39	0.329	118	12.87
129	32	34	1	1075	157.93	272	0.787	345	13.14
130	32	35	2	1100	330.32	2265	0.505	4485	7.80
131	32	36	3	1404	53.01	892	0.390	2287	9.91
132	32	37	4	1750	0.12	2	0.238	8	197.87
133	33	35	1	1100	-203.57	349	0.715	488	10.23
134	33	36	2	1480	10.29	52	0.615	84	16.08
135	33	37	3	1750	0.56	6	0.374	16	-0.57
136	33	38	4	—	—	—	—	—	—
137	34	36	1	1420	67.66	89	0.999	89	14.12
138	34	37	2	1750	1.78	8	0.599	13	23.87
139	34	38	3	1450	1.65	21	1.522	13	32.07
140	34	39	4	1100	8.77	296	3.164	93	22.63
141	35	37	1	1750	6.54	7	0.644	10	25.47
142	35	38	2	1450	23.11	121	1.672	72	20.34
143	35	39	3	1100	47.25	798	2.647	301	19.37
144	35	40	4	1080	8.08	289	1.312	220	21.23
145	36	38	1	1480	380.76	483	1.346	358	15.75
146	36	39	2	1480	219.21	1112	1.654	672	16.24
147	36	40	3	1420	9.95	132	0.715	184	8.82
148	36	41	4	1420	1.60	42	0.732	57	9.02
149	37	39	1	1750	402.22	429	1.042	411	15.19
150	37	40	2	1750	12.49	56	0.431	129	21.49

IP data of Line-II in S. Imbak Sub-area (4)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resis1 (ohm-m)	Tcf	Resis2 (ohm-m)	Charge. (mV/V)
151	37	41	3	1750	3.40	37	0.449	82	20.23
152	38	40	1	1800	67.56	78	0.420	185	19.02
153	38	41	2	1800	12.37	53	0.535	99	21.42
154	39	41	1	1100	108.61	184	1.423	129	22.75

IP data of Line-I in S. Imbak Sub-area (1)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resis1 (ohm-m)	Tcf	Resis2 (ohm-m)	Charge. (mV/V)
1	0	2	1	2300	10.76	9	1.025	8	0.69
2	0	3	2	3000	3.36	8	1.022	7	0.14
3	0	4	3	4000	2.02	9	1.076	8	0.35
4	0	5	4	4400	1.04	9	1.328	6	-0.29
5	1	3	1	3000	16.16	10	0.874	11	0.74
6	1	4	2	4000	5.87	11	0.950	11	0.37
7	1	5	3	4400	2.36	10	1.158	8	0.85
8	1	6	4	3500	1.02	11	1.279	8	0.14
9	2	4	1	2520	14.63	11	1.067	10	0.70
10	2	5	2	2800	3.50	9	1.247	7	0.42
11	2	6	3	2200	1.17	10	1.303	7	2.26
12	2	7	4	1500	0.44	11	1.158	9	2.12
13	3	5	1	2800	11.81	8	1.259	6	0.45
14	3	6	2	3000	3.64	9	1.171	7	-3.64
15	3	7	3	3000	1.60	10	1.015	9	10.59
16	3	8	4	2090	0.65	12	1.243	9	-0.46
17	4	6	1	4000	21.12	10	0.963	10	0.83
18	4	7	2	4000	5.24	10	0.846	11	1.23
19	4	8	3	4000	1.86	9	0.756	11	-3.00
20	4	9	4	4000	0.92	9	0.751	11	-0.60
21	5	7	1	4400	19.51	8	0.873	9	0.21
22	5	8	2	4400	4.28	7	0.827	8	0.79
23	5	9	3	4400	1.75	7	0.838	8	0.09
24	5	10	4	4500	1.01	8	0.873	9	1.00
25	6	8	1	3500	12.63	7	1.005	6	0.46
26	6	9	2	3500	3.43	7	1.020	6	0.36
27	6	10	3	4000	1.86	9	1.060	8	0.57
28	6	11	4	1900	0.30	6	1.052	5	1.82
29	7	9	1	2440	12.13	9	1.052	8	-0.07
30	7	10	2	2870	3.94	10	1.067	9	0.39
31	7	11	3	2100	0.53	5	1.039	4	1.20
32	7	12	4	2100	0.92	5	1.203	4	1.30
33	8	10	1	2100	11.54	10	0.976	10	0.84
34	8	11	2	1800	0.86	4	0.952	4	0.12
35	8	12	3	1800	1.07	4	1.096	3	1.42
36	8	13	4	2600	1.13	16	1.053	15	0.82
37	9	11	1	1800	4.33	5	0.947	5	1.10
38	9	12	2	1800	1.87	4	1.099	3	2.00
39	9	13	3	2600	3.71	27	1.036	26	3.74
40	9	14	4	2250	1.03	17	1.049	16	2.65
41	10	12	1	2200	13.91	12	1.089	11	0.81
42	10	13	2	2600	2.65	8	1.001	7	-12.80
43	10	14	3	2250	1.86	16	1.006	15	-1.08
44	10	15	4	3600	1.18	12	0.804	14	6.24
45	11	13	1	2600	18.02	13	0.920	14	1.35
46	11	14	2	2000	3.59	14	0.939	14	1.26
47	11	15	3	2000	1.07	10	0.756	13	1.99
48	11	16	4	2150	0.40	7	0.818	8	0.03
49	12	14	1	2200	13.79	12	1.000	12	0.53
50	12	15	2	2200	0.61	2	0.826	2	-28.73

IP data of Line-I in S. Imbak Sub-area (2)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resis1 (ohm-m)	Tef	Resis2 (ohm-m)	Charge. (mV/V)
51	12	16	3	2300	1.14	9	0.907	9	0.14
52	12	17	4	2300	0.49	8	0.863	9	-2.25
53	13	15	1	2600	20.66	15	0.805	18	3.96
54	13	16	2	3100	3.78	9	0.934	9	-1.71
55	13	17	3	3100	2.09	13	0.887	14	-2.72
56	13	18	4	2600	1.15	17	1.039	16	-1.23
57	14	16	1	3400	32.32	18	1.176	15	0.01
58	14	17	2	3400	8.82	20	1.040	19	0.31
59	14	18	3	3100	4.38	27	1.184	22	0.08
60	14	19	4	3100	1.44	18	1.046	17	-2.63
61	15	17	1	3100	44.14	27	0.846	31	1.84
62	15	18	2	3100	17.43	42	0.982	42	2.15
63	15	19	3	3100	3.98	24	0.856	28	1.42
64	15	20	4	1550	50.27	61	0.902	67	1.02
65	16	18	1	2400	54.93	43	1.076	39	0.88
66	16	19	2	2150	8.45	30	0.926	32	0.51
67	16	20	3	2000	4.66	44	0.980	44	26.10
68	16	21	4	1750	1.74	38	0.921	41	5.14
69	17	19	1	2150	36.63	32	0.857	37	0.82
70	17	20	2	1440	8.50	45	0.685	65	3.68
71	17	21	3	1750	3.73	40	0.899	44	3.37
72	17	22	4	1500	6.11	154	0.899	171	4.08
73	18	20	1	1440	34.29	45	0.871	51	4.34
74	18	21	2	1300	12.26	71	1.138	62	8.17
75	18	22	3	1500	14.20	178	1.095	162	3.25
76	18	23	4	3600	2.88	30	0.778	38	9.15
77	19	21	1	2700	381.07	266	1.192	223	15.31
78	19	22	2	2700	169.83	474	1.066	444	13.05
79	19	23	3	2700	10.07	70	0.746	93	15.09
80	19	24	4	2700	4.15	58	1.656	35	21.06
81	20	22	1	1900	1460.25	1449	0.898	1613	21.34
82	20	23	2	1900	26.44	105	0.641	163	21.32
83	20	24	3	1900	8.93	89	1.404	63	24.72
84	20	25	4	2000	4.80	90	0.855	105	19.30
85	21	23	1	1350	50.24	70	0.674	103	26.07
86	21	24	2	1350	10.09	56	1.552	36	31.22
87	21	25	3	2000	6.83	64	0.901	71	24.97
88	21	26	4	1500	1.84	46	0.843	54	30.04
89	22	24	1	1500	124.49	156	1.943	80	28.60
90	22	25	2	2000	37.77	142	0.849	167	24.38
91	22	26	3	1500	8.41	106	0.795	133	36.52
92	22	27	4	710	2.48	131	0.688	190	19.80
93	23	25	1	2000	24.58	23	0.415	55	26.32
94	23	26	2	1500	2.75	14	0.448	31	20.56
95	23	27	3	710	0.53	14	0.401	34	52.90
96	23	28	4	900	0.55	23	0.339	67	25.59
97	24	26	1	1500	17.34	22	1.119	19	26.72
98	24	27	2	710	2.40	25	0.979	25	26.85
99	24	28	3	900	1.46	31	0.826	37	24.20
100	24	29	4	2000	3.12	59	1.103	53	25.36

IP data of Line-I in S. Imbak Sub-area (3)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resis1 (ohm-m)	Tcf	Resis2 (ohm-m)	Charge. (mV/V)
101	25	27	1	710	17.78	47	0.854	55	14.11
102	25	28	2	900	6.27	52	0.711	73	18.97
103	25	29	3	2000	9.47	89	0.944	94	21.53
104	25	30	4	1600	1.36	32	0.290	110	19.66
105	26	28	1	1610	39.51	46	0.811	56	22.05
106	26	29	2	1610	14.50	68	1.095	62	20.19
107	26	30	3	1610	-0.76	26	0.325	80	33.27
108	26	31	4	1610	0.10	7	0.853	8	126.44
109	27	29	1	710	39.98	106	1.224	86	20.26
110	27	30	2	710	2.13	23	0.346	66	28.87
111	27	31	3	710	0.54	14	0.980	14	-58.91
112	27	32	4	710	0.98	52	2.217	23	12.67
113	28	30	1	900	9.81	21	0.287	73	7.66
114	28	31	2	900	4.26	36	1.025	35	23.69
115	28	32	3	900	4.12	86	2.059	41	9.73
116	28	33	4	900	0.97	41	1.997	20	3.85
117	29	31	1	2100	179.77	161	2.056	78	20.60
118	29	32	2	1750	74.85	323	2.603	124	24.31
119	29	33	3	1750	7.23	78	1.903	40	13.58
120	29	34	4	1650	0.74	17	0.845	20	43.64
121	30	32	1	1680	101.88	114	0.858	132	19.44
122	30	33	2	1690	5.41	24	0.531	45	14.73
123	30	34	3	1650	0.11	1	0.233	4	-9.46
124	30	35	4	1400	0.80	21	0.297	70	12.32
125	31	33	1	1700	54.49	60	0.580	103	18.68
126	31	34	2	1650	6.21	28	0.310	90	17.24
127	31	35	3	1400	2.11	28	0.431	64	17.71
128	31	36	4	1500	0.95	23	0.535	42	17.74
129	32	34	1	1650	41.36	47	0.569	82	18.80
130	32	35	2	1400	9.62	52	0.890	58	20.35
131	32	36	3	1500	2.49	31	1.122	27	16.60
132	32	37	4	1400	0.82	22	0.618	35	9.17
133	33	35	1	1400	265.17	357	1.605	222	19.29
134	33	36	2	1500	15.89	80	1.700	47	18.13
135	33	37	3	1400	4.20	56	0.871	64	14.67
136	33	38	4	1650	2.70	61	1.330	45	19.01
137	34	36	1	1500	67.44	85	0.965	88	19.34
138	34	37	2	1850	11.53	47	0.473	99	10.50
139	34	38	3	1650	5.05	57	0.751	75	16.40
140	34	39	4	1650	0.96	22	0.421	52	21.15
141	35	37	1	1850	73.13	74	0.550	134	18.96
142	35	38	2	1400	17.39	94	1.006	93	18.81
143	35	39	3	1400	3.93	53	0.585	90	17.53
144	35	40	4	1400	1.32	35	0.401	87	11.01
145	36	38	1	1500	143.77	181	1.485	121	26.04
146	36	39	2	1500	18.55	93	0.840	110	25.35
147	36	40	3	1500	6.80	85	0.582	146	19.87
148	36	41	4	1500	10.37	260	1.726	150	20.89
149	37	39	1	1850	81.90	83	0.594	139	21.73
140	37	40	2	1900	13.22	52	0.434	119	16.14

IP data of Line-I in S. Imbak Sub-area (4)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resis1 (ohm-m)	Tcf	Resis2 (ohm-m)	Charge. (mV/V)
141	37	41	3	1900	23.69	234	1.318	177	20.27
142	38	40	1	1300	241.84	350	0.909	385	15.00
143	38	41	2	1300	114.64	664	2.380	278	21.89
144	39	42	1	1850	448.22	456	1.230	370	17.80

IP data of Line-J in S. Imbak Sub-area (1)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resis1 (ohm-m)	Tcf	Resis2 (ohm-m)	Charge. (mV/V)
1	0	2	1	940	7.25	15	0.849	17	1.28
2	0	3	2	670	0.00	14	0.905	15	2.46
3	0	4	3	1260	1.06	16	1.053	15	2.76
4	0	5	4	2820	1.12	15	1.067	14	-0.87
5	1	3	1	670	4.58	13	1.047	12	0.55
6	1	4	2	1270	2.49	15	1.182	12	0.86
7	1	5	3	2820	2.14	14	1.169	11	5.88
8	1	6	4	2100	0.79	14	1.049	13	13.79
9	2	4	1	1260	7.65	11	1.013	10	1.02
10	2	5	2	2800	4.38	12	0.994	12	0.98
11	2	6	3	1280	0.82	12	0.897	13	0.96
12	2	7	4	1280	0.39	12	0.957	12	-3.07
13	3	5	1	2750	14.94	10	0.956	10	0.95
14	3	6	2	900	1.39	12	0.879	13	1.68
15	3	7	3	950	0.51	10	0.933	10	0.00
16	3	8	4	940	0.24	10	1.072	9	-0.11
17	4	6	1	4000	21.12	10	0.963	10	0.83
18	4	7	2	1800	2.11	9	1.065	8	0.57
19	4	8	3	1750	0.87	9	1.203	7	0.67
20	4	9	4	1750	0.32	7	1.085	6	-1.56
21	5	7	1	2700	15.13	11	1.121	9	1.14
22	5	8	2	3170	4.22	10	1.204	8	0.58
23	5	9	3	3160	1.17	7	1.061	6	1.04
24	5	10	4	3170	0.65	8	0.927	8	1.55
25	6	8	1	2570	23.25	17	0.973	17	1.30
26	6	9	2	2550	3.64	11	0.865	12	1.31
27	6	10	3	2550	1.54	11	0.766	14	1.08
28	6	11	4	2550	0.76	11	0.746	14	1.83
29	7	9	1	2320	14.63	12	0.904	13	1.43
30	7	10	2	2320	3.54	12	0.828	14	1.97
31	7	11	3	2330	1.39	11	0.816	13	1.61
32	7	12	4	4650	1.89	15	0.938	15	1.16
33	8	10	1	3250	17.94	10	0.973	10	0.69
34	8	11	2	2900	4.16	11	0.971	11	0.74
35	8	12	3	4650	0.00	15	1.103	13	1.01
36	8	13	4	3000	1.47	18	1.131	15	1.90
37	9	11	1	2900	14.31	19	0.983	19	0.23
38	9	12	2	4650	7.50	12	1.109	10	1.92
39	9	13	3	3000	2.15	9	1.116	8	1.16
40	9	14	4	2550	0.74	11	0.951	11	0.84
41	10	12	1	3600	33.51	18	1.054	17	3.26
42	10	13	2	2700	4.26	12	1.035	11	1.48
43	10	14	3	2200	1.15	10	0.869	11	1.85
44	10	15	4	3150	0.56	7	1.037	6	-0.99
45	11	13	1	2700	12.30	17	0.984	17	0.02
46	11	14	2	2200	2.03	7	0.829	8	0.10
47	11	15	3	3150	0.85	3	0.996	3	4.38
48	11	16	4	2350	0.32	5	0.971	5	-5.16
49	12	14	1	3750	14.18	7	0.867	8	0.35
50	12	15	2	3750	2.81	6	1.076	5	0.22

IP data of Line-J in S. Imbak Sub-area (2)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resist (ohm-m)	Tef	Resis2 (ohm-m)	Charge. (mV/V)
51	12	16	3	3600	1.21	6	1.044	5	1.33
52	12	17	4	3600	0.67	2	1.085	1	-0.37
53	13	15	1	2850	44.93	30	1.136	26	6.63
54	13	16	2	3650	4.52	9	1.068	8	1.15
55	13	17	3	3650	2.06	4	1.089	3	1.50
56	13	18	4	2450	0.62	10	1.099	9	2.32
57	14	16	1	3000	17.36	11	0.905	12	0.61
58	14	17	2	3000	4.61	6	0.924	6	0.31
59	14	18	3	2350	1.26	10	0.928	10	2.31
60	14	19	4	2350	0.86	14	0.754	18	-5.64
61	15	17	1	3200	17.76	10	1.051	9	0.76
62	15	18	2	3200	3.82	9	1.046	8	0.06
63	15	19	3	3200	2.04	12	0.844	14	-1.96
64	15	20	4	2700	0.93	13	0.831	15	-2.45
65	16	18	1	2000	10.30	10	0.935	10	-0.17
66	16	19	2	2000	3.33	13	0.776	16	-1.05
67	16	20	3	2100	0.90	8	0.779	10	-1.65
68	16	21	4	1750	1.74	38	0.921	41	5.14
69	17	19	1	2000	19.98	19	0.831	22	0.87
70	17	20	2	2750	6.17	17	0.874	19	-0.77
71	17	21	3	2100	2.64	24	0.890	26	-1.39
72	17	22	4	2000	2.31	44	1.038	42	3.81
73	18	20	1	2750	30.53	21	0.992	21	-0.87
74	18	21	2	2100	8.57	31	1.003	30	-2.81
75	18	22	3	2000	5.79	55	1.151	47	2.52
76	18	23	4	2100	3.78	68	1.203	56	9.10
77	19	21	1	2000	62.88	59	0.962	61	1.28
78	19	22	2	2000	29.17	110	1.081	101	3.83
79	19	23	3	2000	14.78	139	1.083	128	6.84
80	19	24	4	2000	9.35	58	0.923	62	10.27
81	20	22	1	2750	245.46	168	1.047	160	4.56
82	20	23	2	2700	72.74	203	1.022	198	10.70
83	20	24	3	2700	30.28	84	0.855	98	12.30
84	20	25	4	1900	11.47	228	0.696	327	7.76
85	21	23	1	2100	230.08	207	1.010	204	12.72
86	21	24	2	2100	48.80	87	0.827	105	15.27
87	21	25	3	1900	22.50	223	0.681	327	12.01
88	21	26	4	1400	8.01	215	1.117	192	1.33
89	22	24	1	2000	195.28	184	0.838	219	24.41
90	22	25	2	1900	70.18	278	0.758	366	20.44
91	22	26	3	1400	23.08	311	1.275	243	16.55
92	22	27	4	1250	17.21	518	1.233	420	11.34
93	23	25	1	1900	205.70	204	0.952	214	18.77
94	23	26	2	1400	51.04	274	1.569	174	15.02
95	23	27	3	1250	34.47	518	1.387	373	13.99
96	23	28	4	1550	3.80	92	1.176	78	21.82
97	24	26	1	1400	171.97	231	0.918	251	14.39
98	24	27	2	1250	54.90	330	0.826	399	16.29
99	24	28	3	1550	7.40	90	0.706	127	22.76
100	24	29	4	1600	5.27	130	0.821	158	25.02

IP data of Line-J in S. Imbak Sub-area (3)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resis1 (ohm-m)	Tcf	Resis2 (ohm-m)	Charge. (mV/V)
101	25	27	1	1250	478.57	719	0.924	778	12.30
102	25	28	2	1550	20.10	98	0.787	124	20.12
103	25	29	3	1600	10.39	127	0.930	136	23.10
104	25	30	4	1200	2.24	68	0.507	134	17.03
105	26	28	1	1400	1.00	126	0.940	134	16.00
106	26	29	2	1400	1.00	179	1.154	155	20.00
107	26	30	3	1400	1.00	113	0.656	172	7.00
108	26	31	4	1400	1.00	121	1.249	96	23.00
109	27	29	1	1250	1.00	261	1.039	251	17.00
110	27	30	2	1250	1.00	193	0.625	308	14.00
111	27	31	3	1250	1.00	215	1.206	178	23.00
112	27	32	4	1250	1.00	168	1.117	150	19.00
113	28	30	1	1550	1.00	72	0.685	105	15.00
114	28	31	2	1550	1.00	85	1.352	62	25.00
115	28	32	3	1550	1.00	100	1.189	84	22.00
116	28	33	4	1550	1.00	168	1.343	125	22.00
117	29	31	1	1600	1.00	127	2.051	61	25.00
118	29	32	2	1600	1.00	158	1.293	122	25.00
119	29	33	3	1600	1.00	172	1.404	122	25.00
120	29	34	4	800	3.40	166	1.502	110	20.78
121	30	32	1	1200	1.00	148	0.519	285	20.00
122	30	33	2	1670	19.17	87	0.613	141	20.90
123	30	34	3	1359	5.22	73	0.653	111	24.50
124	30	35	4	1280	4.26	125	0.691	180	25.75
125	31	33	1	1670	101.92	114	1.289	88	20.72
126	31	34	2	1350	20.61	115	1.282	89	23.94
127	31	35	3	1280	14.31	210	1.295	162	27.28
128	31	36	4	1350	4.82	134	0.828	161	22.41
129	32	34	1	1350	80.62	113	0.947	119	19.96
130	32	35	2	1280	35.66	210	0.947	221	27.21
131	32	36	3	1350	10.80	151	0.610	247	21.93
132	32	37	4	1180	3.49	111	0.439	252	26.37
133	33	35	1	1280	165.33	243	0.913	266	22.89
134	33	36	2	1350	34.97	195	0.619	315	18.97
135	33	37	3	1180	9.35	149	0.466	319	23.42
136	33	38	4	1670	9.13	206	0.744	276	24.72
137	34	36	1	1350	81.77	114	0.670	170	20.95
138	34	37	2	1180	17.32	111	0.568	195	28.13
139	34	38	3	1350	12.61	176	0.935	188	27.60
140	34	39	4	1350	5.91	165	0.903	182	28.62
141	35	37	1	1180	78.90	126	0.867	145	27.29
142	35	38	2	1280	38.05	224	1.460	153	29.79
143	35	39	3	1280	15.43	228	1.317	173	31.81
144	35	40	4	1300	12.64	338	1.786	189	27.47
145	36	38	1	1350	136.95	191	1.382	138	26.92
146	36	39	2	1350	30.19	169	1.103	153	28.60
147	36	40	3	1350	15.68	203	1.435	141	26.39
148	36	41	4	1350	2.36	71	0.591	120	22.26
149	37	39	1	1180	73.09	117	0.624	187	28.99
150	37	40	2	1180	24.90	149	0.890	167	29.22

IP data of Line-J in S. Imbak Sub-area (4)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resis1 (ohm-m)	Tef	Resis2 (ohm-m)	Charge. (mV/V)
151	37	41	3	1180	3.48	61	0.367	166	22.75
152	38	40	1	1150	102.09	159	1.089	146	34.07
153	38	41	2	1150	12.78	95	0.472	201	26.42
154	39	42	1	1650	70.61	99	0.461	214	29.65

IP data of Line-K in S. Imbak Sub-area (1)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resis1 (ohm-m)	Tcf	Resis2 (ohm-m)	Charge. (mV/V)
1	0	2	1	2600	1231.57	891	1.285	693	6.01
2	0	3	2	2550	698.37	2057	1.437	1431	7.91
3	0	4	3	2100	349.94	3134	2.092	1498	8.71
4	0	5	4	2300	32.18	527	1.981	266	7.48
5	1	3	1	2550	1657.76	1222	0.925	1321	7.84
6	1	4	2	2100	540.46	1940	1.267	1531	8.12
7	1	5	3	2300	43.11	353	1.103	320	7.05
8	1	6	4	2200	15.10	259	0.623	415	7.47
9	2	4	1	2100	1164.27	1046	1.158	903	6.03
10	2	5	2	2300	57.50	189	0.969	195	5.30
11	2	6	3	2200	15.47	133	0.549	242	7.01
12	2	7	4	2550	12.12	179	0.767	233	6.85
13	3	5	1	2250	251.75	211	0.764	276	9.72
14	3	6	2	2200	43.16	148	0.476	310	9.68
15	3	7	3	2510	30.49	228	0.710	321	9.77
16	3	8	4	2510	12.91	193	0.462	417	11.34
17	4	6	1	2200	99.08	85	0.642	132	5.52
18	4	7	2	2100	45.86	164	1.084	151	7.15
19	4	8	3	2100	19.28	172	0.721	238	9.45
20	4	9	4	2100	14.93	267	0.759	351	8.17
21	5	7	1	2250	134.36	112	1.382	81	4.11
22	5	8	2	2250	33.55	112	0.891	125	4.80
23	5	9	3	2250	20.32	169	0.955	176	2.97
24	5	10	4	2250	6.26	105	1.071	98	1.32
25	6	8	1	2200	102.58	88	0.626	140	6.15
26	6	9	2	2200	48.68	167	0.731	228	3.07
27	6	10	3	2200	13.69	117	0.821	142	1.72
28	6	11	4	1900	7.09	141	0.781	180	3.74
29	7	9	1	2000	440.75	415	1.220	340	10.46
30	7	10	2	2000	64.88	244	1.293	188	4.23
31	7	11	3	1900	28.13	279	1.221	228	4.47
32	7	12	4	2000	9.11	171	1.227	139	6.29
33	8	10	1	2200	399.45	342	0.905	377	10.58
34	8	11	2	1900	99.01	392	0.900	435	12.98
35	8	12	3	2000	32.17	303	0.913	331	13.95
36	8	13	4	1600	14.03	331	1.176	281	12.31
37	9	11	1	1900	565.86	561	0.854	656	11.17
38	9	12	2	2000	130.27	490	0.924	530	12.22
39	9	13	3	1600	47.93	565	1.178	479	11.94
40	9	14	4	1700	16.57	366	1.463	250	10.97
41	10	12	1	2000	443.13	417	1.144	364	7.88
42	10	13	2	1600	132.99	627	1.366	459	8.59
43	10	14	3	1700	39.39	436	1.583	275	9.51
44	10	15	4	1450	5.68	148	1.235	119	9.94
45	11	13	1	1600	697.52	822	1.126	730	7.63
46	11	14	2	1700	135.94	602	1.215	495	9.74
47	11	15	3	1450	16.19	211	0.910	231	13.75
48	11	16	4	1900	14.65	290	0.882	328	9.72
49	12	14	1	1700	663.01	733	0.904	810	8.19
50	12	15	2	1450	57.69	301	0.690	436	11.25

IP data of Line-K in S. Imbak Sub-area (2)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resis1 (ohm-m)	Tcf	Resis2 (ohm-m)	Charge. (mV/V)
51	12	16	3	2000	43.73	410	0.686	597	10.23
52	12	17	4	2000	25.61	485	0.677	716	10.26
53	13	15	1	1450	545.92	714	0.749	953	9.61
54	13	16	2	1600	240.08	1129	0.803	1405	10.66
55	13	17	3	1600	56.86	674	0.806	836	12.62
56	13	18	4	1550	8.25	201	0.869	231	20.46
57	14	16	1	1700	1152.05	1269	1.068	1188	9.73
58	14	17	2	1700	209.80	933	1.077	866	12.26
59	14	18	3	1700	15.46	171	1.146	149	21.72
60	14	19	4	1700	4.40	97	0.600	161	14.87
61	15	17	1	1450	859.16	1129	0.950	1188	11.58
62	15	18	2	1450	15.54	81	1.010	80	18.62
63	15	19	3	1450	5.47	71	0.548	129	12.24
64	16	18	1	1510	127.52	158	1.065	148	20.13
65	16	19	2	1510	16.99	84	0.609	137	15.40
66	17	19	1	1500	148.14	185	0.594	311	17.76

IP data of Line-L in S. Imbak Sub-area (1)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resis1 (ohm-m)	Tcf	Resis2 (ohm-m)	Charge. (mV/V)
1	0	2	1	2600	444.63	321	0.967	331	6.24
2	0	3	2	2700	48.49	135	1.231	109	2.68
3	0	4	3	3050	19.15	118	1.915	61	-1.15
4	0	5	4	1700	2.69	66	0.721	91	174.76
5	1	3	1	2700	194.26	135	1.202	112	1.82
6	1	4	2	3050	62.05	153	1.612	94	1.84
7	1	5	3	1900	7.67	76	0.567	134	4.03
8	1	6	4	1850	4.52	92	0.718	128	5.83
9	2	4	1	3050	153.54	95	1.178	80	1.93
10	2	5	2	1900	11.26	44	0.406	108	2.65
11	2	6	3	1850	6.07	62	0.552	112	4.73
12	2	7	4	2600	5.40	78	0.636	122	4.84
13	3	5	1	1900	15.75	16	0.335	47	0.78
14	3	6	2	1850	7.44	30	0.549	54	1.63
15	3	7	3	2700	6.19	43	0.669	64	3.76
16	3	8	4	2700	3.84	53	0.595	89	3.64
17	4	6	1	1850	40.50	41	1.680	24	0.96
18	4	7	2	3050	23.54	58	1.704	34	2.50
19	4	8	3	3050	11.19	69	1.426	48	1.74
20	4	9	4	3050	6.50	80	1.511	52	3.50
21	5	7	1	1800	39.32	41	0.920	44	1.11
22	5	8	2	1800	10.90	45	0.752	59	-0.36
23	5	9	3	1800	4.88	51	0.793	64	0.97
24	5	10	4	1800	2.90	61	0.811	75	2.13
25	6	8	1	1800	73.27	77	0.812	94	3.33
26	6	9	2	1800	17.98	75	0.925	81	3.62
27	6	10	3	1800	8.18	86	0.957	89	3.99
28	6	11	4	2400	6.97	109	0.935	116	4.73
29	7	9	1	2600	110.79	80	1.197	66	4.15
30	7	10	2	2600	32.80	95	1.188	79	4.22
31	7	11	3	2400	16.81	131	1.136	115	5.04
32	7	12	4	1750	6.95	149	0.898	165	6.83
33	8	10	1	2800	87.49	59	1.081	54	0.84
34	8	11	2	2400	30.22	94	1.019	92	1.82
35	8	12	3	1700	9.85	108	0.876	123	6.03
36	8	13	4	1850	6.49	132	1.181	111	4.54
37	9	11	1	2400	85.77	67	0.946	70	1.56
38	9	12	2	1700	16.51	73	0.827	88	2.87
39	9	13	3	1850	8.56	87	1.136	76	4.70
40	9	14	4	2350	4.56	73	1.035	70	6.16
41	10	12	1	1700	65.88	73	0.853	85	2.45
42	10	13	2	1850	20.57	84	1.230	68	2.89
43	10	14	3	2400	8.81	69	1.104	62	4.66
44	10	15	4	1700	5.57	124	0.922	134	4.47
45	11	13	1	1850	84.49	86	1.033	83	3.14
46	11	14	2	2400	24.77	78	0.945	82	6.30
47	11	15	3	1700	16.11	179	0.797	224	5.86
48	11	16	4	2400	16.64	262	1.184	221	8.13
49	12	14	1	2400	134.43	105	0.925	113	3.15
50	12	15	2	1700	31.38	139	0.777	178	6.93

IP data of Line-L in S. Imbak Sub-area (2)

No.	P1	C1	N	Curr (mA)	Voltage (mV)	Resis1 (ohm-m)	Tcf	Resis2 (ohm-m)	Charge. (mV/V)
51	12	16	3	1700	24.10	267	1.142	233	7.18
52	12	17	4	1700	14.63	324	1.242	260	13.24
53	13	15	1	1700	153.14	169	0.933	181	7.64
54	13	16	2	1850	83.57	340	1.405	241	7.26
55	13	17	3	1850	35.65	363	1.452	249	12.80
56	13	18	4	2400	8.24	129	0.915	140	7.22
57	14	16	1	2400	286.33	225	1.079	208	7.93
58	14	17	2	2400	65.19	205	1.019	201	14.27
59	14	18	3	2400	15.14	119	0.640	185	8.87
60	14	19	4	2400	8.27	130	0.860	151	7.50
61	15	17	1	1700	110.15	122	0.971	125	10.48
62	15	18	2	1700	15.59	69	0.615	112	8.12
63	15	19	3	1700	7.17	79	0.820	96	9.32
64	16	18	1	1750	314.70	337	0.705	478	14.02
65	16	19	2	1750	96.53	415	1.027	404	13.50
66	17	19	1	1950	207.53	201	1.526	131	10.97

Appendix 9

Generalized drilling results and summary of drilling activities

Drilling Results

Hole No.	Machine Type	Drilling Period	Drilling Depth (m)	Core		Drilling Shift			Drilling Rate	
				Length (m)	Recovery (%)	Drilling	Preparation & Removing	Total	Meter Per Shift	Meter per Total Shift
MJSI-1	F-30	1995- 8-29 1995- 9- 8	201.25	196.74	97.75	16	14	30	12.58	6.71
MJSI-2	F-30	1995- 9-23 1995- 9-29	200.30	200.30	100.00	13	10	23	15.41	8.70
MJSI-3	F-30	1995- 9-22 1995- 9-28	200.84	200.84	100.00	13	13	26	15.45	7.72
MJSI-4	F-30	1995- 9- 2 1995- 9-10	202.20	202.20	100.00	16	14	30	12.64	6.74
MJSI-5	F-30	1995-10- 9 1995-10-14	200.20	200.20	100.00	12	10	22	16.68	9.10

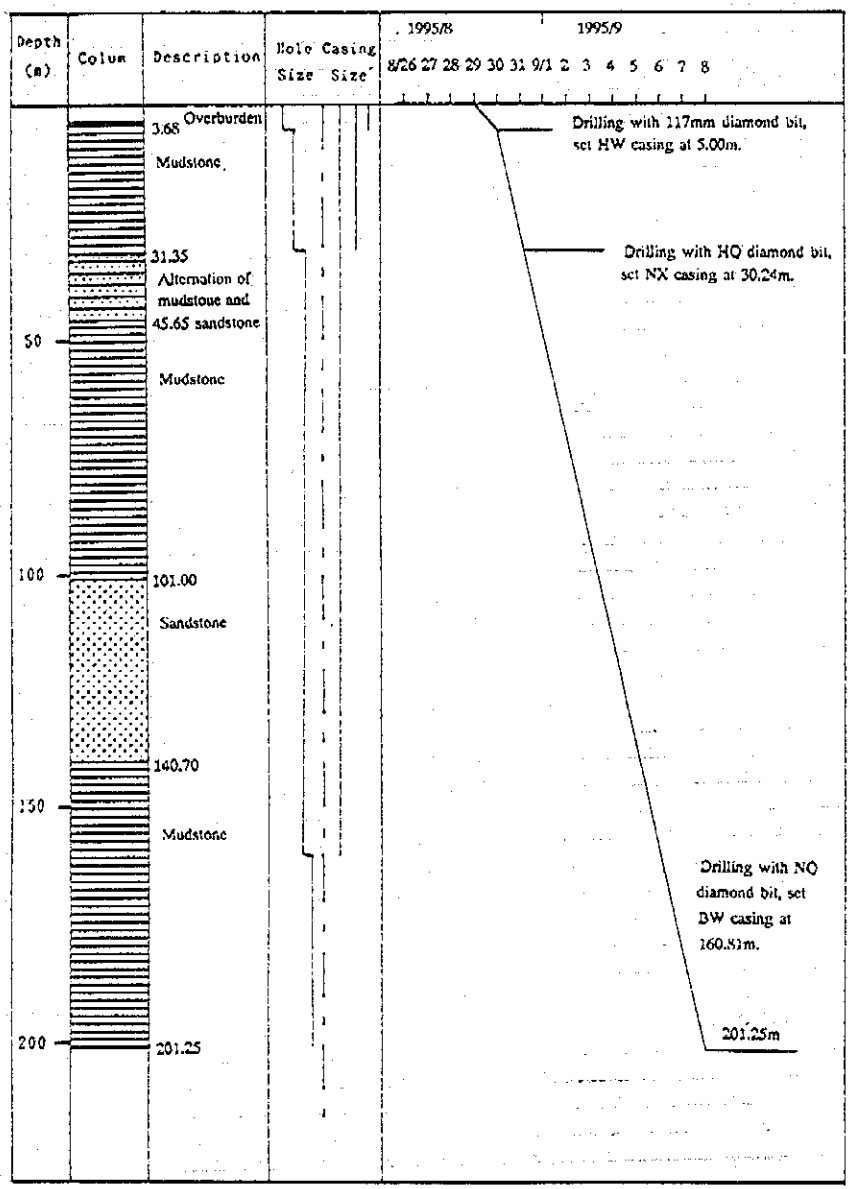
Drilling Activities

	Drill Hole	MJSI-1	MJSI-2	MJSI-3	MJSI-4	MJSI-5
Drilling Period	Presparation Days (A)	8/23 to 8/28 6	9/17 to 9/22 6	9/17 to 9/21 5	8/25 to 9/ 1 8	10/ 4 to 10/ 8 5
	Drilling Days (B)	8/29 to 9/ 8 11	9/23 to 9/29 7	9/22 to 9/28 7	9/ 2 to 9/10 9	10/ 9 to 10/14 6
	Removing Days (C)	9/ 9 to 9/16 8	8/30 to 10/ 3 5	9/29 to 10/ 6 8	9/11 to 9/16 6	10/15 to 10/19 5
	Total days (D)	25	17	20	23	16
Depth	Planned Depth (E)	200.00 m	200.00 m	200.00 m	200.00 m	200.00 m
	Drilled Depth (F)	201.25 m	200.30 m	200.84 m	202.20 m	200.20 m
Core Recovery	Overburden (G)	2.68 m	7.10 m	6.00 m	7.28 m	2.56 m
	Core Length (H)	196.74 m	200.30 m	200.84 m	202.20 m	200.20 m
	Recovery (H/F)	97.76 %	100.00 %	100.00 %	100.00 %	100.00 %
	Unit Recovery 0 m to 50 m	96.64 %	100.00 %	100.00 %	100.00 %	100.00 %
	Unit Recovery 50 m to 100 m	100.00 %	100.00 %	100.00 %	100.00 %	100.00 %
	Unit Recovery 100 m to 150 m	94.34 %	100.00 %	100.00 %	100.00 %	100.00 %
	Unit Recovery 150 m to 200 m	100.00 %	100.00 %	100.00 %	100.00 %	100.00 %
Casing	HW Casing	5.00 m	8.60 m	8.00 m	12.00 m	4.32 m
	NW Casing	30.24 m	30.00 m	30.01 m	30.03 m	30.09 m
	BW Casing	160.81 m	-	-	159.98 m	-
Rate	F/B meter/day	18.30 m	28.61 m	28.69 m	22.46 m	33.37 m
	F/D meter/total day	8.05 m	11.78 m	10.04 m	8.79 m	12.51 m

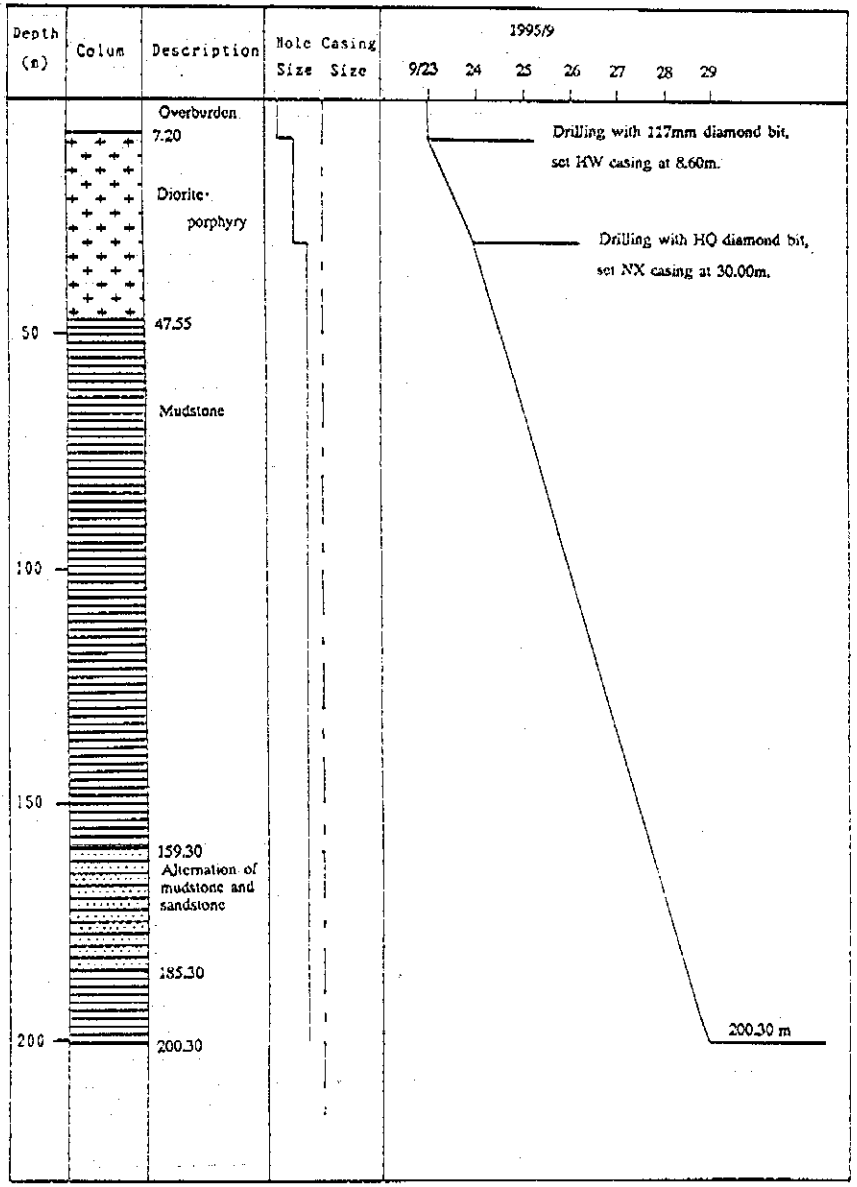
Appendix 10

Progress record of drilling

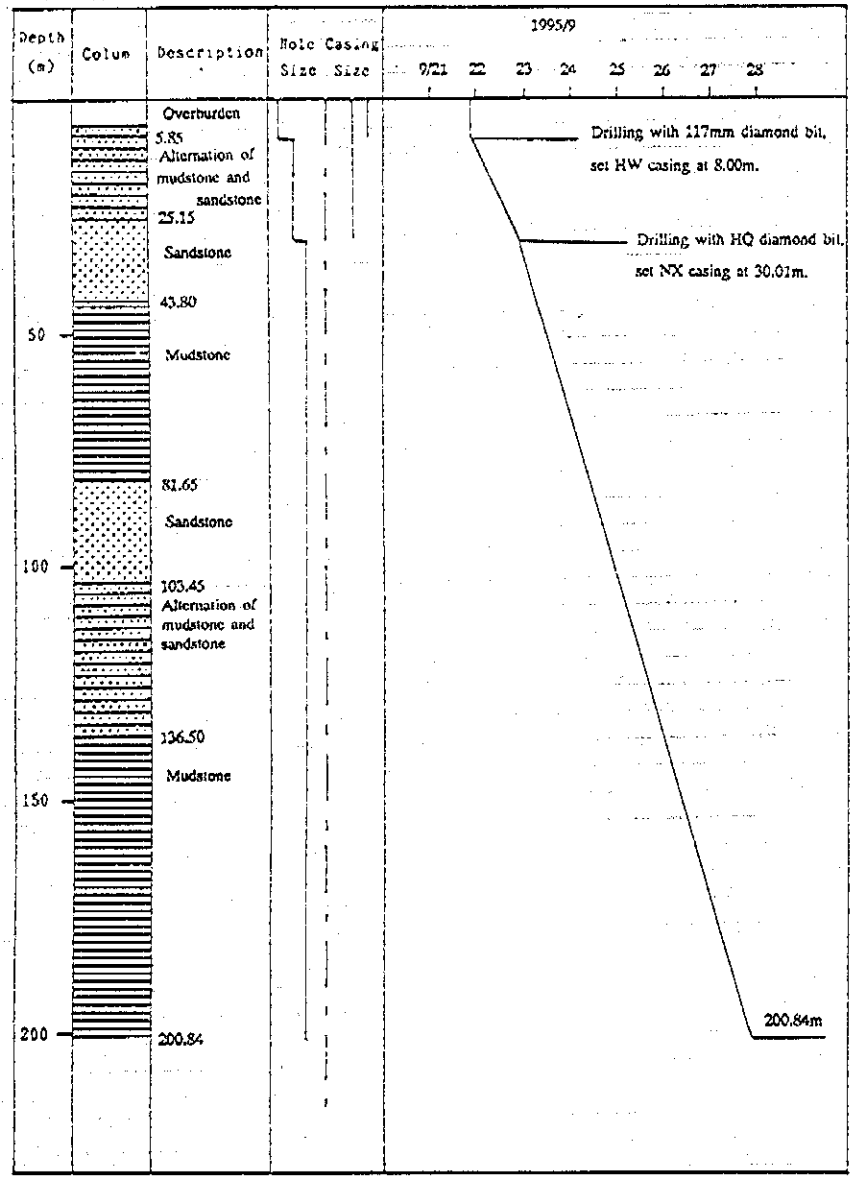
MJSI-2


Depth (m)
Colum
Description
Hole Size
Casing Size
1995/8
1995/9
8/26 27 28 29 30 31 9/1 2 3 4 5 6 7 8
Overburden
3.68
Mudstone
31.35
Alternation of mudstoue and
45.65 sandstone
Mudstone
101.00
Sandstone
140.70
Mudstone
201.25
50
100
150
200
Drilling with 117mm diamond bit, set HW casing at 5.00m.
Drilling with HQ diamond bit, set NX casing at 30.24m.
Drilling with NQ diamond bit, set BW casing at 160.81m.
201.25m

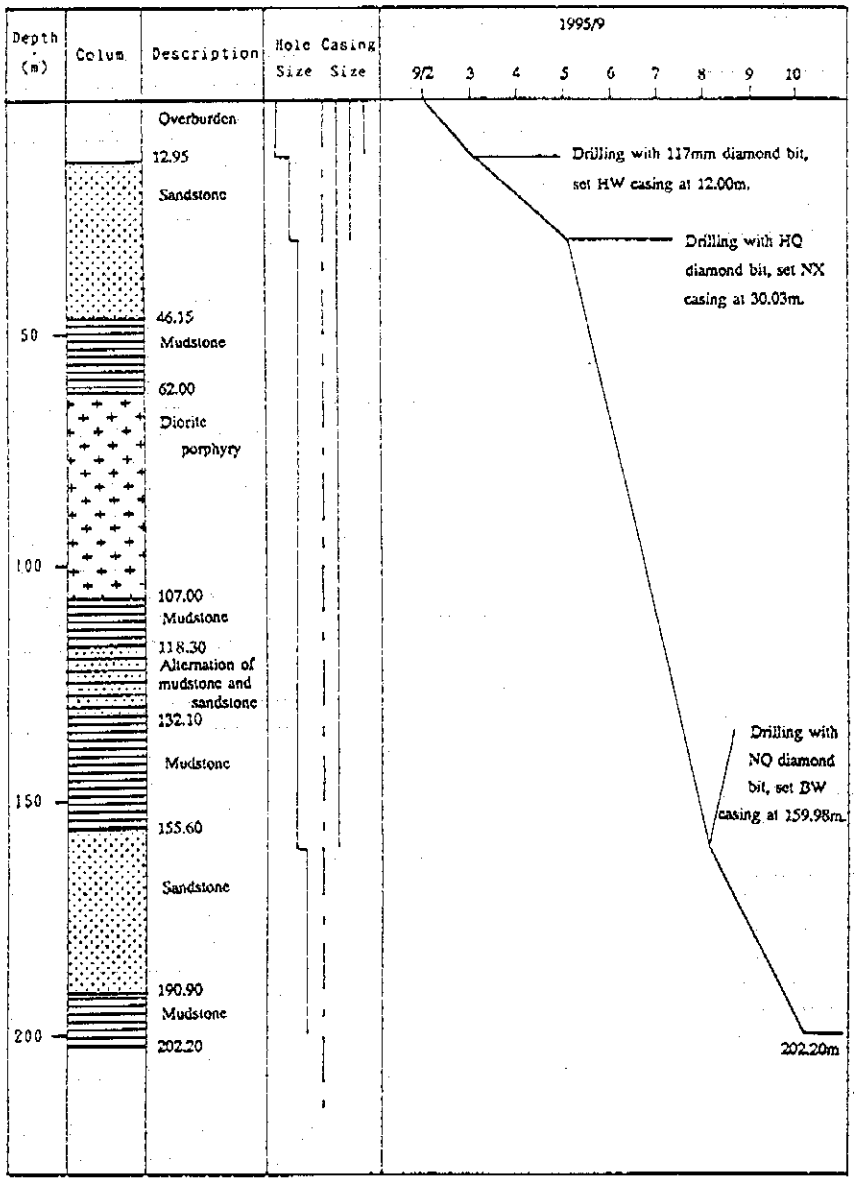
MJSI-2


Depth (m)
Colum
Description
Hole Size
Casing Size
1995/9
9/23 24 25 26 27 28 29
Overburden
7.20
Diorite-porphyry
47.55
Mudstone
159.30
Alternation of mudstone and sandstone
185.30
200.30
50
100
150
200
Drilling with 117mm diamond bit, set HW casing at 8.60m.
Drilling with HQ diamond bit, set NX casing at 30.00m.
200.30 m

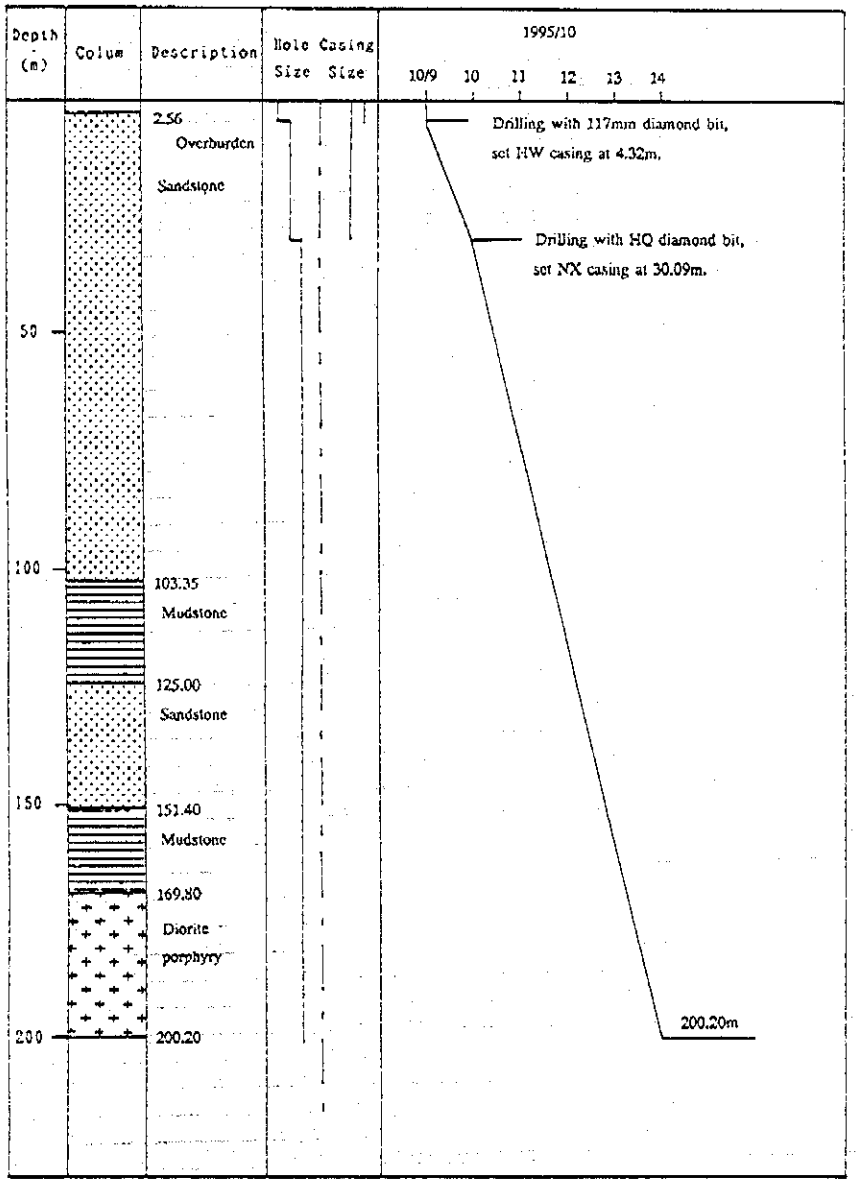
MJSI-3


Depth (m)
Colum
Description
Hole Size
Casing Size
1995/9
9/21
22
23
24
25
26
27
28
Overburden
5.85
Alternation of mudstone and sandstone
25.15
Sandstone
43.80
Mudstone
81.65
Sandstone
103.45
Alternation of mudstone and sandstone
136.50
Mudstone
200.84
50
100
150
200
Drilling with 117mm diamond bit, set HW casing at 8.00m.
Drilling with HQ diamond bit, set NX casing at 30.01m.
200.84m

MJSI-4


Depth (m)
Colum
Description
Hole Size
Casing Size
1995/9
9/2
3
4
5
6
7
8
9
10
Overburden
12.95
Sandstone
46.15
Mudstone
62.00
Diorite porphyry
107.00
Mudstone
118.30
Alternation of mudstone and sandstone
132.10
Mudstone
155.60
Sandstone
190.90
Mudstone
202.20
50
100
150
200
Drilling with 117mm diamond bit, set HW casing at 12.00m.
Drilling with HQ diamond bit, set NX casing at 30.03m.
Drilling with NQ diamond bit, set BW casing at 159.98m.
202.20m

MJSI-5


Depth (m)
Colum
Description
Hole Size
Casing Size
1995/10
10/9
10
11
12
13
14
2.56
Overburden
Sandstone
103.35
Mudstone
125.00
Sandstone
151.40
Mudstone
169.80
Diorite porphyry
200.20
50
100
150
200
Drilling with 117mm diamond bit, set HW casing at 4.32m.
Drilling with HQ diamond bit, set NX casing at 30.09m.
200.20m

Appendix 11

Drilling equipments and consumed materials

Drilling Equipment

Article	Model	Specification	Quantity
Drilling Machine	F-30	Maker: Mindrill (Australia) Capacity: BQWL 300 m Weight: 854 kg	2 sets
Diesel Engine	SR-4	Maker: (England) Horse Power: 31 HP/1500 rpm Weight: 270 kg	2 sets
	SR-2	Maker: (England) Horse Power: 10 HP/1500 rpm Weight: 195 kg	2 sets
Drilling Pump	--	Maker: Benroyal (Australia) Max capacity: 240 l/min Weight: 500 kg	2 sets
Wireline Hoist	WF-1	Maker: (Australia) Hoisting Capacity: 350 m	2 sets
Water Pump	E 32-20	Maker: (Australia) Max. capacity: 150 l/min	1 set
	50Z-20	Maker: (Australia) Max. capacity: 120 l/min	1 set
Diesel Engine	L-90E	Maker: Yanmar(Japan) Max. capacity: 6.6 KW, 9.0 PS/3600 rpm	1 set
	L-40-AE-DP	Maker: Yanmar(Japan) Max. capacity: 3.1 KW, 4.2 PS/3600 rpm	1 set
Drill Rod		HQWL(3.00 m/joint)	20 joints
		HQWL(1.00 m/joint)	6 joints
		HQWL(0.58 m/joint)	12 joints
		NQWL(3.00 m/joint)	160 joints
		NQWL(0.50 m/joint)	12 joints
		BQWL(3.00 m/joint)	150 joints
Casing Pipe		HW(3.00 m/joint)	20 joints
		HW(1.00 m/joint)	6 joints
		HW(0.50 m/joint)	12 joints

Consumed Material

Hole No.	HW 117 mm			HQ 101 mm			NQ 76 mm			BQ 59 mm		
	D.L.	Bit	R.	D.L.	Bit	R.	D.L.	Bit	R.	D.L.	Bit	R.
MJSI-1	–	–	–	30.24 m	1	1	130.57 m	2	1	40.44 m	1	1
MJSI-2	3.91m	1	–	26.09 m	1	1	170.30 m	2	1	–	–	–
MJSI-3	3.91m	1	–	26.10 m	1	1	170.83 m	2	1	–	–	–
MJSI-4	–	–	–	30.03 m	1	1	131.03 m	2	1	41.14 m	1	1
MJSI-5	4.32m	1	–	25.77 m	1	1	170.11 m	2	1	–	–	–

D.L. :Drilling Length (m) R. :Reamer

Consumed Material

Hole No.	Light Oil(l)	Cement 50 kg/Sx(Sx)	Bentonite 50 kg/Sx(Sx)
MJSI-1	1,800	5	20
MJSI-2	1,500	5	20
MJSI-3	1,500	5	20
MJSI-4	1,800	5	20
MJSI-5	1,600	5	20

Appendix 12

Drilling logs and assay results

Hole No. MJSI-1 (From 0.00 m to 50.00 m)

Depth (m)	Chart	Lithology and Alteration	Mineralization
		overburden light brown clayey soil with pebbles of mudstone.	
3.68		dark gray mudstone, brecciated and soft dark.	very weak Py, Ap dism, fracture filling Py film of 1-1mm wide rarely occurs, 1-few cm patches of Po, Py, Cp rarely occur.
7.85		gray mudstone with 0.5 - 5.0 cm wide sandstone layers, mudstone 80 %, lamina <10° - <20°	
10			11.30: Po,Py patch 2×7cm
		16.08-16.20: core crushed.	
		18.90-19.18: core crushed.	
20			19.65: Qz, Py, Cp vein 5mm wide, <70° .
		22.20 - 22.35: core crushed.	
			26.65: Qz vein with Py, Cp, 1cm wide, <70° .
30			30.95-31.00: network of 1- 2mm wide Py, Cpy veins.
31.35		alternation of mudstone and sandstone, mudstone dominates, dark gray mudstone(70 %) and gray fine sandstone(30%).	
			37.00: 3-4cm wide Po, Cp shapless patch.
40			43.95-44.32: Po, Cp patches in sandstone layer.
45.65		mudstone with 1cm to few mm sand lamina, <10° - <20° .	
50			

Depth (m)	D.L. (m)	Au (g/t)	Ag (g/t)	Cu (%)	Pb (%)	Zn (%)
26.55 26.95	0.40	<0.1	2.9	0.01	0.01	0.01

Hole No. MJSI-1 (From 50.00 m to 100.00 m)

Depth (m)	Chart	Lithology and Alteration	Mineralization	Depth (m)	D.L. (m)	Au (g/t)	Ag (g/t)	Cu (%)	Pb (%)	Zn (%)
		dark gray mudstone with sandstone lamina of 1mm to 10cm, lamina <10° -<20° .	very weak Po, Ap dism with rare occurrences of Po, Cp, (Ga) patches of few cm and fracture filling Py films of few mm wide.							
		54.30-54.60: core crushed.								
			57.70: Qz vein with Po, Py, Cp, Sp 2mm wide <80° .	56.95 57.30	0.35	<0.1	1.0	0.01	<0.01	<0.01
60			61.55: Po, Cp patch of 3×5 cm in sandstone layer.							
			64.25-64.50: few mm wide Po veinlets are slightly abundant.							
		69.70-69.80: core crushed.								
70			71.90: Po, Cp patch 3×10cm.							
			75.65: Po, Cp band-patch 1cm wide,<80° .							
			76.00-79.00: Po patch is abucent, only fracture filling film of less than 1mm.							
			79.30: Po, Cp band, ± 5mm wide, <60° .							
80			79.90: Po paych, shapless, 5×3cm.							
			88.55: Qz vein with Cp, Sp, 2 to 5mm wide, <85° .							
90			93.70: Sp, Py, Cp patch in sandstone layer, 3 to 5cm.							
		95.85-97.25: core crushed and brecciated.								
		99.35-99.75: core crushed and brecciated.								
100										

Hole No. MJSI-1 (From 100.00 m to 150.00 m)

Depth (m)	Chart	Lithology and Alteration	Mineralization
101.00		mudstone	very weak Py, Po, Ap dism, occationally Po, Py, Cp patch (nodule), veinlet and patch, 1 to 2 per meter. 102.10: Po, Py, Cp occur along reverse fault of few mm wide, dislocation 3cm, <80° . 105.30: Po, Cp, Py shaplee patch, 5×4cm.
		sandstone with mudstone lamina, sandstone(80%) and dark gray mudstone(30%) lamina of 1mm to 1cm wide, lamina <10° to <20° .	
110		112.20-112.50: core crushed Py films fill fractures. 113.10: reverse fault with dislocation of 5cm, <80° . 113.50- 113.70: core crushed. 114.40: 2cm wide fracture with Py. film, <70°	113.80: Po, Cp nodule, 4×5cm.
		118.50-118.90: core fractured.	117.20-117.50: Po, Cp, Py fracture filling film, few mm wide.
120		120.50: 5mm wide fracture Chl, Py, <85°	120.00-126.50: Py, Cp patch (nodule) is slightly abundant. 120.30: Po, Cp nodule, 4×5cm. 123.85: Po, Cp band 1 to 3cm. 126.00: Po, Cp band of 2cm wide, <10° , Cp occurs outside and srrounding Po.
130		135.10-135.80: sandstone layer.	131.00-149.00: Po patch abandunt, few per meter. 131.10: Cp, Py vein, 2 to 5 mm wide, <85° . 134.00-134.60: ±1mm wide Po, Cp film abandunt.
		137.90-138.15: core crushed.	137.80: Cp, Py vein, 0.5 to 1cm wide, <60° .
140			139.55: Py, Cp patch, 5×6cm.
140.70		mudstone(80%) with sandstone(20%) lamina and layer, few mm to 30cm 146.70-147.20: core crushed.	141.00: Py, Cp patch, 1.5 cm. 142.10- 142.30. Py, Po, Cp veinlet, few mm wide.
150			

Depth (m)	D.L. (m)	Au (g/t)	Ag (g/t)	Cu (%)	Pb (%)	Zn (%)
139.55 139.70	0.15	<0.1	2.4	0.02	<0.01	0.15

Hole No. MJSI-1 (From 150.00 m to 200.00 m)

Depth (m)	Chart	Lithology and Alteration	Mineralization	Depth (m)	D.L. (m)	Au (g/t)	Ag (g/t)	Cu (%)	Pb (%)	Zn (%)
		mudstone with sandstone layer and lamina.	very weak Po, Py, Ap dism., Po, Cp patch (nodule), few cm wide, 1 to 2 per meter.	150.00	0.15	<0.1	2.2	0.02	0.01	0.24
			150.05: Cp, Py shapless patch, 5×5cm.	150.15						
			157.75 - 163.00: Po patch is slightly abundant.							
160			159.00: Po, Cp nodule, 5×5cm.							
163.90										
164.45		lost core								
170										
		175.90-176.10: core crashed.								
180		180.20-180.80: core crushed, argillized and carbonated, <70° .								
190			189.50: Qz vein with Po, 5cm wide, <80° to <90° .							
			190.50: Qz, Po, Cp shapless patch, few cm.							
		192.00-201.25: core crushed.	190.00-201.25: oxidized Py films of less than 1mm occur.							
200										

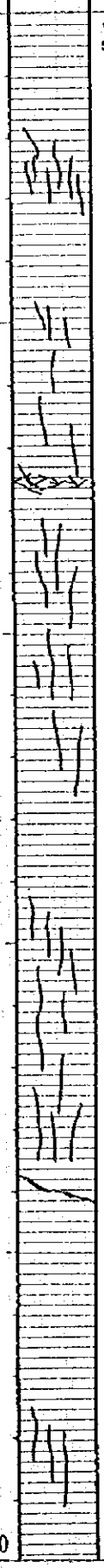
Hole No. MJSI-1 (From 200.00 m to 201.25 m)

Depth (m)	Chart	Lithology and Alteration	Mineralization	Depth (m)	D.L. (m)	Au (g/t)	Ag (g/t)	Cu (%)	Pb (%)	Zn (%)
		mudstone with sandstone layer and lamina.								
201.15										
210										

Hole No. MISI-2 (From 0.00 m to 50.00 m)

Depth (m)	Chart	Lithology and Alteration	Mineralization	Depth (m)	D.L. (m)	Au (g/t)	Ag (g/t)	Cu (%)	Pb (%)	Zn (%)
		overburden light brown soil with oxidized mudstone boulder.								
7.20		dark gray diorite porphyry, hornblende phenocryst, 1-5mm size, fine grained like andesite. 7.20-10.10: light gray, argillized and silicified. 8.20-8.60: carbonated. 10.10-21.80: slightly chloritized, relatively fresh diorite porphyry. 10.90-11.10: oxidized with He.	7.20-10.10: weak Po and Cp dism., fracture filling film of Po and Cp. 10.10-21.80: very weak Py dism. 15.70-16.10: fracture fillingPy. film, few mm wide.	7.55 8.55	1.00	<0.1	4.8	0.03	0.03	0.09
10										
		19.15: oxidized fracture with He, <80°, 1mm wide.								
20		20.10: oxidized fracture with He, <80°, 1mm wide. 21.80-30.00: silicified, slightly argillized, light gray diorite porphyry.	21.80-30.00: weak Po and Cp dism., fracture filling Po, Sp, Py film, few mm, some of them oxidized to He. 25.60: Po, Py, Cp vein, 3cm wide, <80°.	25.60 26.25	0.65	<0.1	25.2	0.06	0.13	0.51
			27.50: Py, Po, Cp, Ap vein, 2cm wide, <70°.	27.50 27.60	0.10	<0.1	3.8	0.04	0.01	0.08
30		30.00-33.90: dark gray, relatively fresh.	30.00-33.90: very weak Py dism.							
		33.90-42.00: slightly silicified and chloritized.	33.90-42.00: weak Po dism, fracture filling film py, Sp, Cp, few mm wide. 34.40: Po, Py, Ap, Cp vein, 2.5cm wide, <80°.	34.45 34.80	0.35	0.3	9.6	0.08	0.02	0.31
40				40.65 41.55	0.90	<0.1	2.6	0.01	<0.01	0.17
		42.00-44.40: relatively fresh, dark gray. 44.40-47.55: light gray, silicified.	42.00-44.40: very weak Py dism. 44.40-47.55: weak Po dism, fracture filling film of Py, Sp, Po, Cp, 1 to few mm wide.	44.85 45.05	0.20	<0.1	4.7	0.02	0.02	1.71
47.55		mudstone with sandstone lamina and layer, 1mm to 20cm, <20°, slightly chloritized along fracture.	47.55-51.55: very weak Po dism, fracture filling Po film rarely occur, few cm size patch or nodule of Po and Cp occurs few per meter.							
50										

Hole No. MJSI--2 (From 50.00 m to 100.00 m)

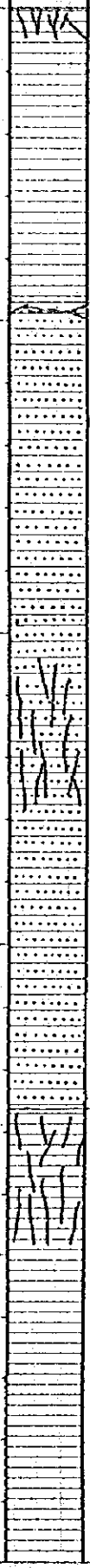


Depth (m)	Lithology and Alteration	Mineralization	Depth (m)	D.L. (m)	Au (g/t)	Ag (g/t)	Cu (%)	Pb (%)	Zn (%)
50	drak gray to black mudstone with sandstone layer.	48.70-48.80: network of Sp and Po veinlet, few mm wide. 51.00-76.00: lacks Py and Po dism.							
		less than 1mm wide fracture filling Py film, Po patch and nodule rarely occur.	54.30 55.20	0.90	<0.1	2.7	<0.01	0.01	0.12
60									
	64.50: 4cm wide argillized, crushed zone, <70° .	64.40-64.70: few mm wide Qz vein with Py network.							
70									
		75.90-76.50: Po patches of few cm size. 75.90-82.00: very weak Po and Py dism. 78.00-86.00: Po fracture filling film, less than 1mm to few mm wide.							
80									
		86.50-92.50: Po patch and nodule of few cm wide rarely occurs.							
	88.80-91.30: core fractured.	87.45: Po and Cp vein, 5mm wide, <70° . 95.00-96.20: fracture filling Po and Cp films of few mm wide, <80° .							
90									
100									

Hole No. MJSI-2 (From 100.00 m to 150.00 m)

Depth (m)	Chart	Lithology and Alteration	Mineralization	Depth (m)	D.L. (m)	Au (g/t)	Ag (g/t)	Cu (%)	Pb (%)	Zn (%)
110		dark gray to black mudstone with sandstone layer.	patch and nodule of Po of few cm size rarely occur, 1 or 2 per meter.							
		112.80–113.35: core crushed								
		115.15–115.60: core crushed.								
120										
			123.50: 1.5cm wide Po rich band, <20°.							
			128.00–129.30: Qz, Py, Po fracture filling film, ± 1mm wide.							
130			129.70: 3cm wide, silicified band with Po.	130.10	0.60	<0.1	0.1	<0.01	<0.01	0.03
			130.10–130.65: Qz, Po, Cp veinlet and patch of few mm to 1cm.	130.70						
			132.05–132.25: veinlet of Po.							
			139.00–141.30: network of Qz, Ca, Po veinlets, a few mm wide.							
140										
			149.00–151.00: network of Qz, Po, Ca veinlets, few mm wide.							
150										

Hole No. MJSI-2 (From 150.00 m to 200.00 m)

Depth (m)	Chart	Lithology and Alteration	Mineralization	Depth (m)	D.L. (m)	Au (g/t)	Ag (g/t)	Cu (%)	Pb (%)	Zn (%)
		dark gray to black mudstone with sandstone layer								
159.30										
160		alternation of mudstone(50%) and sandstone(50%), few mm to 30cm layers, sandstone layers are brecciated.	Po and Cp patch and nodule of few cm occur in sandstone layers, 1 to 2 per meter. Sandstone layer has weak Po dism. 159.60: 5 cm wide Po rich band.							
170			171.10–175.10: network of few mm wide Po, Po-Qz veinlets, <80° .							
180										
185.30		dark gray to black mudstone with few mm wide sandstone lamina.	Po rich patch rarely occurs, sandstone layer is weakly Po disseminated. 185.30–189.00: fracture filling films of Po, less than 1mm.							
190										
200										

Hole No. MJSI-2 (From 200.00 m to 200.30 m)

Depth (m)	Chart	Lithology and Alteration	Mineralization	Depth (m)	D.L. (m)	Au (g/t)	Ag (g/t)	Cu (%)	Pb (%)	Zn (%)
200.30		dark gray to black mudstone with few mm sandstone lamina.								
210										

Hole No. MJSI-3 (From 0.00 m to 50.00 m)

Depth (m)	Chart	Lithology and Alteration	Mineralization	Depth (m)	D.L. (m)	Au (g/t)	Ag (g/t)	Cu (%)	Pb (%)	Zn (%)
		overburden light brown soil with peeble and boulder of weathered sandstone and mudstone.								
5.85		alternation of gray to dark gray mudstone(40%) and gray sandstone(60%), each layer is few mm to 1m wide. 8.10-16.20: core generally crushed and oxidized, sandstone is silicified along fractures.	Py dism. and fracture filling Py film of less than 1mm to few mm, generally oxidized. 17.10-18.20: Qz, Py fracture filling films of few mm are abundant, <80° to <90° .	17.40 18.10	0.70	<0.1	4.6	0.01	0.03	0.06
25.15		gray sandstone(90%) with mudstone(10%) lamina of few mm to few 10 cm. lamina <10 ° to <20° .	Py dism. and fracture filling Py film, occationally Py lamina of few mm wide occurs along mudstone lamina, Py dism. less in sandstone.							
43.80		mudstone(90%) with sandstone(10%) layer of few mm to few 10cm. 46.60-59.00: slightly chloritized.	fracture filling film of Py and Cp, 1 to few mm wide, ± 1mm wide strips of Py, Cp along mudstone lamina, Py dism.							
50										

Hole No. MJSI-3 (From 50.00 m to 100.00 m)

Depth (m)	Chart	Lithology and Alteration	Mineralization	Depth (m)	D.L. (m)	Au (g/t)	Ag (g/t)	Cu (%)	Pb (%)	Zn (%)
		mudstone with sand stone layer.	50.50: Po, Py, Cp concentric nodule, few cm to 5cm. Py dism., fracture filling Py film less than 1 to few mm wide.	50.10 50.50	0.40	<0.1	0.6	<0.01	<0.01	<0.01
60			60.40: Qz vein with Py, 1cm wide, <60°. 61.60-64.00: fracture filling Py film of few mm wide is abundant. 63.20: Qz, Po, Py, Cp vein, 1 cm wide, <80°.							
		65.00-69.00: silicified.								
		66.10: 10cm wide brecciated, argillized zone, lamina <20°. 66.95-67.25: core crushed.	66.45: Qz, Po, Py, Cp vein of 1.5cm wide, <90°. 67.40-68.00: Qz, Po, Py, Cp irregular vein of +5cm wide, <70°.	67.60 68.35 68.80	0.75 0.45	<0.1 <0.1	15.8 1.1	0.08 <0.01	0.07 <0.01	<0.01 0.03
70			68.70- 69.00: Po, Cp irregular vein or patch of +5cm wide, <80°. 71.30: Qz, Py, Sp, Cp vein, 0.5cm wide, <80°.							
			78.50-80.50: Py, Cp, Sp veinlets of few mm wide, Py dism slightly strong.							
80										
81.65		sandstone(80%) with mudstone(20%) layer, each layer is few mm to few 10cm wide.	Py dism., fracture filling Py film, ocationally Py occurs along laminaand patch of ±5 mm size, rarely Sp is accosiated with Py.							
			88.00-91.00: Py patch and slightly strong Py dism.							
90										
			95.00-99.00: occationally Sp, Cp, Po patch and veinlet few mm to few cm occur. 96.80: Qz, Py, Po vein of 1cm wide, <80°.							
100										

Hole No. MJSI-3 (From 100.00 m to 150.00 m)

Depth (m)	Chart	Lithology and Alteration	Mineralization	Depth (m)	D.L. (m)	Au (g/t)	Ag (g/t)	Cu (%)	Pb (%)	Zn (%)
		sandstone with mudstone layer.								
103.45		alternation of sandstone(50%) and mudstone(50%), each layer is few cm to 50cm, lamina <20° .	weak Py dism., fracture filling Py film of less than 1mm, rarely few mm wide Py, Po, Sp, Cp films occur.							
110										
			114.90-118.50: Py, Po, Cp film of few mm is slightly abundant. 114.90: Qz, Py, Po, Sp, Cp vein of 0.5cm wide, <85° .							
120										
		124.10-124.80: core fractured.	125.90: Qz vein of 3cm wide, <85° .							
130			130.00-136.00: fracture filling film of Py, Po, Cp is abundant.							
		133.30-133.60: core crashed.								
136.50		mudstone(90%) with sandstone(10%) lamina of few mm to few cm.	weak Py and Po dism., fracture filling Py film or Py, Po, Cp film of ±1 mm wide.							
140										
			148.00: Po dism. and Po film increase, more than Py.							
150										

Hole No. MJSI-3 (From 150.00 m to 200.00 m)

Depth (m)	Chart	Lithology and Alteration	Mineralization	Depth (m)	D.L. (m)	Au (g/t)	Ag (g/t)	Cu (%)	Pb (%)	Zn (%)
		mudstone with sandstone lamina.	Po and Py dism., fracture filling Py film and Py, Po, Cp film.							
			153.00: Qz, Py, Po, Cp vein, 1cm wide, <70° .	153.30 153.90	0.60	<0.1	0.8	<0.01	<0.01	0.01
160			160.60: Qz, Po, Py, Cp vein, 1cm wide, <20° .							
			weak Py and Po dism., Py and Po-Cp fracture filling film, less than 1mm.							
			167.20-172.50: ±1cm wide Py, Cp, Sp veins occur, <70° to <80° .							
			167.50: Py, Cp, Sp vein, 1cm wide, <80° .	168.15 168.70	0.55	<0.1	11.8	0.04	0.14	0.43
170			168.15: Py, Cp, Sp vein, 0.5cm wide, <80° .	169.20 169.70	0.50	<0.1	8.4	0.02	0.15	0.14
			168.55: Py, Cp, Sp vein, 0.5cm wide, <80° .							
			169.20: Py, Cp, Sp vein, 0.5cm wide, <80° .							
			171.90: Py, Cp, Sp vein, 0.7cm wide, <80° .							
180			181.00- 185.00: Py, Cp nodule or patch of few cm, Py fracture filling film of less than 1mm.							
			185.70: Qz, Py, Po, Sp shapless vein, 5mm wide, <80° .							
190										
200										

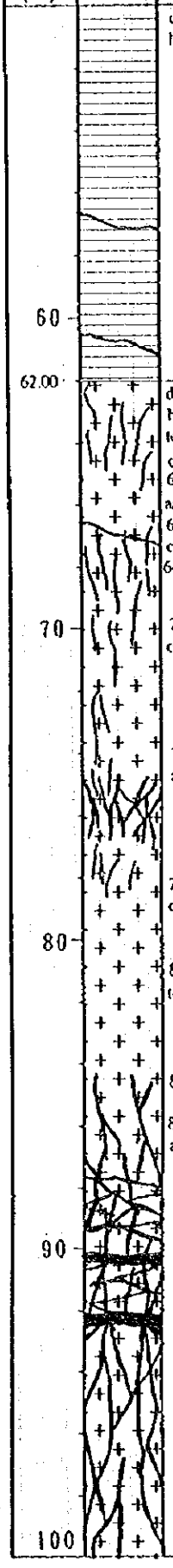
Hole No. MJSI-3 (From 200.00 m to 200.84 m)

Depth (m)	Chart	Lithology and Alteration	Mineralization	Depth (m)	D.L. (m)	Au (g/t)	Ag (g/t)	Cu (%)	Pb (%)	Zn (%)
200.84		mudstone with sandstone lamina.								
210										

Hole No. MJSI-4 (From 0.00 m to 50.00 m)

Depth (m)	Chart	Lithology and Alteration	Mineralization	Depth (m)	D.L. (m)	Au (g/t)	Ag (g/t)	Cu (%)	Pb (%)	Zn (%)
10		overburden brown soil and light gray sandstone boulder.								
12.95		gray sandstone(80%) with mudstone lamina and layer of few mm to few cm, partly weakly chloritized, especially along fracture, lamina <10° to <20° . 12.95-15.90: slightly chloritized mudstone(40%) is abundant. 14.80-15.25: core crushed.	weaK Py, Ap, Po dism , fracture filling Py film of ±1cm wide. 12.95-16.00: Py fracture filling film is abundant. 16.10: Po patch, 4×5c m. 18.80: Py fracture filling film, 1mm wide, <80° .							
20		22.20-22.80: slightly chloritized.	23.50: Py fracture filling film, 1 to 2mm wide, <70°							
30		34.60-35.00: core crushed.	31.25: Qz, Sp, Py, Cp vein, 1cm wide, <50° . 32.05: Py fracture filling film, 1mm wide, <85° . 33.20: Py fracture filling film, 2mm wide, <80° .	31.25 31.35	0.10	0.3	9.9	0.01	0.02	1.16
40		41.20-46.15: mudstone lamina increases.	41.60: Qz, Py vein, 7mm wide, <70° .							
46.15		dark gray mudstone with sandstone lamina of few mm to 1cm, lamina <10° to <20° .	45.70-45.80: Sp, Py fracture filling film. very weak Py, Ap dism , Py, Cp fracture filling film of less than 1mm wide.							
50										

Hole No. MJSI-4 (From 50.00 m to 100.00 m)



Depth (m)	Lithology and Alteration	Mineralization	Depth (m)	D.L. (m)	Au (g/t)	Ag (g/t)	Cu (%)	Pb (%)	Zn (%)
	dark gray mudstone with sandstone lamina.	50.65: Qz vein with Py, Cp, chlorite, 5mm wide, <10°.							
		51.80-60.90: Py, Cp nodule or patch of few cm occasionally occur.							
		54.00: Qz, Sp vein, 5mm wide, <0°.							
		56.00-60.90: few mm wide Qz, Ap, Cp, Cp, Sp veinlets occur few veinlet per meter.	56.30						
		56.60: Qz, Ap, Cp vein, 1.5cm wide, <20°.	56.70	0.40	<0.1	26.2	0.01	0.08	0.48
		61.50: Qz, Ap, Sp, Cp vein, 1.5cm wide, <70°.	61.50						
		Py weak dism. all through diorite porphyry.	61.65	0.15	<0.1	1.3	<0.01	0.03	0.07
	diorite porphyry with plagioclase, hornblende, biotite phenocryst of 1 to 0.5cm across, boundary <30°, no clear chilled margin and hornfels.	62.00-63.25: Sp-Cp of Py fracture filling film, less than 1mm wide.							
	62.00-63.25: silicified, slightly argillized, texture not clear.	61.25-70.75: weak Py, Cp dism., Sp-Cp and Py film, less than 1 mm to few mm.	66.40						
	63.25-64.25: relatively fresh with clear texture.	66.40: Qz, Sp, Cp vein, 1.5cm wide, <80°.	67.40	1.00	<0.1	4.7	0.02	0.03	0.14
	64.25-70.75: chloritized and silicified.	70.75-74.70: Py dism., fracture filling film of Sp and Cp, less than 1mm rarely occurs.							
	70.75-74.70: relatively fresh with clear texture.	74.70-78.50: weak Py, Cp, Sp, Ap dism., less than 1mm to few mm wide fracture filling film of Sp-Cp.	75.85						
	74.70-78.50: silicified, slightly argillized.	75.20-76.90: Qz, Sp, Cp irregular network veins, max. width 3cm, <90°.	76.80	0.95	<0.1	43.2	0.09	1.72	2.20
	78.50-81.40: gray, argillized, core crushed.	78.50-81.40: very weak Py, Cp, Sp dism., Sp, Cp fracture filling film rarely occurs.	79.00	1.00	<0.1	3.2	0.01	0.14	0.22
	81.40-83.60: relatively fresh and texture well preserved.	81.40-83.60: weak Py dism., Sp film rarely occurs.	80.00						
	83.60-84.10: argillized, core crushed.	83.60-84.10: weak Py dism	83.60						
	84.10-107.00: light gray, slightly argillized, silicified.	84.10-101.90: Sp rich zone(±1%). Sp, Cp fracture filling film, network veinlet, shapless patch, few mm to 10 cm, weak Py dism. and fracture filling film.	84.10	0.50	<0.1	4.3	0.02	0.10	0.21
			87.00						
			88.00	1.00	0.5	37.2	0.13	0.11	0.42
			89.00	1.00	0.2	39.2	0.11	0.11	0.46
			90.00	1.00	0.1	90.5	0.12	0.79	0.91
	91.50-92.80: core crushed.	86.70-89.50: Qz, Sp, Ap, Cp patch and irregular vein of 1 to 10cm are abundant.	90.80	0.80	0.8	5.5	0.09	0.01	0.38
		90.00-93.40: Qz, Sp, Py and Ap, Cp veins and irregular patches are abundant, few cm to few 10 cm, boundary with the host rock is not sharp.	92.00	1.00	0.4	5.9	0.08	0.01	0.04
			93.00	1.00	0.2	9.0	0.11	0.02	1.09
			94.00	1.00	0.3	9.3	0.08	0.02	1.01
		90.10: Qz, Sp, Py, Ap, Cp vein, 20cm wide, no sharp boundary, <10°.	95.00						
		92.05: Qz, Py, Cp, Ap vein, 40cm wide, <70°.							

Hole No. MJSI-4 (From 100.00 m to 150.00 m)

Depth (m)	Chart	Lithology and Alteration	Mineralization	Depth (m)	D.L. (m)	Au (g/t)	Ag (g/t)	Cu (%)	Pb (%)	Zn (%)
		diorite porphyry	100.45: Qz vein with Ap, 30cm wide, <70°. 101.90-107.00: Sp, Cp fracture filling film, less than 1mm.							
107.00		dark gray mudstone(80%) with sandstone(20%) lamina of 1mm to few cm,	very weak Py dism, rarely thin (± 1mm) film of Py and Qz, Py veinlet fill fracture, <50°.							
110										
118.30		alternation of mudstone(50%) and sandstone(50%), each layer is 1cm to 50cm wide.	Py fracture filling film, ± 1mm.							
120										
			124.35: irregular shape vein of Py, few mm to 10mm wide, <80°.	124.30 124.70	0.40	<0.1	10.6	0.02	0.02	0.03
130										
132.10		dark gray mudstone(70%) with sandstone(30%) layer of 1mm to 10cm wide.	fracture filling Py film of less than 1mm, very weak Po, Py dism. 133.00-150.80: few cm size nodule and patch of Po, Py, Cp. Py occurs outside of Po and Cp, preferably occurs in sandstone layer, few in 1 meter.							
140										
150										

Hole No. MJSI-4 (From 150.00 m to 200.00 m)

Depth (m)	Chart	Lithology and Alteration	Mineralization	Depth (m)	D.L. (m)	Au (g/t)	Ag (g/t)	Cu (%)	Pb (%)	Zn (%)
		dark gray mudstone with sandstone layer.								
155.60		gray sandstone(95%) with mudstone(5%) lamina of 1mm to few cm wide.	Py, Po fracture filling film, less than 1mm, weak Po, Py dism.							
160			160.50: Py, Po, Cp vein, 1.5cm wide, <80° .	160.45 160.65	0.20	1.3	3.3	0.07	<0.01	0.01
170										
180			very weak Po, Cp dism.							
			184.70: Qz, Po, Cp vein, 0.5cm wide, <60° . 185.30: Po, Cp vein, 0.5cm wide. 185.40: Po, Cp vein, 0.5cm wide, <70° . 186.80: Po, Cp vein, 0.3cm wide, <10° .							
190										
190.90		mudstone(80%) with sandstone(20%) lamina and layer of 1mm to 10cm.	Po, Py fracture filling film, less than 1mm to few mm wide. very weak Po, Py dism.							
200										

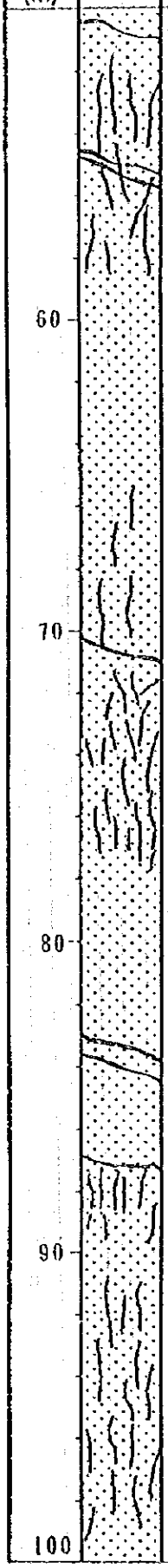
Hole No. MJSI-4 (From 200.00 m to 202.20 m)

Depth (m)	Chart	Lithology and Alteration	Mineralization	Depth (m)	D.L. (m)	Au (g/t)	Ag (g/t)	Cu (%)	Pb (%)	Zn (%)
202.20		mudstone with sandstone lamina								
210										

Hole No. MJSI-5 (From 0.00 m to 50.00 m)

Depth (m)	Chart	Lithology and Alteration	Mineralization	Depth (m)	D.L. (m)	Au (g/t)	Ag (g/t)	Cu (%)	Pb (%)	Zn (%)
		overburden brown soil with weathered sandstone pebble.								
2.56		gray sandstone with mudstone lamina of few mm to few cm, sandstone is slightly silicified. 2.56-16.00: fracture filling Py film, oxidized to He. lamina <10° to <20° .	very weak Py dism., fracture filling film of Py, ± 1mm tofew mm wide. 5.15-5.30: cubic Py spots(1 to 2%), few mm size. 6.90-7.00: cubic Py(1%) of few mm size and Cp dism. 12.40-12.50: cubic Py(±) dism., ±1%. 20.90-21.10: Dism. of cubic Py(±1%), some of the grains are oxidized, (Cp). 21.20: Py, (Sp) vein, 0.5cm wide, <80° . 25.00-25.40: dism. of cubic Py, partly oxidized, less than 1%. 25.90: Py, (Sp) vein, 1cm wide, <20° . 26.00-30.00: fracture filing film of Py (partly oxidized), Sp, Py, few mm wide. 32.15-32.30: dism. of cubic Py, few mm size, less than 1%. Py fracture filling film, ±1mmm wide, very weak Py dism.							
10										
20										
30		30.50-34.00: mudstone incleases, slightly chloritized.								
40		38.50-40.00: mudstone lamina incleases, slightly chloritized. 41.50-43.10: mudstone lamina incleases, slightly chloritized.								
50		46.20-47.50: mudstone lamina incleases.								

Hole No. MJSI-5 (From 50.00 m to 100.00 m)



Lithology and Alteration	Mineralization	Depth (m)	D.L. (m)	Au (g/t)	Ag (g/t)	Cu (%)	Pb (%)	Zn (%)
gray sandstone with mudstone lamina	fracture filling Py film, ±1mm wide.							
	50.50: Qz, Py, Cp, (Sp) vein, 4cm wide, <20°.							
	53.45-53.60: dism. of oxidized Py grains, elongated.	54.80						
		55.80	1.00	0.3	0.5	<0.01	<0.01	<0.01
56.00-56.50: core crushed and brecciated.	54.65-55.65: Qz, Py, Cp, (Sp) veins, 1.5cm and 2.0cm wide, <80°, patches of fine Py occur around them.							
	59.90-71.00: ±1 mm size Py (oxidized) grains are scattered.							
	60.00-70.00: fracture filling Py film is rare.							
71.25-72.60: chloritized, slightly greenish color.	70.80:Qz, Py, Cp vein, 2cm wide, <80°.							
	70.80-76.00: fracture filling Py, Cp film, <70° to <80°.							
75.10-77.00: chloritized.	75.10-77.10: chloritized zone, occationally Py, Cp dism. and patches of few cm occur.	75.60						
		76.15	0.55	<0.1	8.1	0.06	0.02	0.04
	80.00-86.00: oxidized Py, Po spots are scattered.							
	83.00: Qz, Ba, Py, Ap, Cp vein, 1cm widem, <80°.							
	83.70: Qz, Ba, Py, Cp vein, 1.5cm wide.	83.75						
		84.30	0.55	0.1	4.7	0.08	0.01	<0.01
	86.60-86.90: black patch consisting of fine Py, few cm, shapless.							
	86.90: Qz, Py, Cp vein, 1cm wide, <85°.							
	87.90-88.50: fracture filling film of Qz, Py, Cp.							
	90.00-100.00: fracture filling film of Py and Po, Cp, less than 1mm. very week Py, Po dism.							
95.20-95.50: core crushed.								

Hole No. MJSI-5 (From 100.00 m to 150.00 m)

Depth (m)	Chart	Lithology and Alteration	Mineralization	Depth (m)	D.L. (m)	Au (g/t)	Ag (g/t)	Cu (%)	Pb (%)	Zn (%)
		gray sandstone with mudstone lamina .	fracture fillinig film of Py, Po, Cp, very weak Py, Po dism.							
103.35		dark gray mudstone with sandstone layer of few mm to few cm. 104.50–120.00: slightly greenish, chloritized.	103.60: Qz, Py, Cp, Ap vein, 2.5cm wide, <20° .	103.60 103.65	0.05	5.7	13.8	0.32	0.01	0.01
110			108.00–120.00: patch or nodule consisting of fine grained Po occurs 2 or 3 per meter. 108.90: Py, Cp lenz, max. width 1cm, <20° . 112.00–113.00: network of Qz, Po, Cp veinlet, few mm to 5mm wide.							
120			117.00–119.00: fracture filling film of Py, Po, Cp.							
			123.10–124.00: network of Qz, Ap, Cp and Po, Cp veins, few mm to 2cm wide.	123.40 124.00	0.60	12.3	6.9	0.17	<0.01	<0.01
125.00		gray sandstone with dark gray mudstone lamina of few mm to few cm, lamina <20° .	123.90: Ap, Cp vein, 2cm wide, <10° . very weak Py, Po dism., fracture filling film rare.							
130			130.70: Qz, Py vein, 5mm wide, <60° . 133.30–133.35: dism. of Py, Po few mm grains. 134.40: Qz, Ba, Py, Po, Cp vein, 1cm wide, <80° . 137.50–140.20: Py or Po fracture filling film, ±1mm wide, few cm across oxidized patch.							
140			141.40: Qz, Py, Cp vein, 2cm wide, <60° .							
		146.60–150.10: mudstone lamina is slightly abundant.	147.00: Qz, Ba, Py vein, 5mm wide, <70° . 148.20: Qz, Ba, Py vein, 1 cm wide, <80° . 148.75–149.20: Qz, Ba, Py veinlet. 149.35: Qz, Ba, Py, Po vein, 1cm wide, <70° . 149.85: Qz, Po, Cp vein, 4cm wide, <80° .	149.85 150.10	0.25	0.2	6.8	0.07	<0.01	<0.01
150										

Hole No. MJSI-5 (From 150.00 m to 200.00 m)

Depth (m)	Chart	Lithology and Alteration	Mineralization
151.40		gray sandstone with dark gray mudstone lamina.	very weak PO, Py dism. fracture filling film of Po, Cp and Py, Cp, less than 1mm to few mm.
		dark gray mudstone with rare sandstone lamina and layer of 10 to 1 cm.	156.50-169.80: Po, (Cp) nodule and patch of few cm across, one or two per meter.
160			158.00: Qz, Po, Cp vein, 2cm wide, <80°.
			158.20: Qz, Po, Cp vein, 1cm wide, <70°.
			159.70-161.00: fracture filling film of Qz, Po and Po, Cp, few mm wide.
			165.10,165.30: ±5cm, Po, Cp nodule.
			165.15: Qz, Po, Cp, Py vein, 1cm wide, <70°.
			166.75: Po, Cp rich zone (patch), 3cm wide.
169.80			Po, Cp, (Py) dism. ±1%, fracture filling film of Po, Cp, Py.
170		gray diorite porphyry, phenocrysts are few mm to 5mm across plagioclase and hornblende, matrix consisits of plagioclase and biotite. intrusion angle <70°.	172.40: Po (oxidized), Cp vein, 1cm wide, <80°.
			175.90: Qz vein, 2cm wide, <80°.
		169.80-173.50: texture is not clear, gray color, silicified and slightly chloritized.	176.60-181.20: Po film rarely occurs, very weak Po dism.
		175.10-176.60: texture is not clear, gray color, silicified and slightly chloritized.	181.20-185.90: Po, Cp dism. (1%), fracture filling film of Po, Cp, ±1mm wide.
180			181.70: Qz, Po, Cp vein, 1cm wide, <80°.
		181.20-185.90: texture is not clear, silicified and chloritized.	183.05-183.60: Qz, Ba, Cp vein, 2 to 3cm.
			185.10-185.65: network of Qz, Po, Cp veins, ±1cm, <80°.
		185.90-189.80: relatively fresh diorite porphyry.	185.90-189.80: very weak Po, Cp dism., fracture filling film less and rare.
		189.80-192.30: silicified diorite porphyry.	189.80-192.30: Po, Cp dism.(±1%), fracture filling film of Po, Cp.
190			
		192.30-194.60: relatively fresh diorite porphyry.	
			190.40: Qz, Po, Cp vein, 1cm wide, <80°.
		194.60-200.20: silicified, slightly chloritized diorite porphyry.	194.60-200.20: Po, Cp dism.(±), fracture filling Po, Cp film and vein, ±1mm to 1cm wide.
			196.40-196.90: network of Qz, Po, Cp, (Py) veins, 1 cm wide.
200			

Depth (m)	D.L. (m)	Au (g/t)	Ag (g/t)	Cu (%)	Pb (%)	Zn (%)
150.10	0.25					
175.10 175.80	0.70	<0.1	4.1	0.03	0.01	0.01
183.00 183.60	0.60	<0.1	3.7	0.06	<0.01	<0.01
185.10 185.70	0.60	<0.1	0.9	0.02	<0.01	<0.01
192.00 193.00	1.00	<0.1	0.9	0.02	0.01	0.01
195.00 195.80	0.80	0.2	0.4	0.03	<0.01	<0.01
196.25 196.85	0.60	0.4	4.7	0.14	<0.01	<0.01

Hole No. MJSI-5 (From 200.00 m to 200.20 m)

Depth (m)	Chart	Lithology and Alteration	Mineralization	Depth (m)	D.L. (m)	Au (g/t)	Ag (g/t)	Cu (%)	Pb (%)	Zn (%)
200.80		diorite porphyry								
210										

E 4680.50

E 4681.00

E 4681.50

E 4682.00

400 m

300 m

300 m

A

N1454.50

500 m

N1454.00

500 m

N1453.50

600 m

N2Tj

40

30

0

60

IM-1

I1

10

85

I1

10